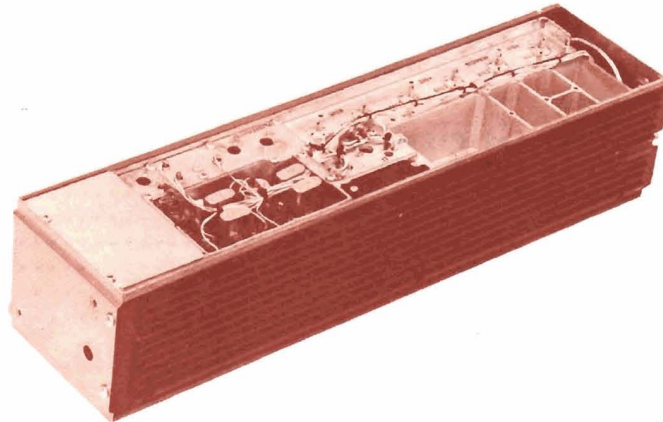


MASTR **Progress Line**

132—174 MHz RECEIVER MODELS 4ER41C10—21, 34—45
& 4ER41E10—21, 34—45 (Includes Options 7341—7344)



SPECIFICATIONS *

FCC Filing Designation	ER-41-C & E	
Frequency Range	132—174 MHz	
Audio Output	5 watts at less than 5% distortion	
Sensitivity	Standard Receivers	Ultra-High Sensitivity Receivers
	12-dB SINAD (EIA Method) 20-dB Quieting Method	0.35 μ V 0.5 μ V
Selectivity	-90 dB (adjacent channel, 30 kHz channels)	
	-100 dB at \pm 15 kHz	
Spurious Response	-100 dB	
	-94 dB	
First Oscillator Stability	\pm .0005% (-30°C to +60°C)	
	\pm .0002% (-30°C to +60°C)	
Modulation Acceptance	\pm 7 kHz (narrow-band)	
Squelch Sensitivity	0.2 μ V	
	0.1 μ V	
	Greater than 20-dB quieting (less than 1.5 μ V)	
Intermodulation (EIA)	-80 dB	
	-75 dB	
Maximum Frequency Separation	0.4%	
Frequency Response	+1 and -8 dB of a standard 6-dB per octave de-emphasis curve from 300 to 3000 Hz (1000-Hz reference)	

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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WARNING

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. **KEEP AWAY FROM LIVE CIRCUITS.**

The preamplifier uses a Field-Effect Transistor (FET) as the active device. The FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals. Lead identification for the FET is shown in Figure 2A. The FET has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 2B).

RF from the antenna is coupled through T1/T2 to the "source" terminal of FET Q1. Q1 operates as a grounded-gate amplifier. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the "drain" terminal and coupled through a tuned circuit (T3/T4) to the input of five helical resonators.

HELICAL RESONATORS

In standard receivers, five helical resonators (L301/L302 through L309/L310) provide the RF selectivity in the front end. RF cable W441 connects the RF signal from the antenna to a tap on L301/L302. In UHS receivers, the five helical resonators provide additional RF selectivity of the signal from the amplifier.

The tap on L301/L302 is positioned to provide the proper impedance match to the antenna or preamplifier. The output of the helical resonators is coupled through C3 to the 1st Mixer Assembly.

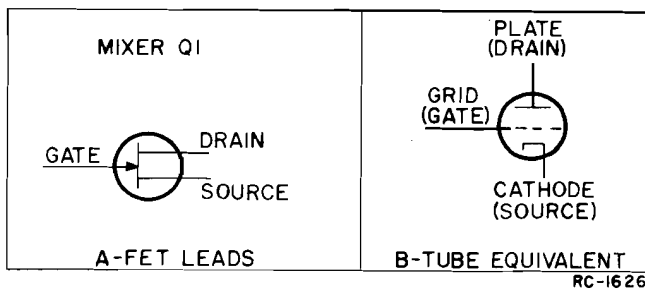


Figure 2 - FET Nomenclature

STANDARD OSCILLATOR/MULTIPLIER (A305-A310)

The receiver 1st oscillator operates in a transistorized Colpitts oscillator circuit. The oscillator crystal operates in a fundamental mode at a frequency of approximately 13 to 18 megahertz. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides $\pm 0.0005\%$ frequency stability as soon as the receiver is energized--without the warm-up time required by crystal ovens or warmers.

In single frequency receivers, bias for the oscillator transistor is obtained by a jumper from H1 to H2 on the oscillator board.

In multi-frequency receivers, a diode is connected in series with the crystal, and up to three additional crystal circuits can be added. The 10-volt jumper is removed and the proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit.

Switching the +10 volts to the crystal circuit forward biases the diode and reduces its impedance. This applies the crystal frequency to the base of oscillator transistor Q1. Feedback for the oscillator is developed across C21. The output is coupled to the base of 1st multiplier Q2.

The output of the 1st multiplier (tripler Q2) is transformer-coupled (T1/T2) to the 2nd multiplier assembly. The 1st multiplier tank is tuned to three times the crystal frequency, and is metered at centralized metering jack J442-4 through metering network CR5, R16, R5 and C33.

OSCILLATOR/MULTIPLIER BOARD WITH ICOM (Options 7341 - 7344)

Oscillator/Multiplier Boards A311 thru A314 use ICOM Module Model 4EG26A11. See the chart below:

OSCILLATOR BOARD	OPTION NUMBER	NUMBER OF FREQUENCIES
A311	7341	1
A312	7342	2
A313	7343	3
A314	7344	4

The ICOM Module consists of a crystal controlled Colpitts oscillator, a voltage regulator and a buffer output stage. The entire module (including crystal) is enclosed in a dust proof aluminum can, with the ICOM frequency and the receiver operating frequency printed on the top. Access to the oscillator trimmer is obtained by prying off the plastic GE decal on the top of the can.

The oscillator frequency is temperature-compensated at both ends of the temperature range to provide instant frequency compensation, with a frequency stability of $\pm 0.0002\%$ without crystal ovens or warmers.

In single-frequency receivers, +10 volts for operating the ICOM is obtained by a jumper from H1 to H2. With the ICOM operating, diode CR1 is forward biased and the oscillator output is applied to 1st multiplier Q2.

The output of the 1st multiplier (tripler Q2) is transformer-coupled (T1/T2) to the 2nd multiplier assembly. The 1st multiplier tank is tuned to three times the crystal frequency, and is metered at centralized metering jack J442-4 through metering network CR5, R16, R5 and C33.

In multi-frequency receivers, up to three additional ICOM modules can be plugged into the board. The 10-volt jumper is removed and the proper frequency is selected by switching the desired ICOM to +10 volts by means of a frequency selector switch on the control unit.

CAUTION

All ICOM modules are individually compensated at the factory, and cannot be repaired in the field. Any attempt to remove the ICOM cover will void the warranty.

2ND MULTIPLIER (A303/A304)

The 1st multiplier output is transformer-coupled through A303-T1/T2 to the base of 2nd multiplier A303-Q1. Following the 2nd multiplier are two resonant L-C circuits and a helical resonator tuned to nine times the crystal frequency. The output is taken from a tap on L311/L312 and applied to the 1st mixer.

1ST MIXER (A301/A302)

The 1st mixer uses a Field-Effect Transistor (FET) as the active device. (Fig. 2).

The FET has several advantages over a conventional transistor, including a high input impedance, high power gain, and an output that is relatively free of harmonics (low in intermodulation products).

In mixer A301/A302, RF from the helical resonators is applied to the gate of Q1, and injection voltage from the 2nd multiplier is applied to the source. The mixer output is taken from the drain with the output tuned to the 5.3 MHz high IF frequency.

HI IF AMPLIFIER (A315) AND CRYSTAL FILTER (A316)

A series-resonant circuit (A301-L3 and A315-C1) couples the mixer output to the emitter of the high IF amplifier A315-Q1. The transistor is connected as a grounded-base amplifier which provides a low impedance for the mixer input. The amplifier output is coupled through a transformer T1 to the crystal filter.

The highly-selective crystal filter (A316) provides the major selectivity for the receiver. The output of the filter is coupled through impedance-matching transformer A317-T1 to the base of the 2nd mixer.

2ND OSCILLATOR, 2ND MIXER AND 1ST LO IF AMPLIFIER (A317)

A317-Q2 operates in a Colpitts oscillator circuit, with feedback supplied through

C4. The oscillator low-side injection voltage (4845 kHz) is applied to the base of the 2nd mixer.

The High IF signal from the filter and the injection voltage from the 2nd oscillator is applied to the base of 2nd mixer Q2. The 445-kHz mixer output is applied to three tuned low IF circuits, L1, L2 and L3. These tuned circuits are required for shaping the nose of the IF waveform, and for rejecting any undesired output frequencies from the 2nd mixer.

The low IF signal is applied to the base of 1st low IF amplifier Q317-Q3. The output of A317-Q3 is R-C coupled to the base of the 2nd low IF amplifier.

2ND LO IF AMPLIFIER AND LIMITERS (A318)

Additional amplification of the low IF signal going to the limiter stages is provided by 2nd low IF amplifier A318-Q1. This stage is metered at J442-2 through a metering network consisting of C19, CR3 and R25.

Following the 2nd low IF amplifier are three R-C coupled limiter stages (A316-Q2, -Q3 and -Q4). The 1st limiter is metered at J442-3 through metering network C20, CR4 and R26.

DISCRIMINATOR (A318)

The limiter output is applied to a Foster-Seely type discriminator, where diodes CR1 and CR2 rectify the 455-kHz signal to recover the audio. The discriminator is metered at J442-10 through metering network C16 and R23.

AUDIO - NOISE AMPLIFIER (A318)

The discriminator output is coupled through a low-pass filter (C16, C18, R21 and R22) to the base of audio-noise amplifier Q5. The filter removes any 455-kHz signal remaining in the discriminator output. Q5 operates as an emitter-follower to match the discriminator impedance to the VOLUME control, SQUELCH control, and Channel Guard input. The stage also provides power gain.

AUDIO AMPLIFIERS (A318)

Any audio present in the incoming signal is coupled from the emitter of Q5 through the VOLUME control and a de-emphasis network to the base of audio amplifier Q6. The de-emphasis network consists of C22, C23, C24, R30 and R31.

Audio driver Q7 follows the audio amplifier. The output of Q7 is coupled through transformer T1 to provide phase inversion for the push-pull audio PA stage.

Q301 and Q302 operate as a push-pull, Class AB audio PA stage. The PA output is coupled through audio transformer T301 to the loudspeaker. The yellow and white tertiary windings of T301 supply balanced feedback to the collector of Q7 to minimize distortion.

Base bias for the PA stage and the elimination of crossover distortion is controlled by bias adjust potentiometer R43. The potentiometer is set at the factory as shown in STEP 1 of the receiver Test Procedure.

NOTE

Do not adjust bias adjust potentiometer R43 unless PA transistors Q301 and Q302 have been replaced.

Audio high and low are also present at centralized metering jack J442, and can be used as shown in STEP 1 of the receiver Test Procedure. The output stage provides 5 watts at less than 5% distortion into a 3.5-ohm load at the receiver output terminals (3.2-ohm load at the Control Unit).

SQUELCH (A318)

Noise from the audio-noise amplifier operates the squelch circuit. With no carrier present in the receiver, this noise is coupled to the base of noise amplifier Q8 through a high-pass filter which attenuates frequencies below 3 kHz. The filter consists of C30, C31 and R45, as well as C34 and L3 in the collector circuit of Q8. The gain of Q8 is determined by the Squelch control, which varies the bias on the base of Q8. Thermistor RT2 keeps the critical squelch constant over wide variations in temperature.

The output of noise amplifier Q8 is rectified by diodes CR5 and CR6, and filtered by C36 and C37 to produce a negative DC voltage. This DC voltage is applied to the base of DC amplifier Q9, turning it off. When turned off, the collector voltage of Q9 rises to approximately 8 volts, turning on DC amplifier Q10. When conducting, the collector voltage of Q10 drops to almost ground potential, which removes the base bias to audio amplifier Q6 and audio driver Q7, turning them off.

When the receiver is quieted by a signal (unsquelches), the noise in the receiver is reduced, turning DC amplifier Q9 on and DC amplifier Q10 off. This allows the audio stages to conduct so that sound is heard in the speaker. A network composed of C38, CR7 and R62 slows down the switching action of Q10, preventing an obnoxious "thump" from being heard in the speaker.

Resistor R53 connects from the emitter of audio driver Q7 to the emitter of noise amplifier Q8, providing a hysteresis loop in the squelch circuit. When a weak signal opens the squelch, the signal level may be reduced by 4 to 6 dB without the squelch closing. This limits squelch "flutter" or "picket-fence" operation.

With audio driver Q7 conducting, a positive voltage through R53 helps to reduce the gain of noise amplifier Q8. This positive feedback provides a quick, positive switching action in the squelch circuit. When the receiver squelches, audio driver Q7 turns off and its emitter potential drops to zero. This reduces the DC feedback through R53 to the emitter of noise amplifier Q8. Reducing the feedback causes Q8 to conduct harder, turning the audio stages off quickly.

Keying the transmitter removes the +10 volts from J19, turning off DC amplifier Q9 and turning on Q10 to mute the receiver.

CHANNEL GUARD

Channel Guard Board Model 4EK16A10 is a fully transistorized encoder-decoder for use the MASTR Professional Series mobile and station combinations. The tone frequencies are controlled by plug-in tone networks that are made with precision components for excellent stability and reliability. The tone frequencies range from 71.9 to 203.5 Hz.

Encoder (A319)

Keying the transmitter removes the receiver mute +10 volts, and forward biases feedback control diode CR5, causing it to conduct. When conducting, the diode shunts R39 which reduces the impedance of the positive feedback loop (R39, R35 and C19). This provides the necessary gain to the base of Q5 to permit oscillation.

The encoder tone is provided by selective amp-oscillator transistors Q5 and Q6 which oscillate at a frequency determined by the tone network. Negative feedback applied through the tone network to the base of Q5 prevents any gain in the stage except at the desired encode frequency.

Starting network R45, C21, C22 and CR6 provide an extremely fast starting time for the encoder tone. Keying the transmitter removes the receiver mute +10 volts, causing a pulse to be applied to the base of Q6 to quickly start the oscillator. Thermistor-resistor combination R32 and RT1 provides temperature compensation for the oscillator output. Limiter diodes CR3 and CR4 keep the tone amplitude constant.

Emitter-follower Q7 follows the oscillator circuit. The encoder tone is taken from the emitter of Q7 and applied to an active low-pass filter (G101) on the transmitter.

Decoder (A319)

The decoder function is designed to eliminate all calls that are not tone coded for the Channel Guard frequency. As long as the CHANNEL GUARD-OFF switch on the control unit is left in the CHANNEL GUARD position, all signals are locked out except those from transmitters that are continuously tone coded for positive identification by the receiver.

Placing the CHANNEL GUARD-OFF switch in the OFF position instantly disables the Channel Guard operation so that all calls on the channel can be heard. When the hook-switch option is used, lifting the microphone from its hanger disables the Channel Guard Circuit.

Audio, tone and noise are taken from the emitter of the receiver audio-noise amplifier A318-Q5 and is fed through A319-J1 to four tone amplifier and bandpass filter circuits. The filters remove the audio and high-frequency noise from the signal, and the tone amplifiers provide sufficient gain to insure clipping by limiter diodes CR1 and CR2. The clipping action eliminates variation in the squelch performance due to changes in tone deviation. The signal is then applied to selective amplifiers Q5 and Q6 which amplify only the tone determined by the tone network.

The output of the selective amplifier is applied through emitter-follower Q7 to the high gain, broad-band tone amplifiers Q8 and Q9. The output of Q9 is rectified by detector diodes CR7 and CR8, and the resulting negative DC voltage controls the squelch gate. Q8 is normally biased for low gain. When the tone is detected by CR7 and CR8, feedback is provided through R54 to quickly change the bias on Q8 for full gain. This ensures a more positive "unsquelching" action.

Squelch gate diode CR9 is normally forward biased by a positive DC voltage (approximately 1.5 volts) fed through R58. The forward bias causes CR9 to conduct, feeding a DC voltage to the base of DC amplifier A318-Q10 in the receiver. This removes the bias on the receiver audio stages and holds them off.

When the proper tone is applied to the decoder, the negative DC voltage from the detector diodes back-biases squelch gate diode CR9 and cuts off the positive bias to the receiver DC amplifier A318-Q10. However, the receiver noise squelch circuit continues

to operate until a carrier quiets the receiver.

Placing the CHANNEL GUARD - OFF switch in the OFF position (or removing the microphone from its hookswitch) removes the ground to the base of the decoder DC switch (Q10), causing it to conduct. This back-biases squelch control diode CR9 and cuts off the positive bias to the receiver DC amplifier (A318-Q10). The receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

A tone rejection filter connected in parallel with A318-J2 (in the receiver bypasses any incoming tone to ground. This attenuates the tone level reaching the receiver audio circuits. The filter is composed of C26, C27, C28, C29, L1 and R59.

An optional tone reject filter (A320) that is identical to the filter described above is available for use in two-way radios with transmitter Channel Guard only.

MAINTENANCE

DISASSEMBLY

To service the receiver from the top—

1. Pull locking handle down and pull radio about one inch out of mounting frame.
2. Pry up cover at rear of receiver.
3. Slide cover back and lift off.

To service the receiver from the bottom—

1. Pull locking handle down. Pull radio out of mounting frame.
2. Remove screws in bottom cover. Pry up cover at back of receiver.
3. Slide cover back and lift off.

To remove the receiver from the system frame—

1. Loosen the two Phillips-head retaining screws in front casting (see Figure 3), and pull casting away from system frame.
2. Remove the four screws in the back cover.
3. Remove the two screws holding the receiver at each end of the system frame.
4. Disconnect the antenna jack and the 20-pin connector from the front of the receiver, and slide the unit out of the system frame.

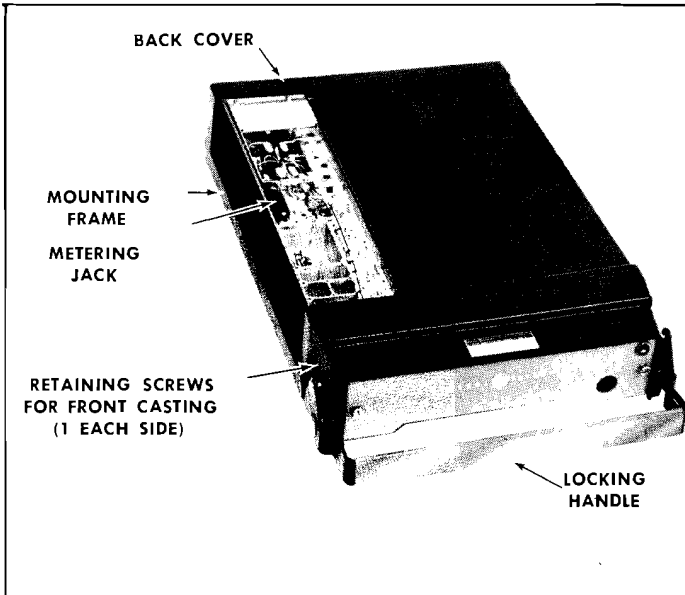


Figure 3 - Removing Top Cover

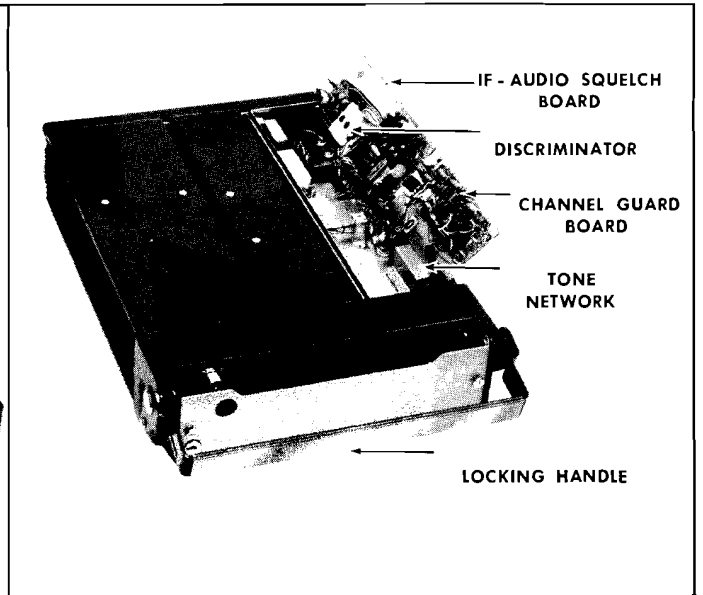


Figure 4 - Removing Bottom Cover

ICOM module, it is not used as the indicator. Instead, measure the following procedure.

ing the 42 to 56.25 should have an accuracy

cribed in Figure 15.

e mercury thermometer

equency counter. Then on the 1st OSC/MULT

°F) or 26.5°C (±2°C), nter should be 3 times case. Adjust the in this frequency.

e 80°F (±4°F) or tion curves of Figure as follows:

GE emblem and select the correction fac-

d on the ICOM by 3 and e correction factor sign (±) given to the

ould be 3 times the factor. Adjust the btain this frequency.

16.948,148 MHz
Green
35°C (95°F)
-1.15 PPM

948,148 MHz x 3 =

tion factor; (50.844
-58 hertz)

or 50.844,386 MHz;

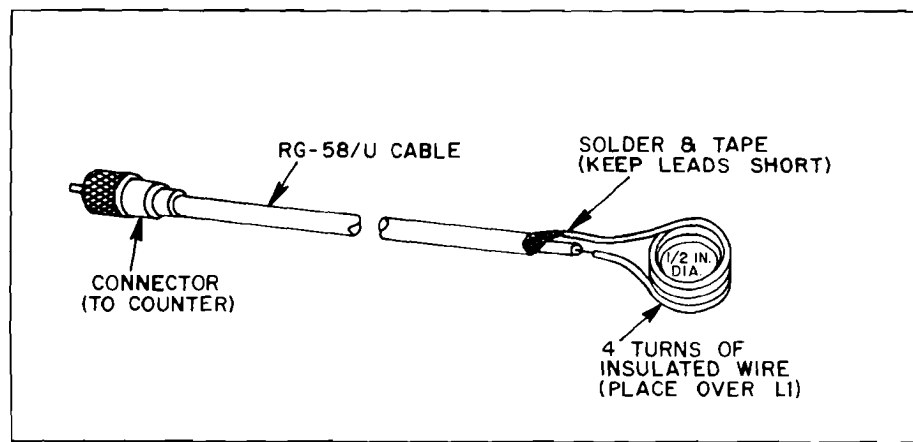


Figure 5 - Coaxial Cable and Test Loop

RC-1779

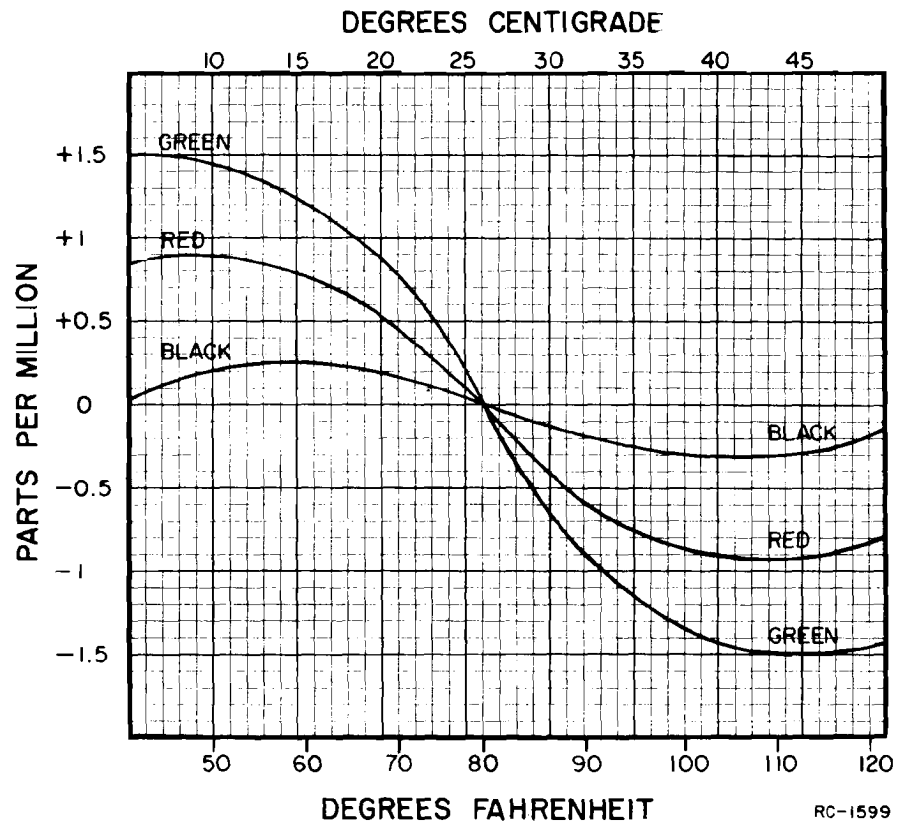


Figure 6 - ICOM Correction Curves

RC-1599

ICOM FREQUENCY ADJUSTMENT

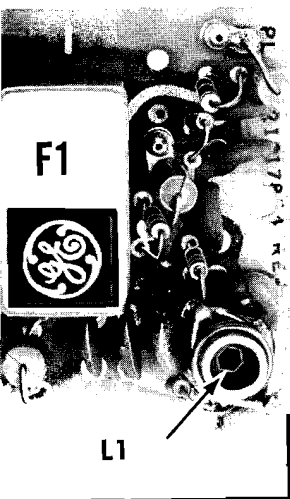
Due to the high stability of the ICOM module, it is not recommended that zero discriminator be used as the indication for setting the oscillator frequency. Instead, measure the ICOM frequency as described in the following procedure.

EQUIPMENT REQUIRED:

1. Frequency Counter capable of measuring the 42 to 56.25 MHz frequency range. The counter should have an accuracy of 0.4 part-per million (PPM).
2. Coaxial cable with test loop as described in Figure 15.
3. Mercury thermometer.

PROCEDURE:

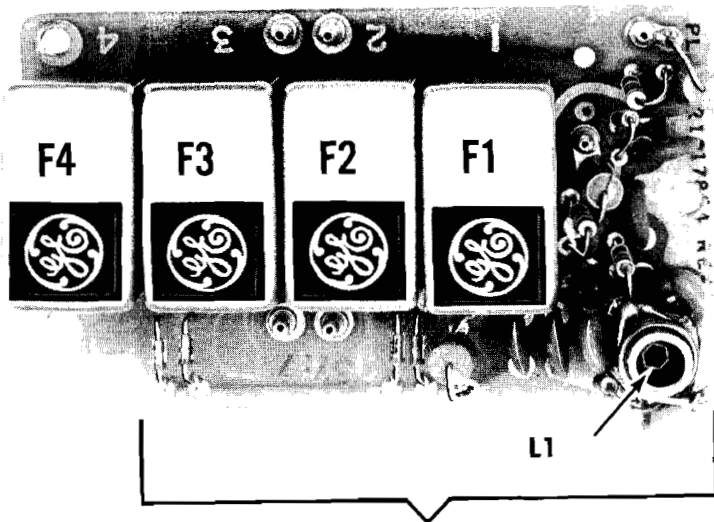
1. Check ICOM temperature by taping the mercury thermometer to the side of the ICOM.
2. Connect the coaxial cable to the frequency counter. Then place the 4-turn test loop over L1 on the 1st OSC/MULT board.
3. If the ICOM temperature is 80°F (±4°F) or 26.5°C (±2°C), the frequency indication on the counter should be 3 times the frequency stenciled on the ICOM case. Adjust the ICOM trimmer (if necessary) to obtain this frequency.
4. If the temperature is not within the 80°F (±4°F) or 26.5°C (±2°C) range, use the correction curves of Figure 6 for setting the ICOM frequency as follows:
 - a. Check the color dot beneath the GE emblem and select the matching curve to determine the correction factor in parts-per-million (PPM).
 - b. Multiply the frequency stenciled on the ICOM by 3 and then multiply this figure by the correction factor (from Figure 6) observing the sign (±) given to the correction factor.
 - c. The frequency measured at L1 should be 3 times the ICOM frequency ± the correction factor. Adjust the ICOM trimmer (if required) to obtain this frequency.



(ER-41-E)

EXAMPLE

ICOM Frequency	-	16.948,148 MHz
ICOM Color Dot	-	Green
Ambient Temperature	-	35°C (95°F)
Correction Factor	-	-1.15 PPM
Multiply ICOM Frequency by 3; (16.948,148 MHz x 3 = 50.844,444 MHz)		
Multiply preceding figure by correction factor; (50.844 MHz x -1.15 PPM = -58.47 hertz (or -58 hertz)		
Set the frequency measured at L1 for 50.844,386 MHz;		
50.844,444		
-	58	
<hr style="width: 50%; margin-left: 0;"/>		50.844,386



1ST OSC MULT. (ER-41-E)

ADJUSTMENT PROCEDURE

ICOM ADJUSTMENT
MODELS 4ER41E10-45

FRONT END ALIGNMENT

EQUIPMENT REQUIRED

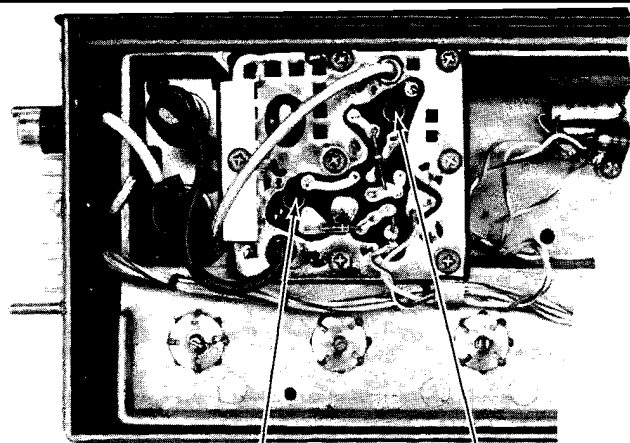
1. GE Test Set Model 4EX3A10, 4EX8K10, 11, station test meter panel or 20,000 ohms-per-volt multimeter.
2. A 132-174 MHz signal source. Connect a one-inch piece of insulated wire no larger than 0.065 inch to generator output probe.

PRELIMINARY CHECKS AND ADJUSTMENTS

1. Connect Test Set to receiver centralized metering jack J442 and set meter sensitivity switch to the TEST 1 or 1-volt position.
2. With Test Set in position J, check for regulated +10 volts. If using Multimeter, measure from C312 to C313.
3. If using Multimeter, connect the positive lead to J442-16 (ground).
4. Disable the Channel Guard.

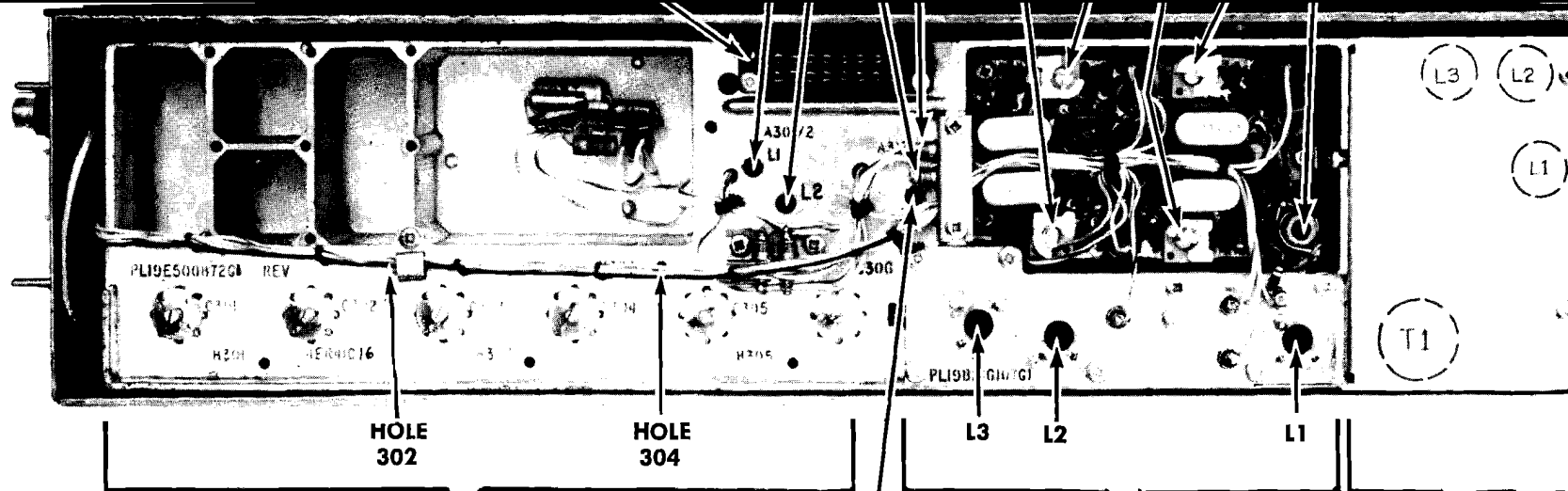
ALIGNMENT PROCEDURE

STEP	METERING POSITION		TUNING CONTROL	METER READING	PROCEDURE
	GE Test Set or Meter Panel	Multimeter - at J442			
OSCILLATOR AND MULTIPLIERS					
1.	D (MULT-1)	Pin 4	L1 (on 1st OSC/MULT) and L1 (on 2nd MULT)	See Procedure	Tune L1 (1st OSC/MULT) for maximum meter reading. Then tune L1 (2nd MULT) for minimum meter reading.
2.	E (MULT-2)	Pin 5	L1 (on 1st OSC/MULT) and L1, L2 and L3 (on 2nd MULT)	See Procedure	Tune L1 (1st OSC/MULT) and L1 and L2 (2nd MULT) for maximum meter reading. Then tune L3 (2nd MULT) for minimum meter reading.
3.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal into Hole 305. Adjust the signal generator for discriminator zero.
4.	B (2nd IF AMP)	Pin 2	L2 and L3 (on 2nd MULT) and C306 (on RF selectivity)	Maximum	Apply an on-frequency signal as above. Tune L2, L3 and C306 for maximum meter reading, keeping signal below saturation.
RF SELECTIVITY					
5.	B (2nd IF AMP)	Pin 2	C301, C302, C303, C304, C305 and C306 (all receivers), and T1/T2 and T3/T4 (UHS receivers)	Maximum	Apply an on-frequency signal to the antenna jack. On UHS receivers, tune T1/T2 and T3/T4 (PREAMP) for maximum meter reading. On all receivers, tune C301 through C306 for maximum meter reading, keeping signal below saturation. Then re-tune C301 through C306 slightly for maximum quieting.
FREQUENCY ADJUSTMENT					
6.	A (DISC)	Pin 10	C9 on 1st OSC/MULT (C10, C11 and C12) for multi-frequency	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 and C12 as required. <div style="text-align: center;">— NOTE —</div> For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50° to 90°F.



T3/T4

T1/T2



HOLE 302

HOLE 304

L3

L2

L1

T1

RF SELECTIVITY

HI IF AMP

2ND MULT

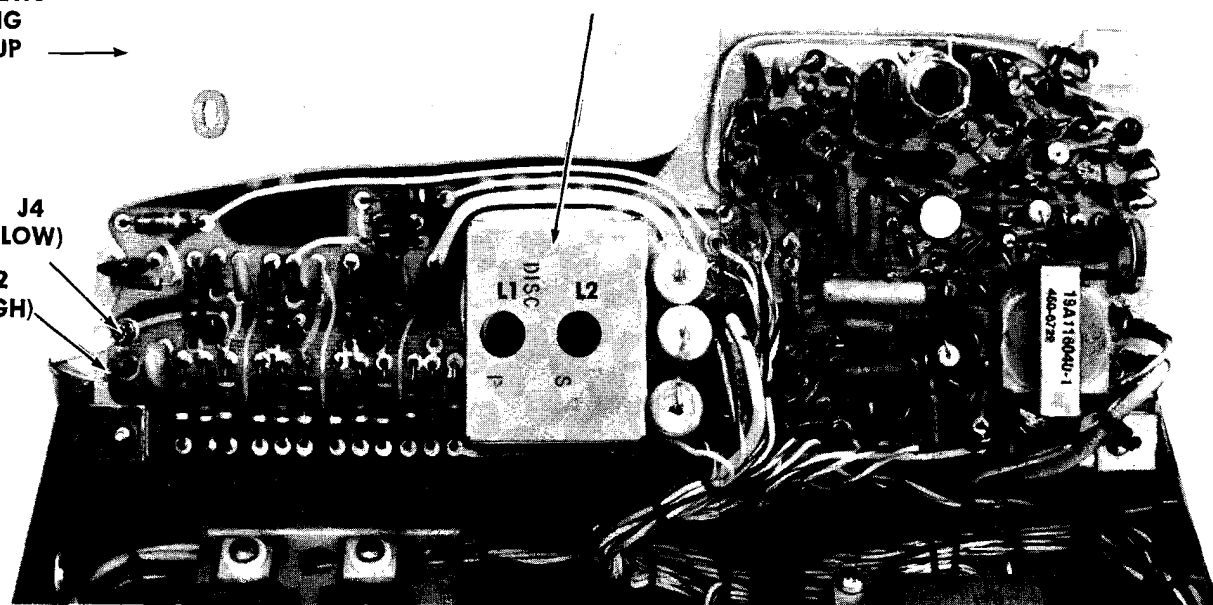
2ND MIXER

IF-AUDIO & SQUELCH

REMOVE THREE SCREWS TO SWING BOARD UP

DISCRIMINATOR

J4 (LOW)
J2 (HIGH)



NOTE 1: Appendix A of DATAFILE Bulletin 1000-6 contains instructions for building a sweep modulator.

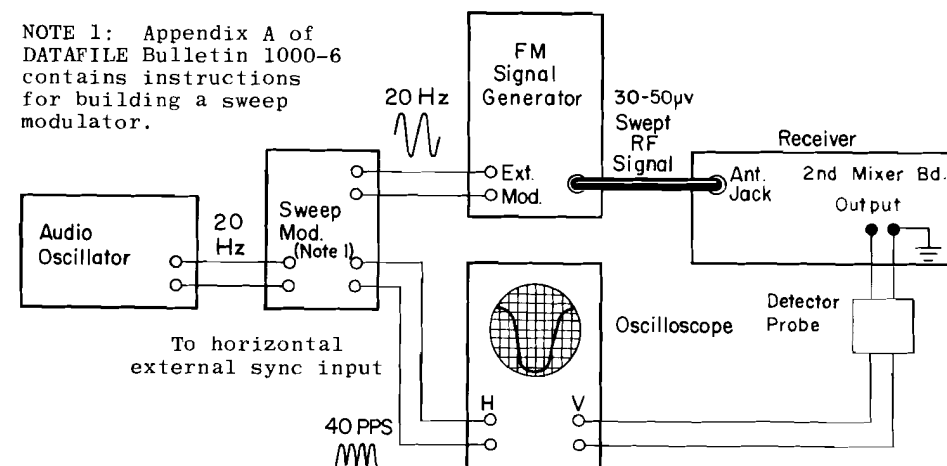
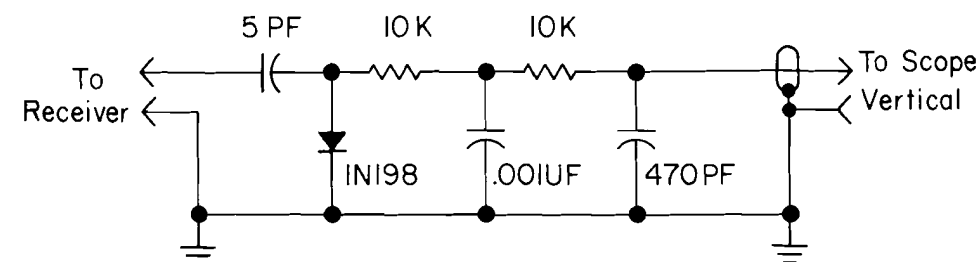
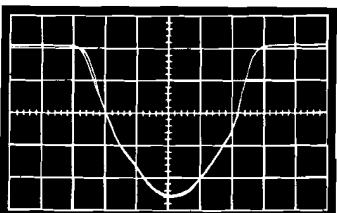


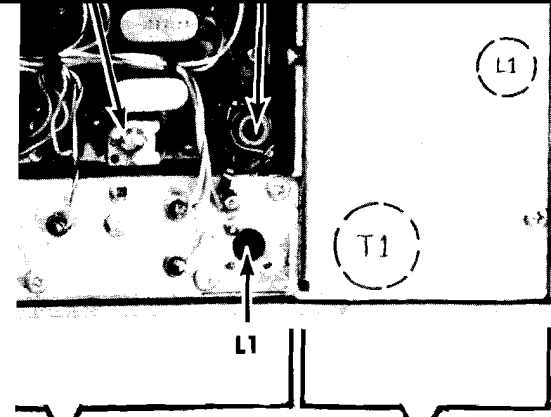
Figure 7 - Test Setup for 20-Hz Double-Trace Sweep Alignment



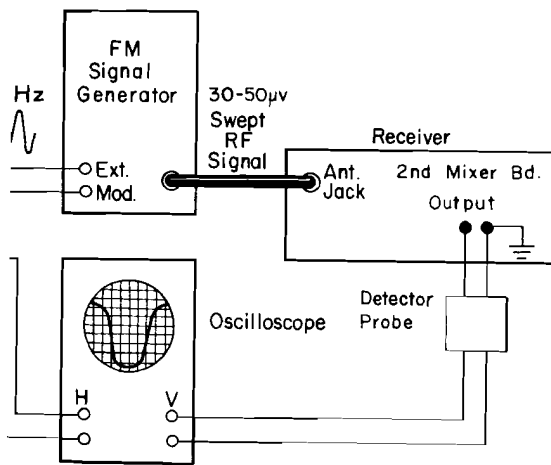
6. Disable the Channel Guard.

ALIGNMENT PROCEDURE

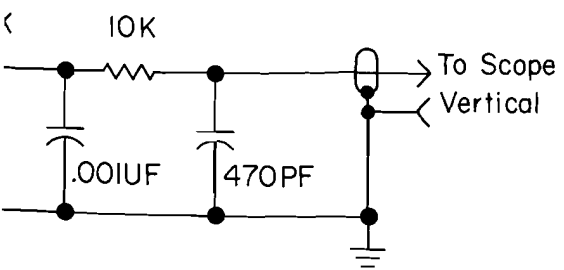
STEP	METERING POSITION		TUNING CONTROL	METER READING	PROCEDURE										
	GE Test Set or Meter Panel	Multimeter - at J442													
DISCRIMINATOR															
1.	A (DISC)	Pin 10	L1 and L2 (on IF-AUDIO SQUELCH board)	Zero	Remove three screws and swing open the IF-AUDIO & SQUELCH board. Adjust L1 (disc primary) 1/2 turn counterclockwise from the bottom of coil. Next, apply a 455-kHz signal to J2 and J4 and adjust L2 (disc secondary) for zero meter reading.										
2.	A (DISC)	Pin 10		See Procedure	Alternately apply a 450-kHz and 460-kHz signal and check for readings of at least 0.3 volt, but not more than 0.5 volt on GE Test Set. Both readings must be within .05 volt. Do not attempt to balance reading any closer than 0.05 volt.										
OSCILLATOR, MULTIPLIERS & 1ST MIXER															
3.	D (MULT-1)	Pin 4	L1 (on 1st OSC/MULT) and L1 (on 2nd MULT)	See Procedure	Tune L1 (1st OSC/MULT) for maximum meter reading. Then tune L1 (2nd MULT) for minimum meter reading.										
4.	E (MULT-2)	Pin 5	L1 (on 1st OSC/MULT) and L1, L2 and L3 (on 2nd MULT)	See Procedure	Tune L1 (1st OSC/MULT) and L1 and L2 (2nd MULT) for maximum meter reading. Then tune L3 (2nd MULT) for minimum meter reading.										
5.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal into Hole 305. Adjust the signal generator for discriminator zero.										
6.	B (2nd IF AMP)	Pin 2	L2 and L3 (on 2nd MULT) and C306 (on RF SELECTIVITY)	Maximum	Apply an on-frequency signal as above. Tune L2, L3 and C306 for maximum meter reading, keeping signal below saturation.										
7.	B (2nd IF AMP)	Pin 2	L2 and L1 (on 1st MIXER A301/A302)	Maximum	Apply an on-frequency signal into Hole 304, and tune L2 and L1 for maximum meter reading, keeping signal below saturation.										
RF SELECTIVITY															
8.	B (2nd IF AMP)	Pin 2	C305, C304, C303 and C302	Maximum	Apply an on-frequency signal in the Hole shown below, keeping the signal below saturation. Tune C302 through C305 for maximum meter reading as shown below: <table border="1" style="margin-left: auto; margin-right: auto;"> <tr> <td>Insert Generator Probe In:</td> <td>Tune</td> </tr> <tr> <td>1. Hole 304</td> <td>C305</td> </tr> <tr> <td>2. Hole 303</td> <td>C304</td> </tr> <tr> <td>3. Hole 302</td> <td>C303</td> </tr> <tr> <td>4. Hole 301</td> <td>C302</td> </tr> </table>	Insert Generator Probe In:	Tune	1. Hole 304	C305	2. Hole 303	C304	3. Hole 302	C303	4. Hole 301	C302
Insert Generator Probe In:	Tune														
1. Hole 304	C305														
2. Hole 303	C304														
3. Hole 302	C303														
4. Hole 301	C302														
9.	B (2nd IF AMP)	Pin 2	C301, C302, C303, C304, C305 and C306 (on all receivers) and T1/T2 & T3/T4 (UHS Receivers)	Maximum	Apply an on-frequency signal to the antenna jack. On UHS receivers, tune T1/T2 and T3/T4 (PREAMP) for maximum meter reading. On all receivers, tune C301 through C306 for maximum quieting.										
2ND MIXER & HI IF															
The 2nd mixer, and high IF circuits have been aligned at the factory and will normally require no further adjustment. If adjustment is necessary, use the procedure outlined in STEPS 10, 11 and 12.															
NOTE															
Refer to DATAFILE BULLETIN 1000-6 IF Alignment of Two-Way Radio FM Receivers for helpful suggestions on how to determine when IF alignment is required.															
10.	B (2nd IF AMP)	Pin 2	L3, L2, L1, T1 (2nd Mixer) and L1 (Hi IF AMP)	Maximum	Apply on-frequency, unmodulated signal and tune L3, L2, L1, T1 (2nd mixer) and L1 (Hi IF AMP) for maximum meter reading, keeping signal below saturation.										
11.			L3, L2, L1, T1 (2nd Mixer) and L1 (Hi IF AMP)		Connect scope, signal generator, and detector as shown in Figure 7. Set signal generator level for 30-50 μ v and modulate with 10 kHz. With detector at the collector of Q3 (2nd mixer board output), tune for double trace as shown on scope pattern.										
															
12.	A (DISC)	Pin 10		See Procedure	Check to see that discriminator idling voltage is within ± 0.05 volt of zero with no signal applied. Check to see that modulation acceptance bandwidth is between 7 and 9 kHz.										
FREQUENCY ADJUSTMENT															
13.	A (DISC)	Pin 10	C9 (on 1st OSC/MULT) (C10, C11 and C12 for multi-frequency)	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units tune C10, C11 or C12 as required.										
NOTE															
For proper frequency control of the receiver, it is recommended that all frequency adjustments be made with the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50° to 90°F.															



1ST MULT 2ND MIXER



10-Hz Double-Trace Sweep Alignment



or Sweep Alignment

ALIGNMENT PROCEDURE

132-174 MHz MASTR RECEIVER
 MODELS 4ER41C10-45 &
 4ER41E10-45

STEP 1

POWER OUTPUT DISTORTION

PROCEDURE

Power Output as follows:

100-microvolt, on-frequency
modulated by 1,000 hertz
frequency deviation to antenna jack

Test Speaker:

Speaker lead pin from J701-2
(Control Unit).

50-ohm load resistor from
J442-7. Connect the Distortion
Analyzer input across the resistor

OR

Turn off of the hookswitch.
Distortion Analyzer input
to J442-7.

Set VOLUME control for five-watt
RMS using the Distortion
Analyzer (VTVM).

Make measurements according
to the manufacturer's instructions. Reading
should be less than 5%. If the receiver
output is to be measured, leave
controls and equipment as they are.

SERVICE CHECK

If distortion is more than 5%, or
if the output is less than five

Then connect a milliammeter in series
with the +12 volt lead at P443-11. With
no signal in, adjust R43 for a reading
of approximately 20 milliamps. This
adjustment should not be necessary un-
less an output transistor has been re-
placed.

- G. Audio Gain (Refer to Receiver Trouble-
shooting Procedure).
- H. Discriminator Alignment (Refer to
Receiver Alignment on reverse side of
page).

STEP 2

USABLE SENSITIVITY (12-dB SINAD)

If STEP 1 checks out properly, measure
the receiver sensitivity as follows:

- A. Apply a 1000-microvolt, on-frequency
signal modulated by 1000 Hz with 3.3-kHz
deviation to J441.
- B. Place the RANGE switch on the Distortion
Analyzer in the 200 to 2000-Hz distortion
range position (1000-Hz filter in the
circuit). Tune the filter for minimum
reading or null on the lowest possible
scale (100%, 30%, etc.)
- C. Place the RANGE switch to the SET LEVEL
position (filter out of the circuit) and
adjust the input LEVEL control for a +2
dB reading on a mid range (30%).
- D. While reducing the signal generator out-
put, switch the RANGE control from SET
LEVEL to the distortion range until a
12-dB difference (+2 dB to -10 dB) is
obtained between the SET LEVEL and
distortion range positions (filter out
and filter in).

- F. Leave all controls as they are and all
equipment connected if the Modulation
Acceptance Bandwidth test is to be per-
formed.

SERVICE CHECK

If the sensitivity level is more than rated
12 dB SINAD, check the alignment of the RF stages
as directed in the Alignment Procedure, and make
the gain measurements as shown on the Trouble-
shooting Procedure.

STEP 3

MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH)

If STEPS 1 and 2 check out properly,
measure the bandwidth as follows:

- A. Set the Signal Generator output for twice
the microvolt reading obtained in the
12-dB SINAD measurement.
- B. Set the RANGE control on the Distortion
Analyzer in the SET LEVEL position (1000-
Hz filter out of the circuit), and adjust
the input LEVEL control for a +2 dB read-
ing on the 30% range.
- C. While increasing the deviation of the
Signal Generator, switch the RANGE con-
trol from SET LEVEL to distortion range
until a 12-dB difference is obtained
between the SET LEVEL and distortion range
readings (from +2 dB to -10 dB).
- D. The deviation control reading for the
12-dB difference is the Modulation
Acceptance Bandwidth of the receiver.
It should be more than ± 7 kHz (but less
than ± 9 kHz).

TEST PROCEDURES

These Test Procedures are designed to help you to service a receiver that is operating---but not properly. The problems encountered could be low power, poor sensitivity, distortion, limiter not operating properly, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized. Once

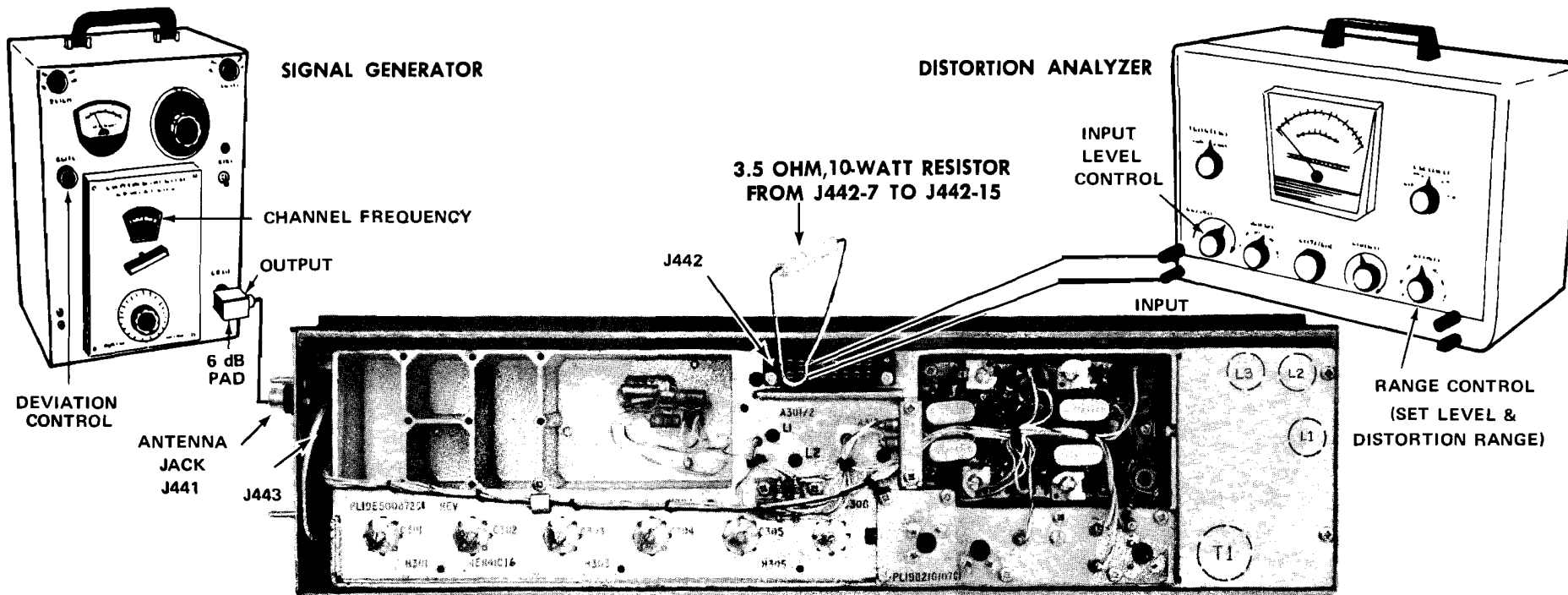
the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

TEST EQUIPMENT REQUIRED

- Distortion Analyzer similar to: Heath IM-12
- Signal Generator similar to: Measurements M-560
- 6-dB attenuation pad, and 3.5-ohm, 10-watt resistor

PRELIMINARY ADJUSTMENTS

1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure.
2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
3. Turn on all of the equipment and let it warm up for 20 minutes.



COMPONENT TOP VIEW

REMOVE THREE SCREWS AND SWING BOARD OPEN

CONTROL UNIT
REAR

SPEAKER

AUDIO
AN

TE

Measure Audio 1

A. Apply a 1
test signa
with ± 3.3
J441.

B. With Five-

Disconnect
(on rear)

Connect a
J442-15 to
tion Analy
as shown.

With Handset:

Lift the h
Connect th
from J442-

C. Adjust the
output (4.
Analyzer a

D. Make disto
to manufac
should be
sensitivity
all contro

S

If the dis
maximum a

STEP 1-QUICKCHECKS

TEST SET CHECKS

These checks are typical voltage readings measured with GE Test Set Model 4EX3A10 in the Test 1 position, or Model 4EX8K10 or 11 in the 1-volt position.

Metering Position	Reading with No Signal in	Reading with 1 μ v unmodulated input
A Disc idling	Less than ± 0.05 VDC	
B 2nd IF	.05 VDC	0.2 VDC
C 1st Lim	0.6 VDC	0.8 VDC
D Mult 1	0.7 VDC	
E Mult 2	1 VDC	
J Regulated +10 Volts	10 VDC	

SYMPTOM CHECKS

SYMPTOM	PROCEDURE
NO SUPPLY VOLTAGE	<ul style="list-style-type: none"> Check power connections and continuity of supply leads, and check fuse in power supply. If fuse is blown, check receiver for short circuits.
NO REGULATED 10-VOLTS	<ul style="list-style-type: none"> Check the 12-volt supply. Then check regulator circuit (See Troubleshooting Procedure for Power Supply).
LOW 1ST LIM READING	<ul style="list-style-type: none"> Check supply voltages and then check oscillator reading at J442-4 & 5 as shown in STEP 2A. Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 1st Limiter stages as shown in STEP 2A.
LOW OSCILLATOR/MULTIPLIER READINGS	<ul style="list-style-type: none"> Check alignment of Oscillator (Refer to Front End Alignment Procedure). Check voltage and resistance readings of 1st Oscillator/Multiplier Q1/Q2. Check crystal Y1.
LOW RECEIVER SENSITIVITY	<ul style="list-style-type: none"> Check Front End Alignment (Refer to Receiver Alignment Procedure). Check antenna connections, cable and relay. Check 1st and 2nd Oscillator injection voltage. Check voltage and resistance readings of 1st Mixer, HI IF Amp and 2nd Mixer. Make SIMPLIFIED GAIN CHECKS (STEP 2A).
LOW AUDIO	<ul style="list-style-type: none"> Check Audio PA (Q301 & Q302) voltage readings on schematic diagram. Make simplified gain and waveform checks of audio and squelch stages (Steps 2A and 2B). Make unsquelched voltage readings in Audio section (Refer to Receiver Schematic Diagram). Check voltage and resistance readings on Channel Guard board.
HIGH DISTORTION AT LOW AUDIO LEVELS (50 MW)	<ul style="list-style-type: none"> Set PA bias adjust R43 as specified under Service. Checks in STEP 1 of TEST PROCEDURES.
IMPROPER SQUELCH OPERATION	<ul style="list-style-type: none"> Check voltage and resistance readings of Squelch circuit (Refer to Receiver Schematic Diagram). Make gain and waveform checks of audio and squelch stages (Steps 2A and 2B).
DISCRIMINATOR IDLING TOO FAR OFF ZERO	<ul style="list-style-type: none"> See if discriminator zero is in center of IF bandpass.

STEP 3-V

EQUIPMENT REQUIREMENTS

1. RF Voltmeter
Millivac Type
2. Signal generator
Correct frequency
the discriminator
3.3 kHz deviation

PROCEDURE

1. Apply probe
negative (-10 V)
2. Move probe
system negative
3. Convert reading
formula:

Voltage
4. Check results
on diagram.

STEP 3-VOLTAGE RATIO READINGS →

EQUIPMENT REQUIRED:

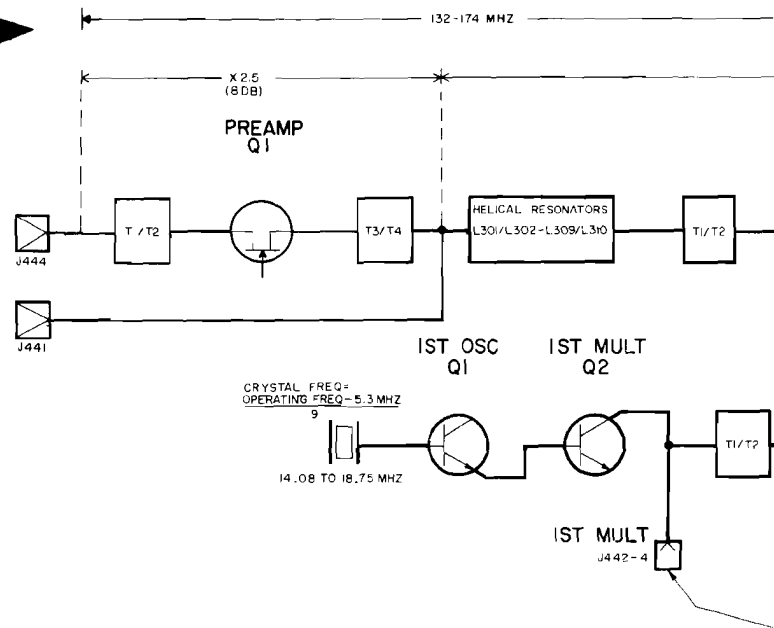
1. RF Voltmeter (Similar to Boonton Model 91-CA or Millivac Type MV-18 C).
2. Signal on receiver frequency (below saturation). Correct frequency can be determined by zeroing the discriminator. Use 1,000 Hertz signal with 3.3 kHz deviation for audio stage.

PROCEDURE

1. Apply probes to input of stage and system negative (-10 VDC). Take voltage reading (E_1).
2. Move probes to input of following stage and system negative. Take reading (E_2).
3. Convert readings by means of the following formula:

$$\text{Voltage Ratio} = \frac{E_2}{E_1}$$

4. Check results with typical voltage ratios shown on diagram.



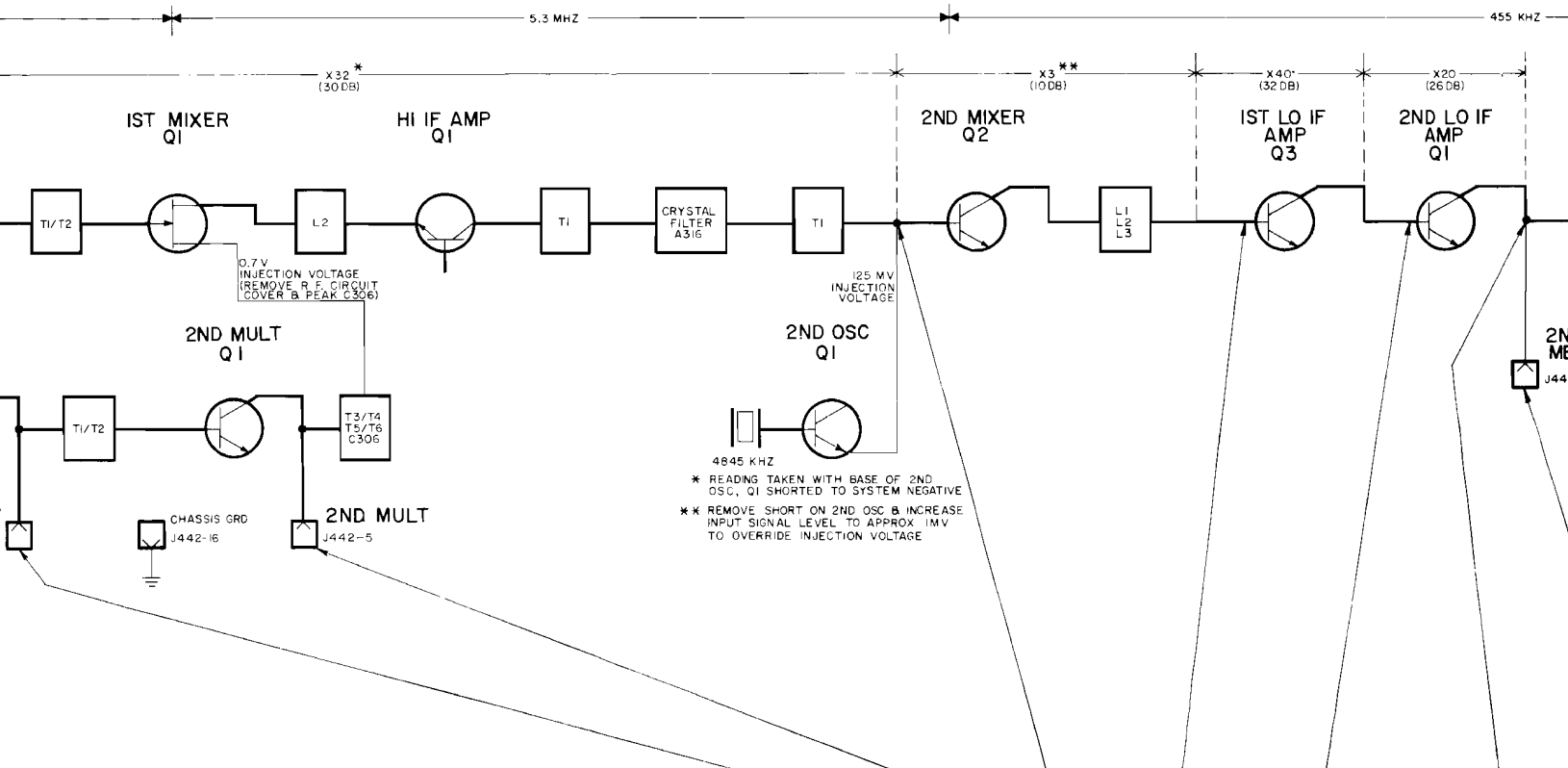
STEP 2A-SIMPLIFIED VTVM

EQUIPMENT REQUIRED:

1. VTVM-AC & DC
2. Signal Generator (measurements M560)

PRELIMINARY STEPS:

1. Set VOLUME control for 4.18 volts across load. If this cannot be obtained, set 70% of max. rotation.
2. Set SQUELCH control fully counterclockwise.
3. Receiver should be properly aligned.
4. Connect VTVM between system negative indicated by arrow (except for 1st and 2nd stages which reference chassis ground).



VTVM GAIN CHECKS

SIGNAL GENERATOR INPUT AT J44) MAINTAIN SETTING AT DISCRIMINATOR ZERO			UNMODULATED	UNMODULATED	UNMODULATED	UNMODULATED
PROCEDURE			INCREASE GENERATOR OUTPUT UNTIL VTVM READING ON 1.5 V SCALE DECREASES BY 50 MV	INCREASE SIGNAL GENERATOR OUTPUT FROM ZERO UNTIL VTVM READING DECREASES BY 5%	INCREASE SIGNAL GENERATOR OUTPUT FROM ZERO UNTIL VTVM READING DECREASES BY 5%	INCREASE SIGNAL GENERATOR OUTPUT FROM ZERO UNTIL VTVM READING DECREASES BY 5%
READING	5 VDC GE TEST SET (POS D, 0.7V)	2.5 VDC GE TEST SET (POS E 1V)	GENERATOR OUTPUT SHOULD BE APPROX 20 MILLIVOLTS	GENERATOR OUTPUT SHOULD BE APPROX 600 MICROVOLTS	GENERATOR OUTPUT SHOULD BE APPROX 5 MICROVOLTS	GENERATOR OUTPUT SHOULD BE APPROX 0.3 MICROVOLTS

ents M560 or equiv.)

8 volts across 3.5-ohm
obtained, set to approx.

counterclockwise.

y aligned.

m negative and points
for 1st and 2nd MULT
ound).

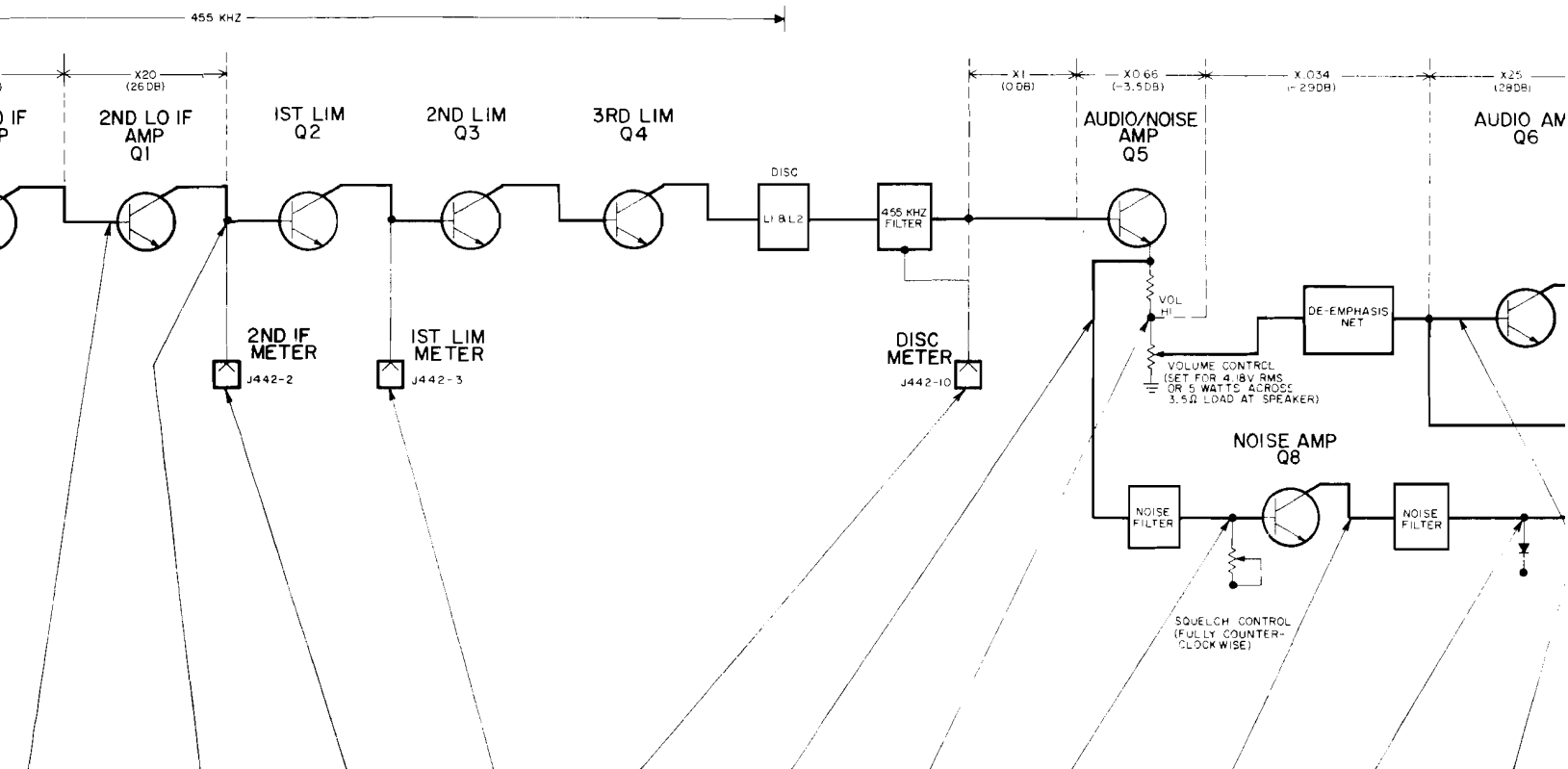
STEP 2B-AUDIO & SQUELCH WAVEFORMS

EQUIPMENT REQUIRED:

1. Oscilloscope.
2. Signal generator (measurements M560 to equivalent).

PRELIMINARY STEPS:

1. Set VOLUME control for 4.18 volts across 3.5-ohm load. If this cannot be obtained, set to approx. 70% of max. rotation.
2. Set SQUELCH control fully counterclockwise.
3. Receiver should be properly aligned.
4. Connect oscilloscope between system negative and points indicated by arrow.



UNMODULATED	UNMODULATED	1 MICROVOLT UNMODULATED	NO SIGNAL INPUT	STANDARD SIGNAL-1 (1 MILLIVOLT AT RECEIVER FREQ. MODULATED BY 1KHZ WITH 3.3 KHZ DEVIATION)	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL
INCREASE SIGNAL GENERATOR OUTPUT FROM ZERO UNTIL VTVM READING DECREASES BY 5%	INCREASE SIGNAL GENERATOR OUTPUT FROM ZERO UNTIL VTVM READING DECREASES BY 5%									
GENERATOR OUTPUT SHOULD BE APPROX 0.3 MICROVOLTS	GENERATOR OUTPUT SHOULD BE APPROX 0.3 MICROVOLTS	-0.6 VDC GE TEST SET (POS B 0.3V)	-2 VDC GE TEST SET (POS C 0.6V)	0.8 VAC	0.75 VAC	0.55 VAC	0.15 VAC	2.3 VAC	0.05 VAC	

SCOPE SETTING	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV
	1 VOLT/DIV	1 VOLT/DIV	1 VOLT/DIV	2 VOLTS/DIV	0.5 VOLTS/DIV	50 MILLIVOLTS/DIV
	2 V P-P	1.4 V P-P	1 V P-P (NOISE)	5.7 V P-P (NOISE)	3 V P-P (NOISE)	0.1 V P-P
STANDARD SIGNAL (1 MILLIVOLT AT RECEIVER FREQ. MODULATED BY 1KHZ WITH 3.3 KHZ DEVIATION)						
NOISE WAVE FORM (NO SIGNAL INPUT)						

WAVEFORMS →

(M560 to equivalent).

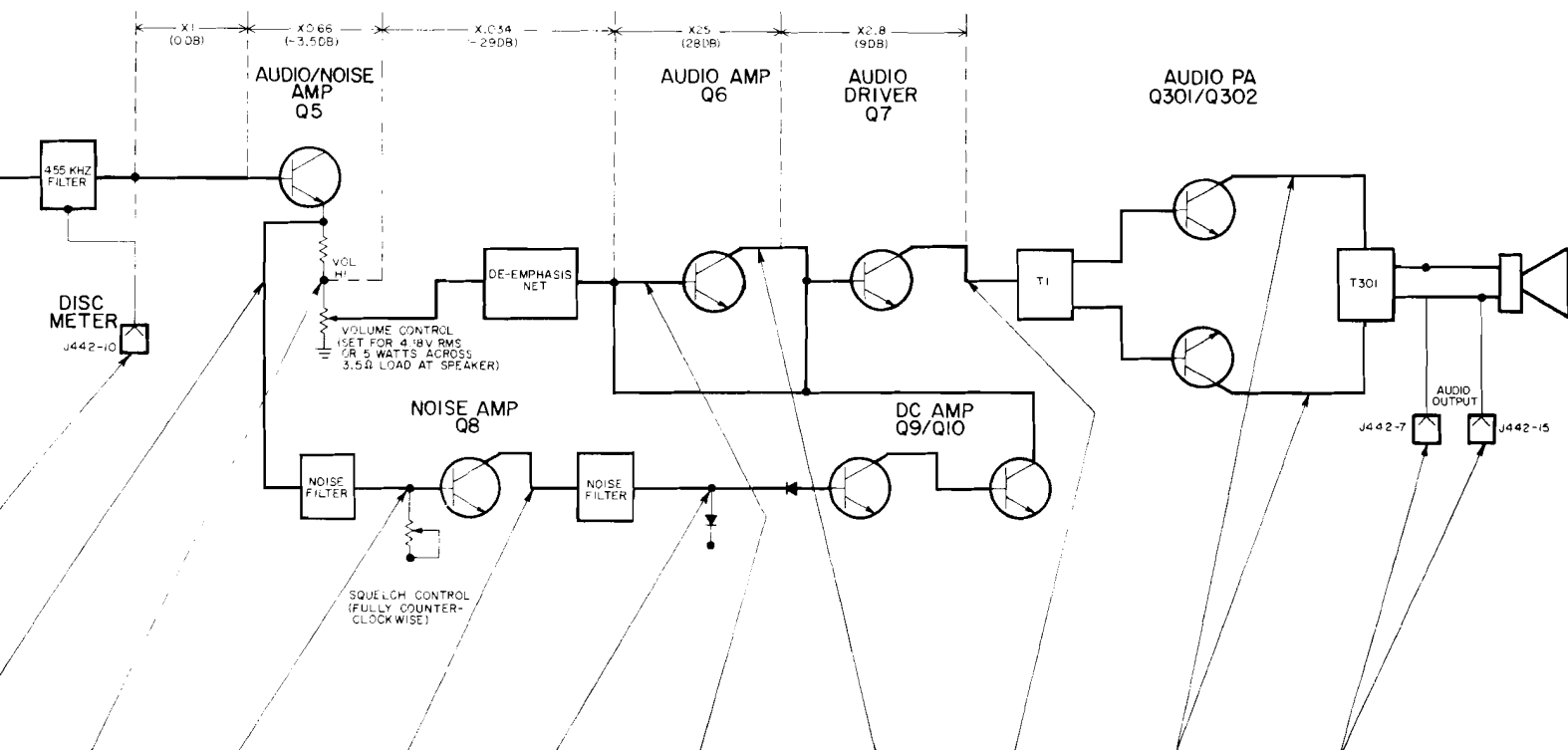
(RC-1633B)

across 3.5-ohm load, set to approx.

erclockwise.

igned.

stem negative and



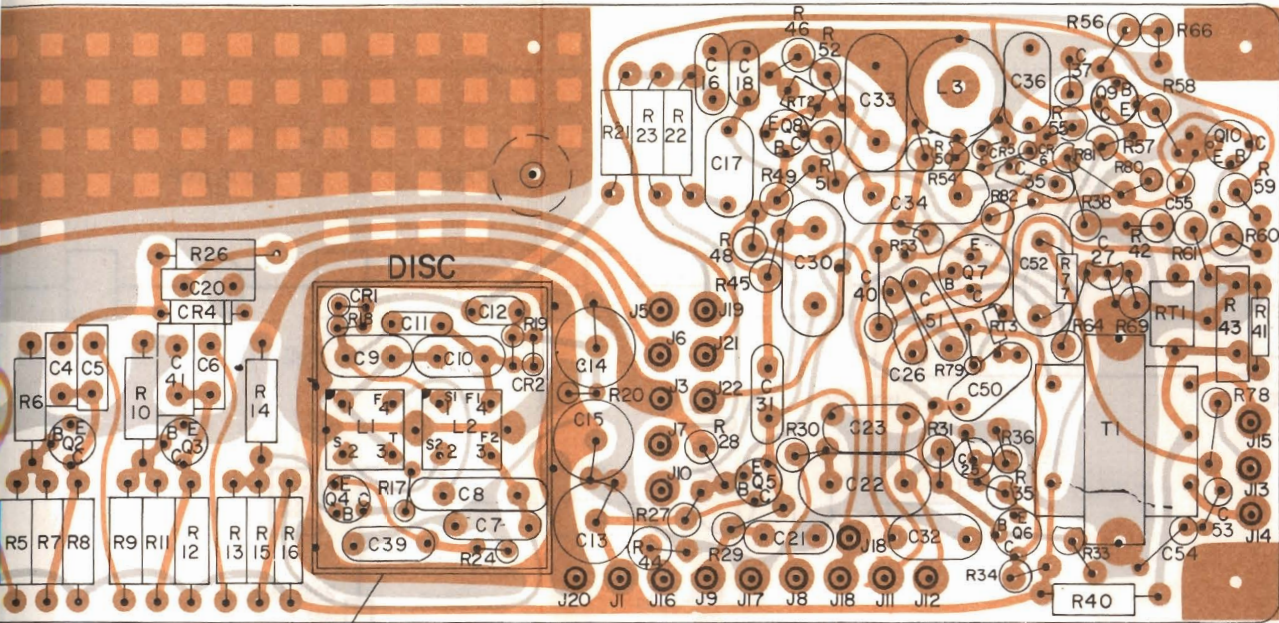
STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL	STANDARD SIGNAL
0.55 VAC	0.15 VAC	2.3 VAC	0.05 VAC		0.5 VAC	1.4 VAC	10 VAC	4.18 VAC

0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV
1 VOLT/DIV	1 VOLT/DIV	2 VOLTS/DIV	0.5 VOLTS/DIV	50 MILLIVOLTS/DIV	1 VOLT/DIV	2 VOLTS/DIV	10 VOLTS/DIV	5 VOLTS/DIV
1.4 V P-P	1 V P-P (NOISE)	5.7 V P-P (NOISE)	3 V P-P (NOISE)	0.1 V P-P	1.9 V P-P	4 V P-P	30 V P-P	12 V P-P

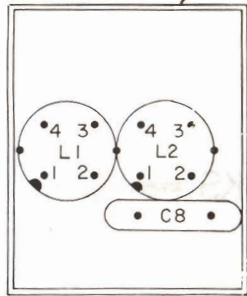
TROUBLE SHOOTING PROCEDURE

132—174 MHz MASTR RECEIVER
 MODELS 4ER41C10-45 & 4ER41E10-45

**IF-AUDIO & SQUELCH BOARD
A318**



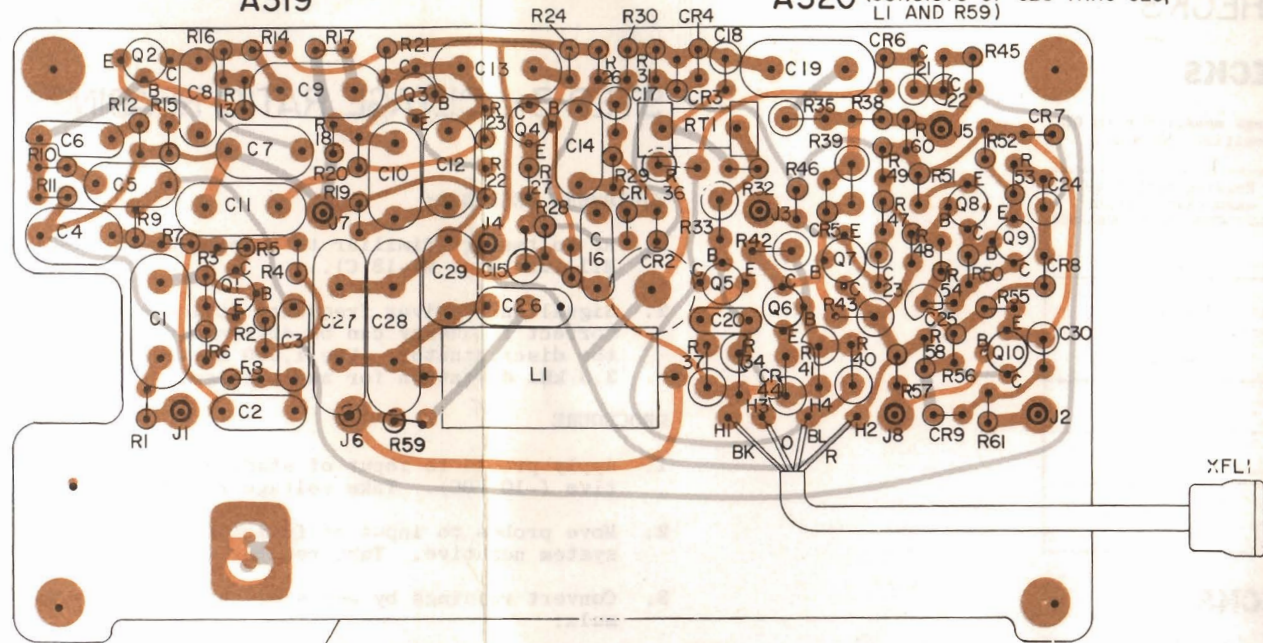
(19C311803, Sh. 1, Rev. 3)
(19C311803, Sh. 2, Rev. 5)



ALTERNATE L1 & L2

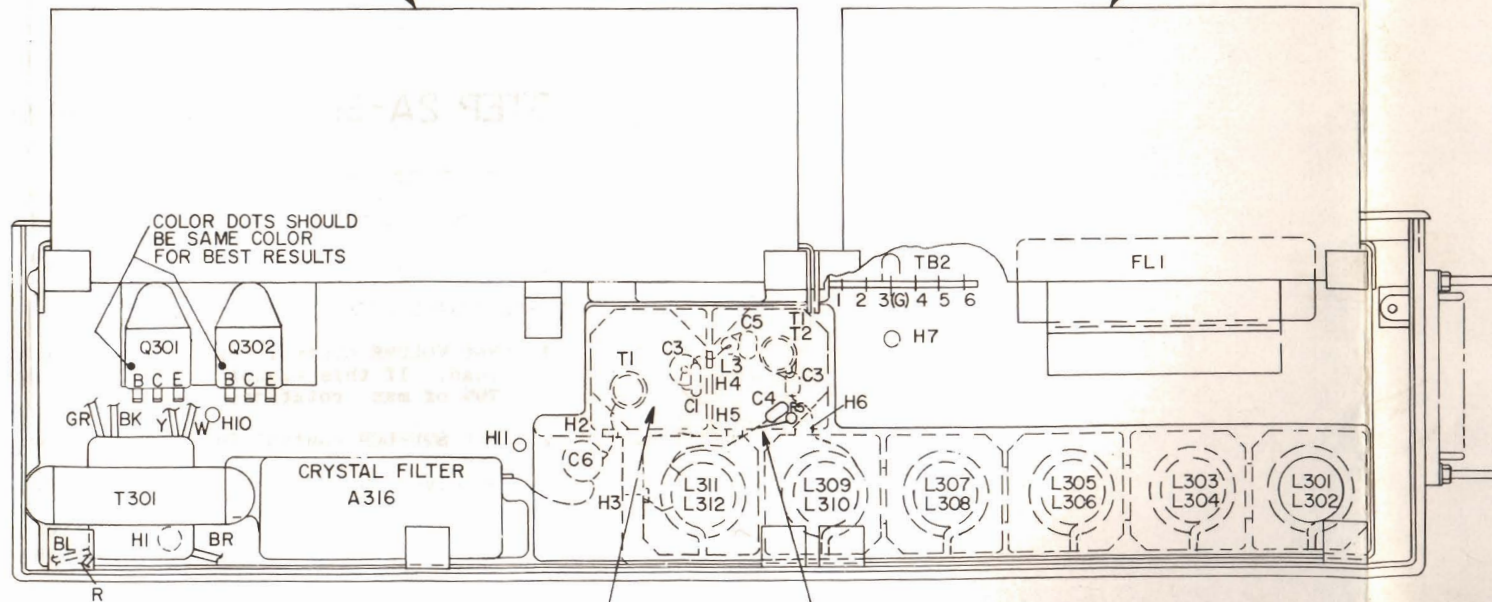
PIN NUMBER MARKING ON SIDE OF CAN OR COLOR DOT IDENTIFIES PIN NUMBER 1 ON DISCRIMINATOR AND 2ND MIXER COILS.

**ENCODER-DECODER
A319**



(19C311794, Sh. 1, Rev. 3)
(19C311794, Sh. 2, Rev. 3)

BOTTOM VIEW

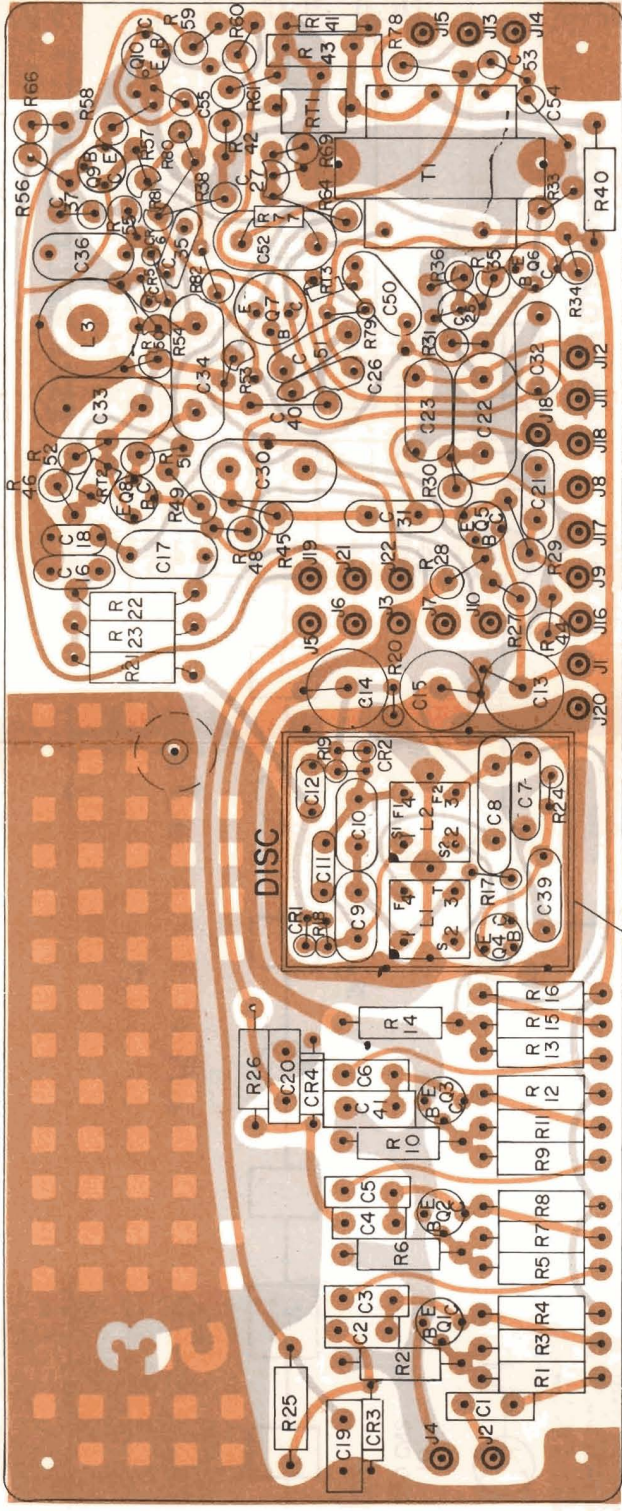


COLOR DOTS SHOULD BE SAME COLOR FOR BEST RESULTS

HI IF AMP

1ST MIXER

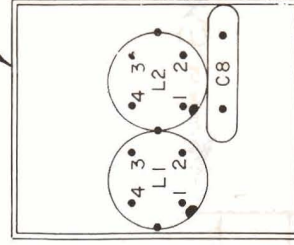
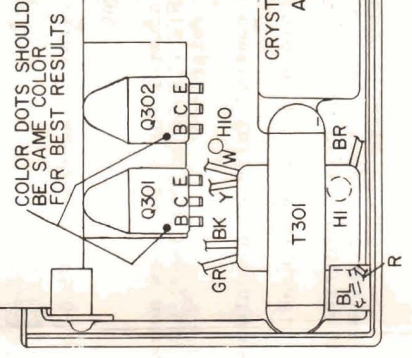
IF-AUDIO & SQUELCH BOARD
A318



BOTTOM VIEW

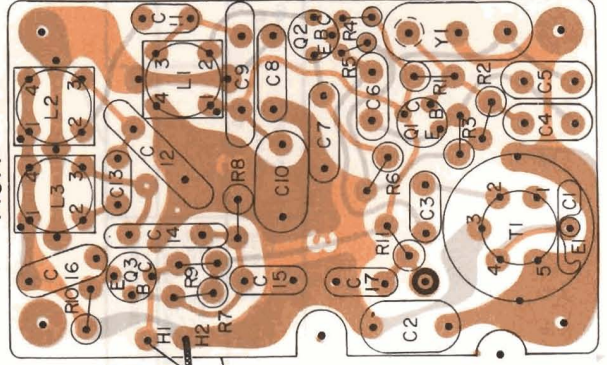
(19C311803, Sh. 1, Rev. 3)
(19C311803, Sh. 2, Rev. 5)

COLOR DOTS SHOULD
BE SAME COLOR
FOR BEST RESULTS



ALTERNATE L1 & L2
PIN NUMBER MARKING
ON SIDE OF CAN OR
COLOR DOT IDENTIFIES
PIN NUMBER 1 ON
DISCRIMINATOR AND 2 ND
MIXER COILS.

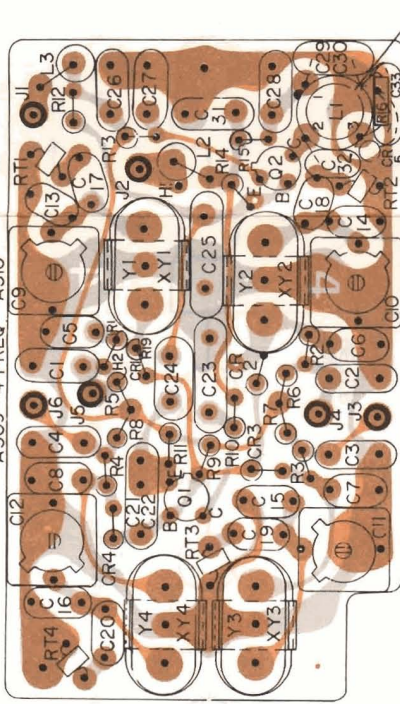
2ND MIXER
A317



(19B216045, Sh. 1, Rev. 3)
(19B216045, Sh. 2, Rev. 3)

1ST OSCILLATOR

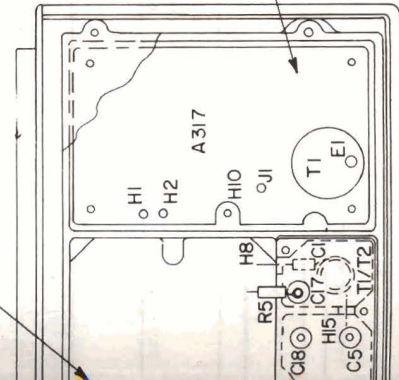
132-150.8MHZ 150.8-174MHZ
A305- 1 FREQ - A306
A307- 2 FREQ - A308
A309- 4 FREQ - A310



(19B204412, Sh. 1, Rev. 4)
(19B204412, Sh. 2, Rev. 4)

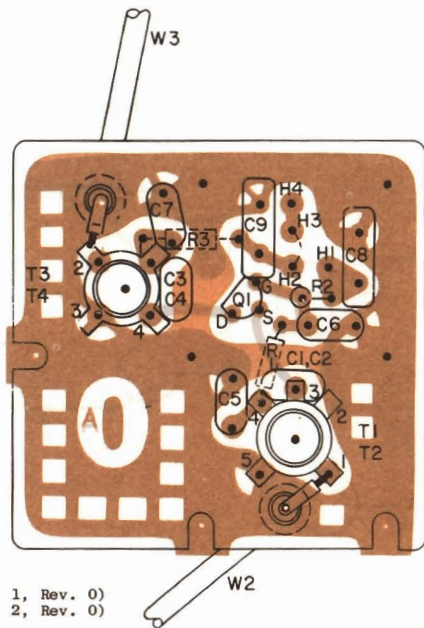
TO A318-J4

TO A318-J2



MULTIPLIER
32-150.8MHZ
50.8-174MHZ

PREAMP (UHS)
A321/A322

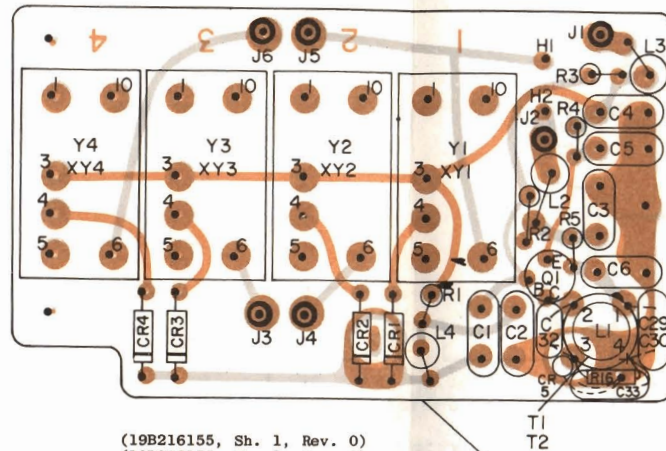


1ST OSC/MULT (WITH ICOM)

132-150.8 MHZ 150.8-174 MHZ

A311 - 1 FREQ - A313

A312 - MULTI FREQ - A314



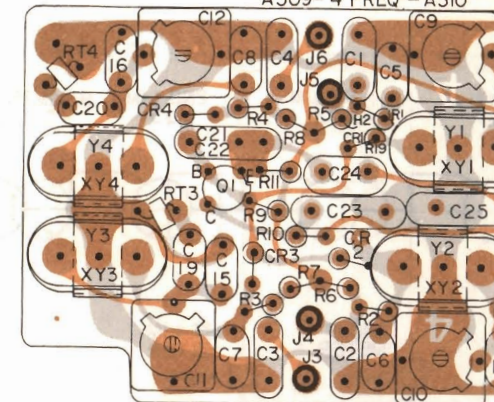
1ST OSCILLATOR

132-150.8 MHZ 150.8-174 MHZ

A305- 1 FREQ - A306

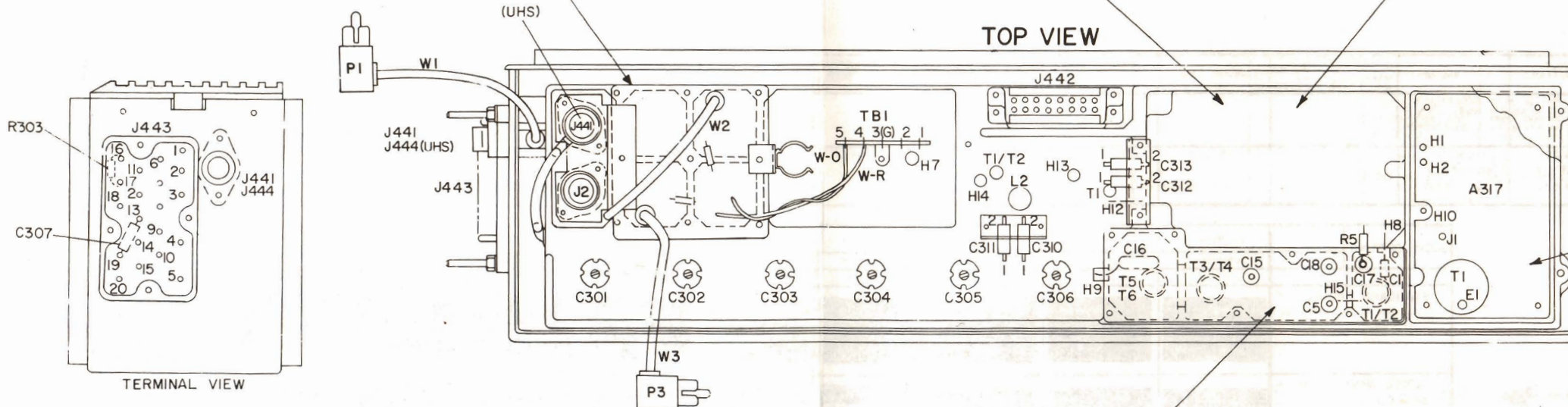
A307- 2 FREQ - A308

A309- 4 FREQ - A310



(19A127449, Sh. 1, Rev. 0)
(19A127449, Sh. 2, Rev. 0)

TOP VIEW



2ND MULTIPLIER
A303 (132-150.8 MHZ)
A304 (150.8-174 MHZ)

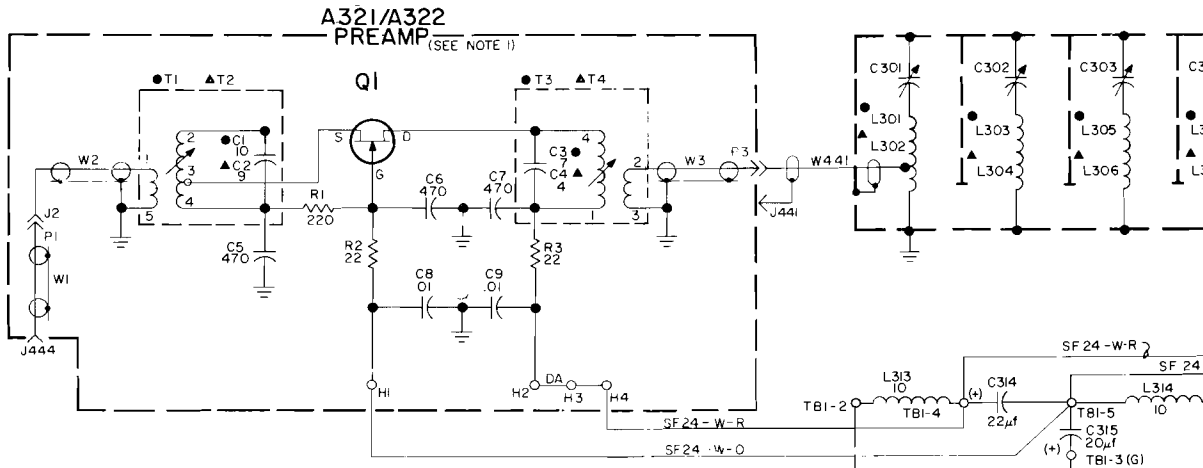


MODEL NUMBER	FREQ RANGE	NO FREQ	WITH CHAN GD	UHS WITH PREAMP
4ER4IC10	132-150.8	1		
4ER4IC11	150.8-174	1		
4ER4IC12	132-150.8	2		
4ER4IC13	150.8-174	2		
4ER4IC14	132-150.8	4		
4ER4IC15	150.8-174	4		
4ER4IC16	132-150.8	1	X	
4ER4IC17	150.8-174	1	X	
4ER4IC18	132-150.8	2	X	
4ER4IC19	150.8-174	2	X	
4ER4IC20	132-150.8	4	X	
4ER4IC21	150.8-174	4	X	
4ER4IC34	132-150.8	1		X
4E14IC35	150.8-174	1		X
4ER4IC36	132-150.8	2		X
4ER4IC37	150.8-174	2		X
4ER4IC38	132-150.8	4		X
4ER4IC39	150.8-174	4		X
4ER4IC40	132-150.8	1	X	X
4ER4IC41	150.8-174	1	X	X
4ER4IC42	132-150.8	2	X	X
4ER4IC43	150.8-174	2	X	X
4ER4IC44	132-150.8	4	X	X
4ER4IC45	150.8-174	4	X	X
4ER4IE10	132-150.8	1		
4ER4IE11	150.8-174	1		
4ER4IE14	132-150.8	4		
4ER4IE15	150.8-174	4		
4ER4IE16	132-150.8	1	X	
4ER4IE17	150.8-174	1		
4ER4IE20	132-150.8	4	X	
4ER4IE21	150.8-174	4		
4ER4IE34	132-150.8	1		X
4ER4IE35	150.8-174	1		X
4ER4IE38	132-150.8	4		X
4ER4IE39	150.8-174	4		X
4ER4IE40	132-150.8	1	X	X
4ER4IE41	150.8-174	1	X	X
4ER4IE44	132-150.8	4	X	X
4ER4IE45	150.8-174	4	X	X

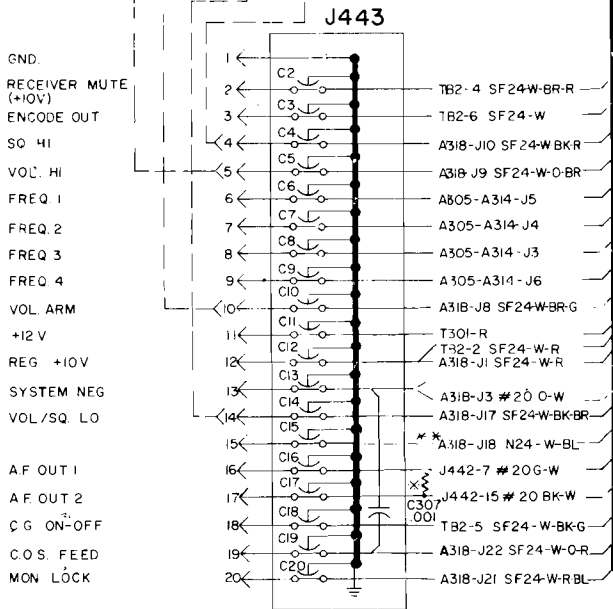
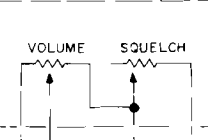
NOTE 1:
 1. PRE-AMP A321/A322 IS PRESENT ONLY IN UHS RECEIVER MODELS SHOWN IN TABLE IN UHS RECEIVERS J444 IS THE ANTENNA INPUT JACK AND J441 CONNECTS THE PRE-AMP OUTPUT TO THE RECEIVER. IN NON-UHS RECEIVERS, J441 IS THE ANTENNA INPUT JACK. TO BYPASS PRE-AMP, CONNECT P1 TO J441. PLACE UNUSED P3 IN PLUG HOLDER CLIP.

REVISION LETTER BLOCK

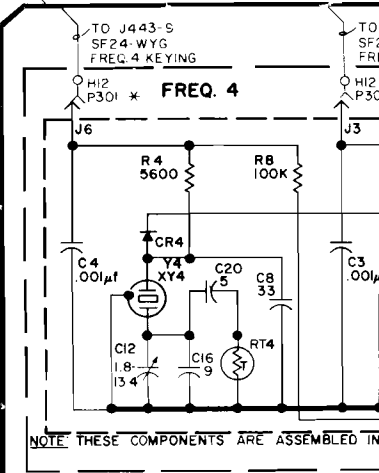
	REV
PL19E500872G1	J
PL19E500872G2	K
PL19B21619G1	A
PL19D413129G1	H
4EK16A10	C
PL19C311797G2	A
PL19A127479G1	
PL19A127479G2	A



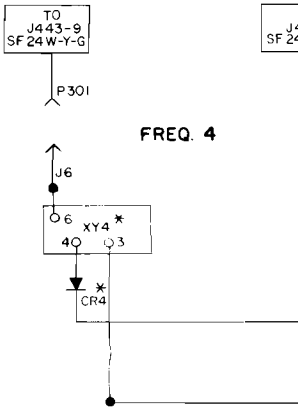
TYP VOL & SQ CONNECTION



XR303 (39~1W)

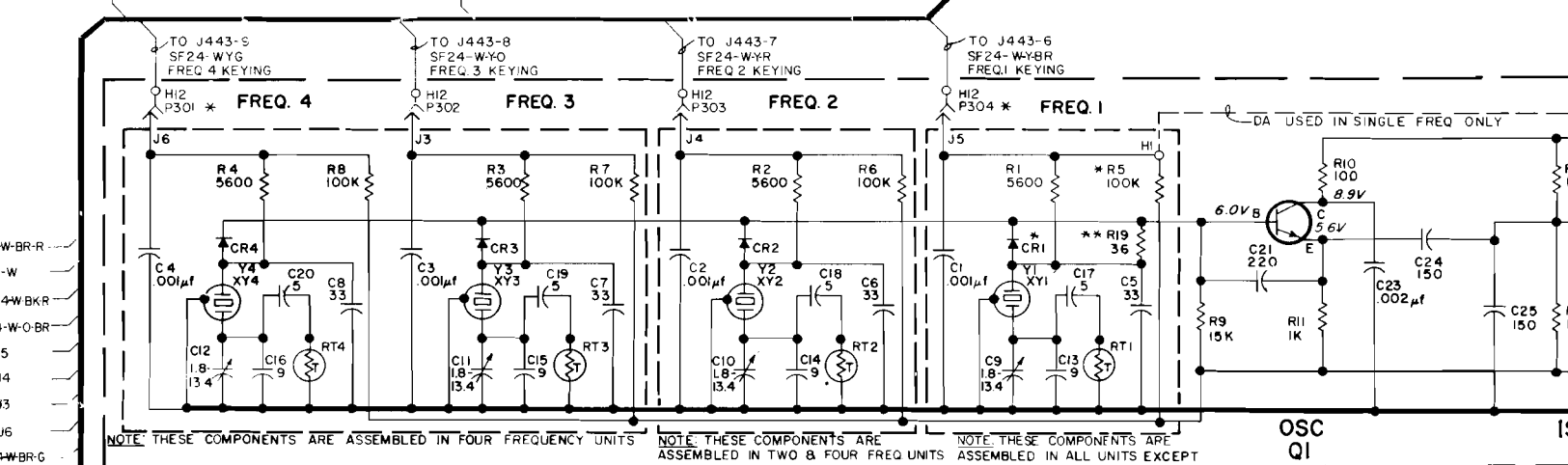
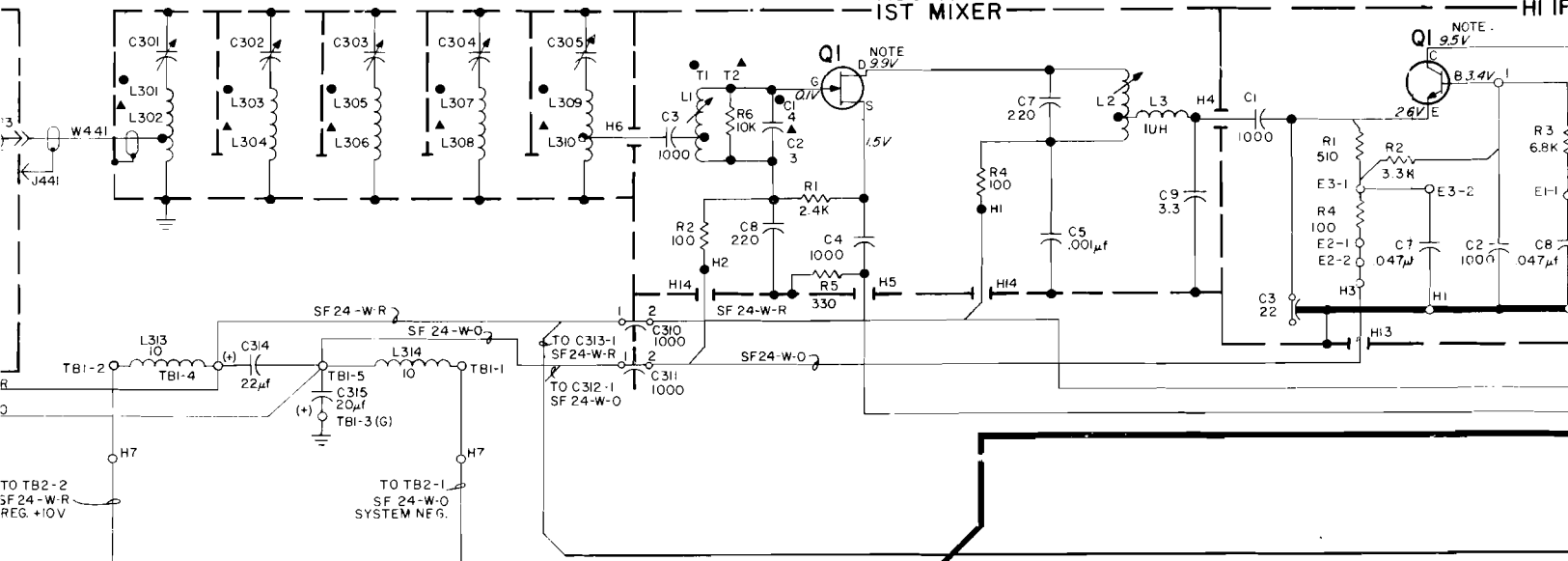


NOTE: THESE COMPONENTS ARE ASSEMBLED IN...



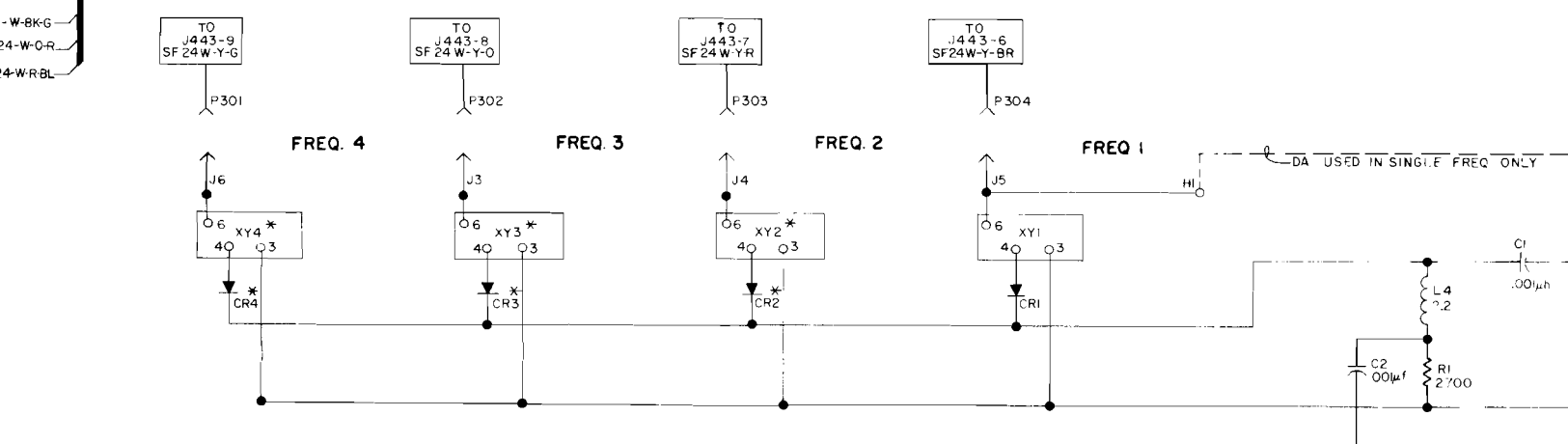
* USED ONLY FOR MU...
 ▲ 150.8-174 MHZ
 ● 132-150.8 MHZ

A301/A302
1ST MIXER



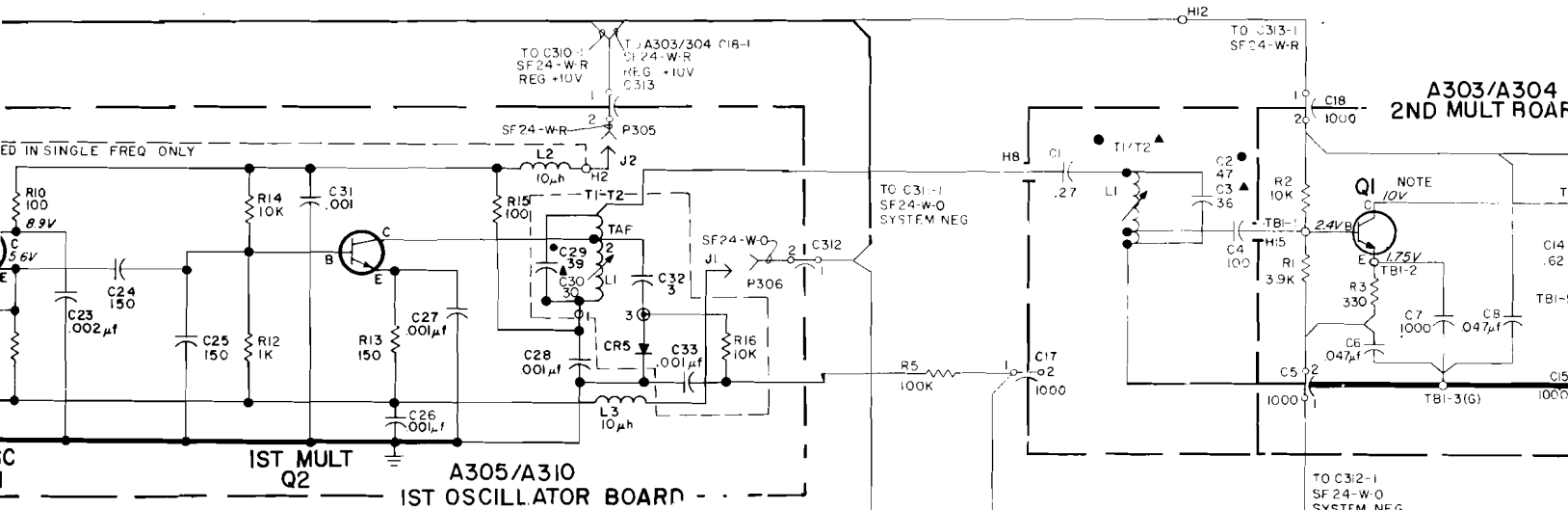
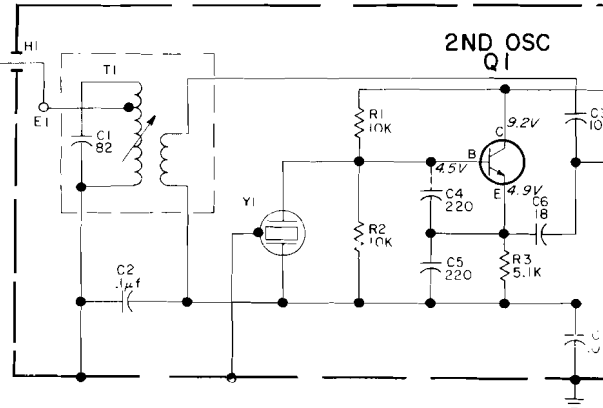
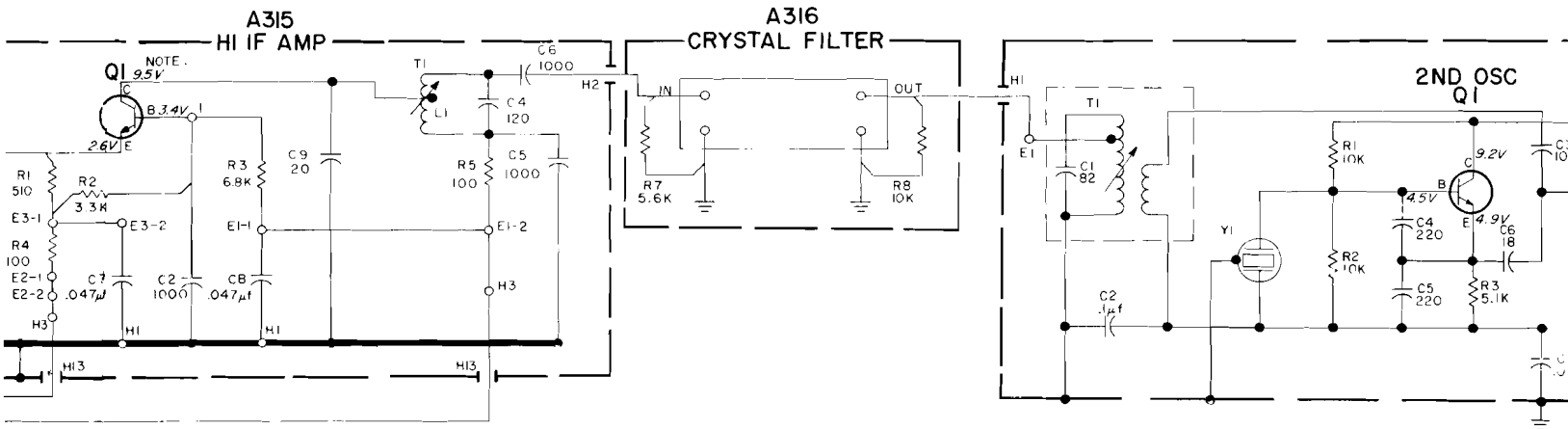
NOTE: THESE COMPONENTS ARE ASSEMBLED IN FOUR FREQUENCY UNITS NOTE: THESE COMPONENTS ARE ASSEMBLED IN TWO & FOUR FREQ UNITS NOTE: THESE COMPONENTS ARE ASSEMBLED IN ALL UNITS EXCEPT OSC Q1

* FOR SINGLE FREQ. OPERATION WIRE W-Y-BR TO J6 AND W-Y-G TO J5 * PARTS MARKED WITH *B* * * NOT USED IN SINGLE FREQ. UNITS. ** USED ONLY IN SINGLE FREQ. UNITS.



* USED ONLY FOR MULTI-FREQ
 ▲ 150.8-174 MHz
 ● 132-150.8 MHz

	REV
A301	P L19B21617BG1
A302	P L19B21617BG2
A303	P L19B21617BG3
A304	P L19B21617BG4

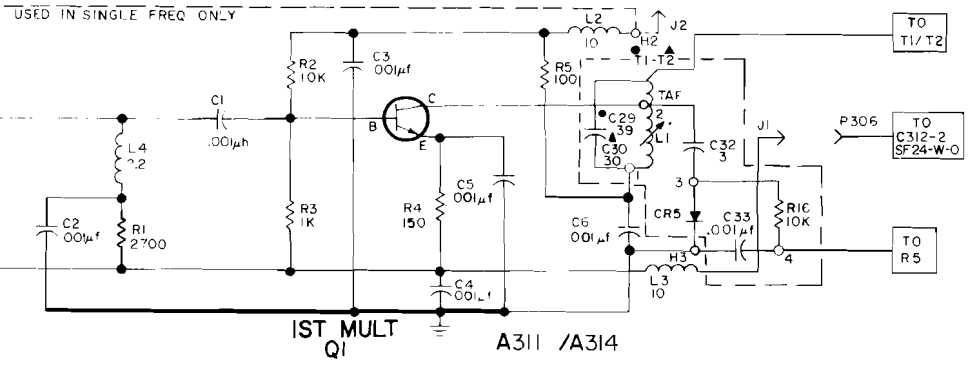


(19D402944, Rev. 3)

		REV
A 305	PL19B204419G1	B
A 306	PL19B204419G4	B
A 307	PL19B204419G2	
A 308	PL19B204419G5	
A 309	PL19B204419G3	
A 310	PL19B204419G6	

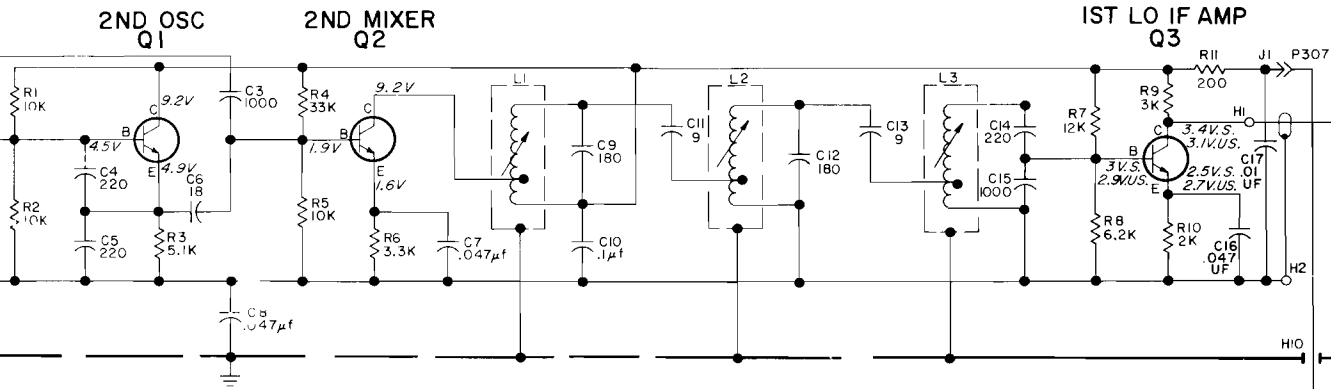
TO J442-4 SF 24 W-G-BL MULTIPLIER 1 METER

(19R621220, Rev. 33)

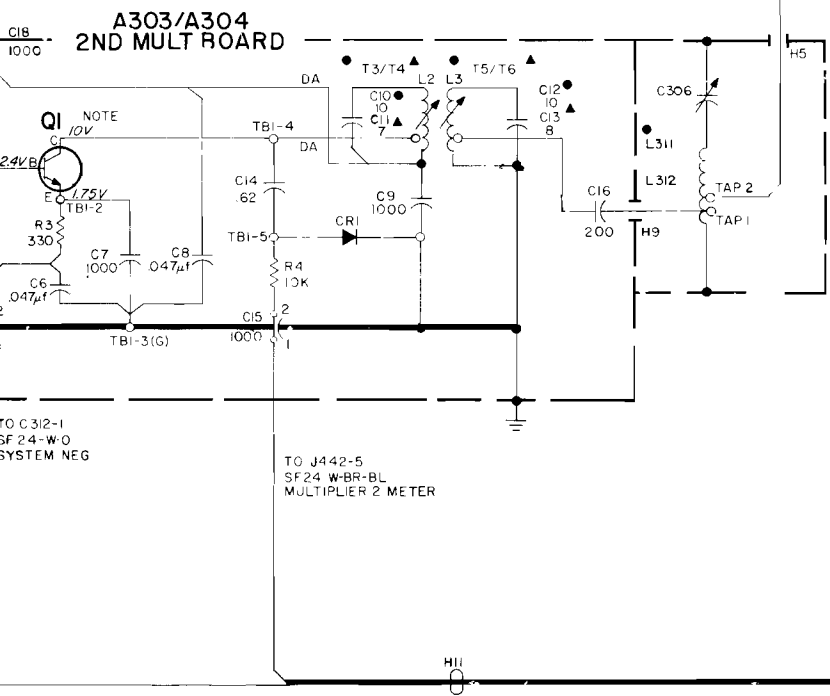


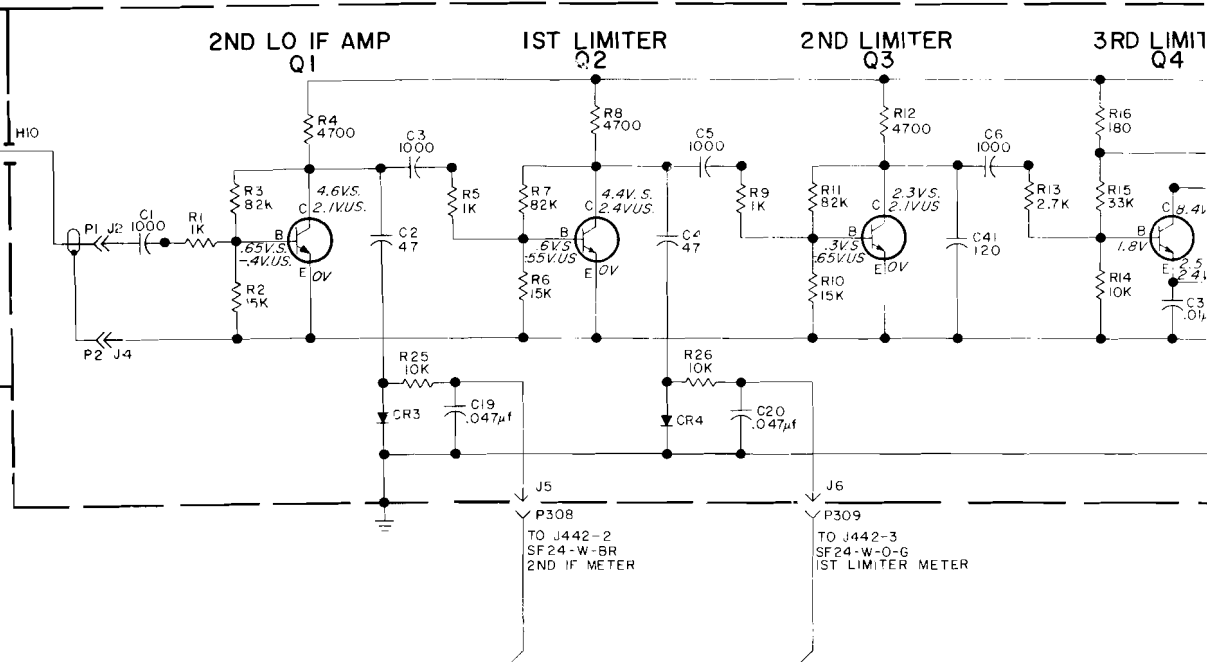
113030, Rev. 2)

A317
2ND MIXER BOARD

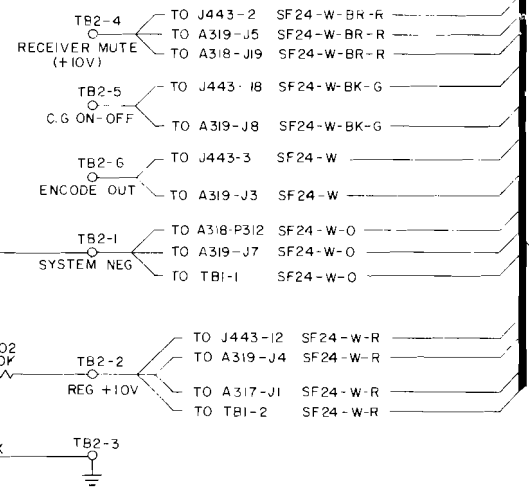
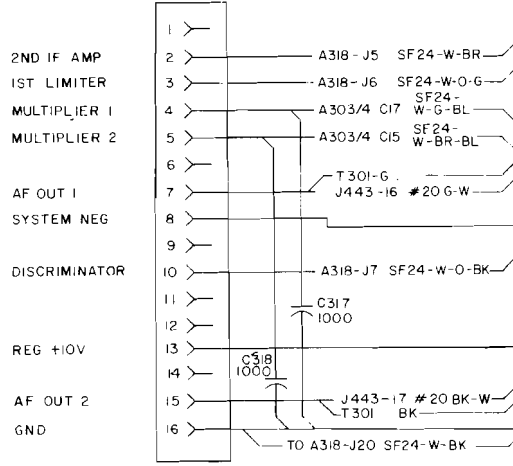


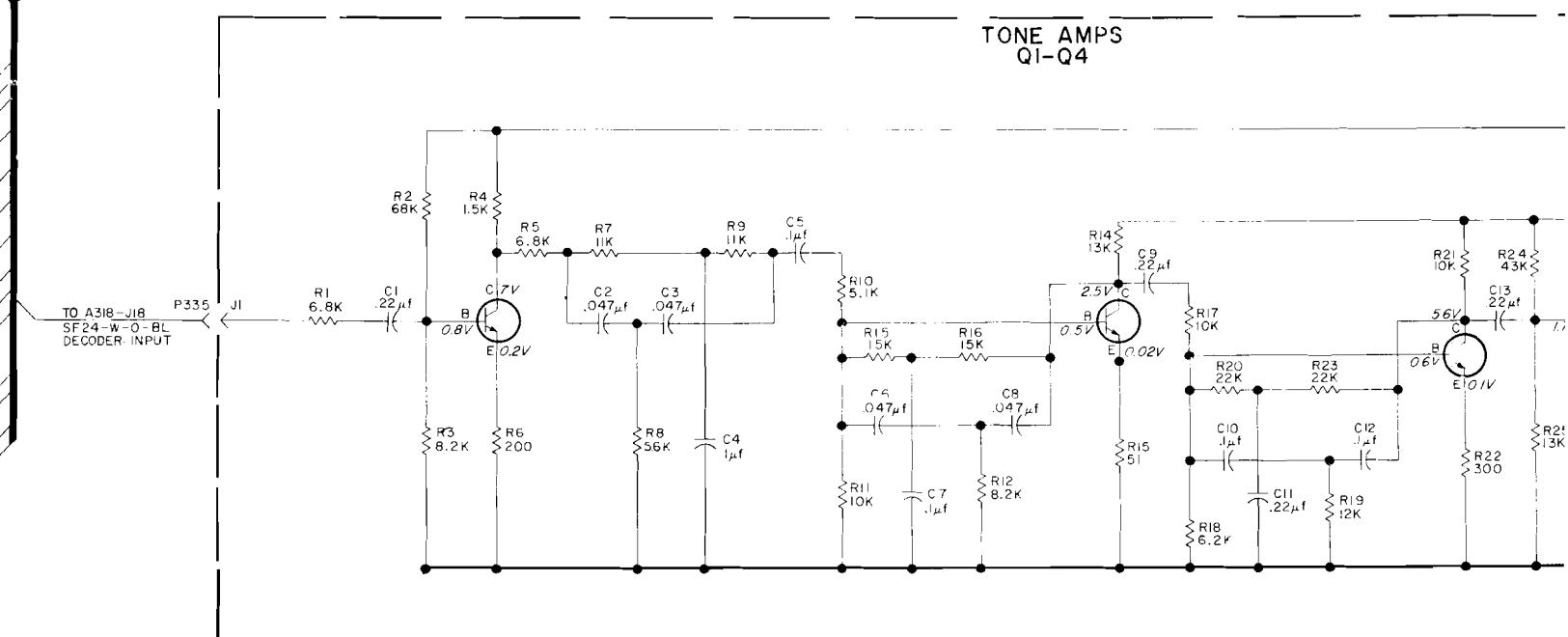
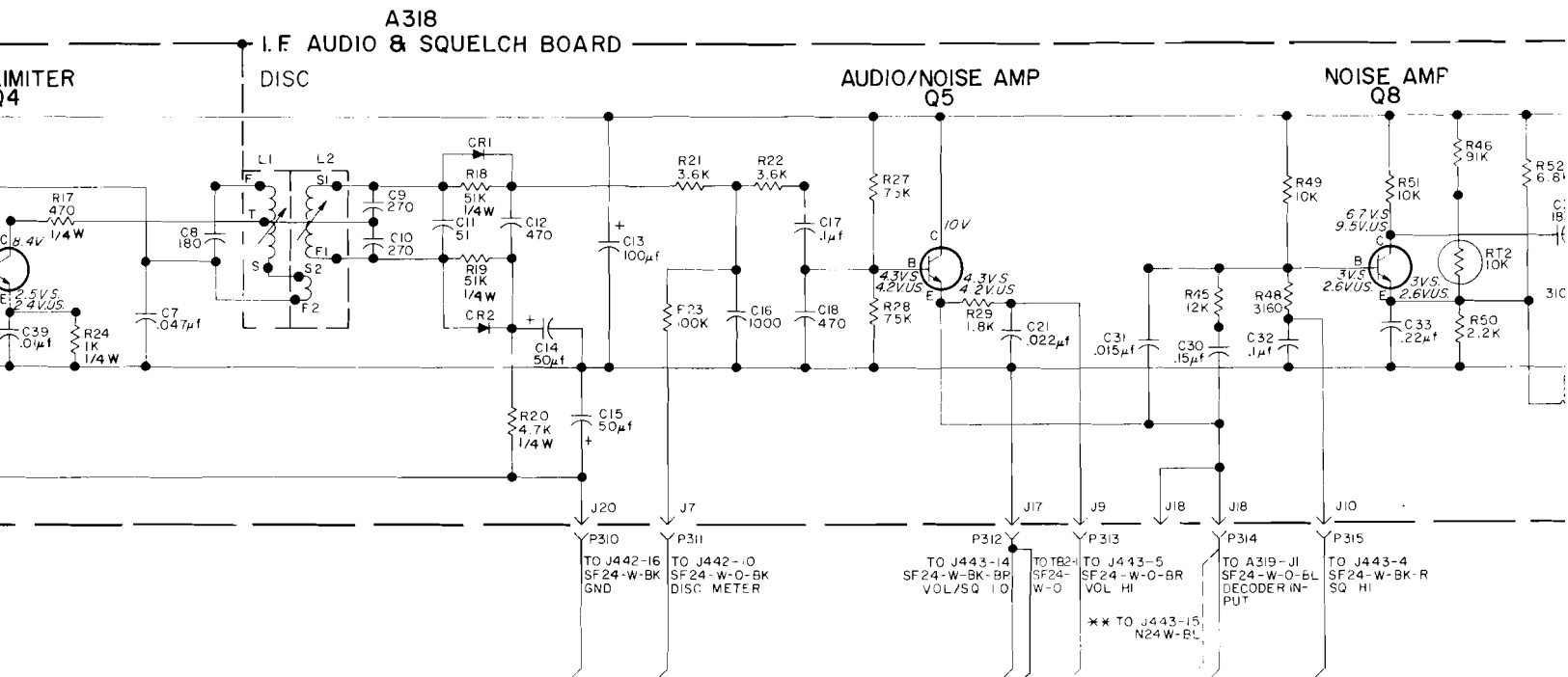
TO TB2-2
SF24-W-R
REG +10V

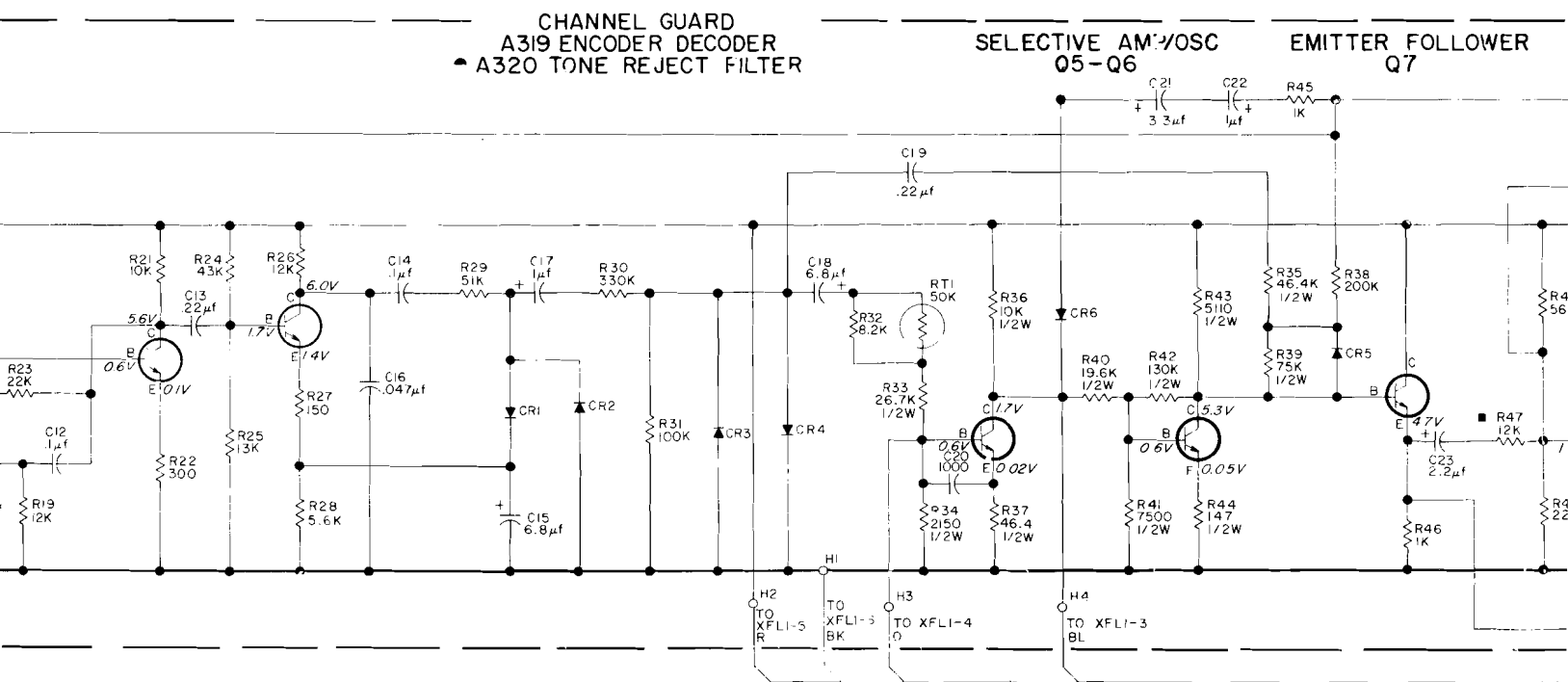
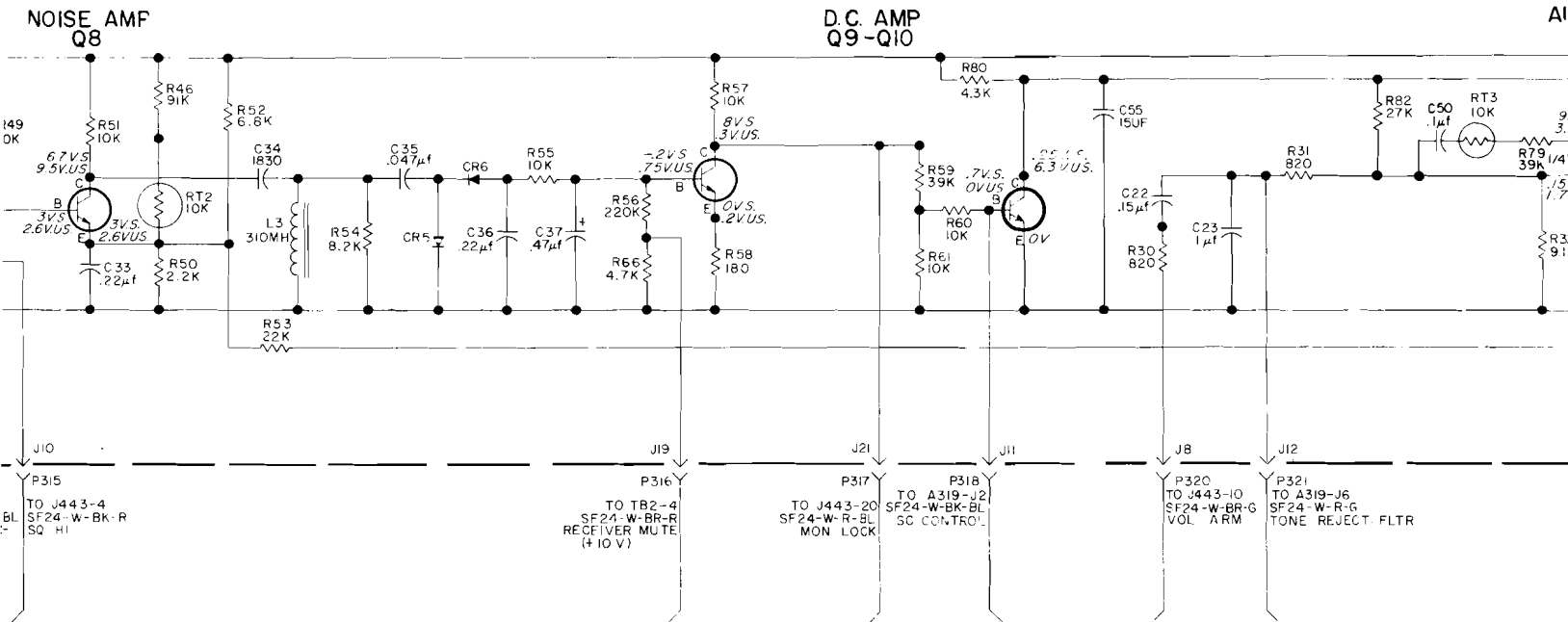


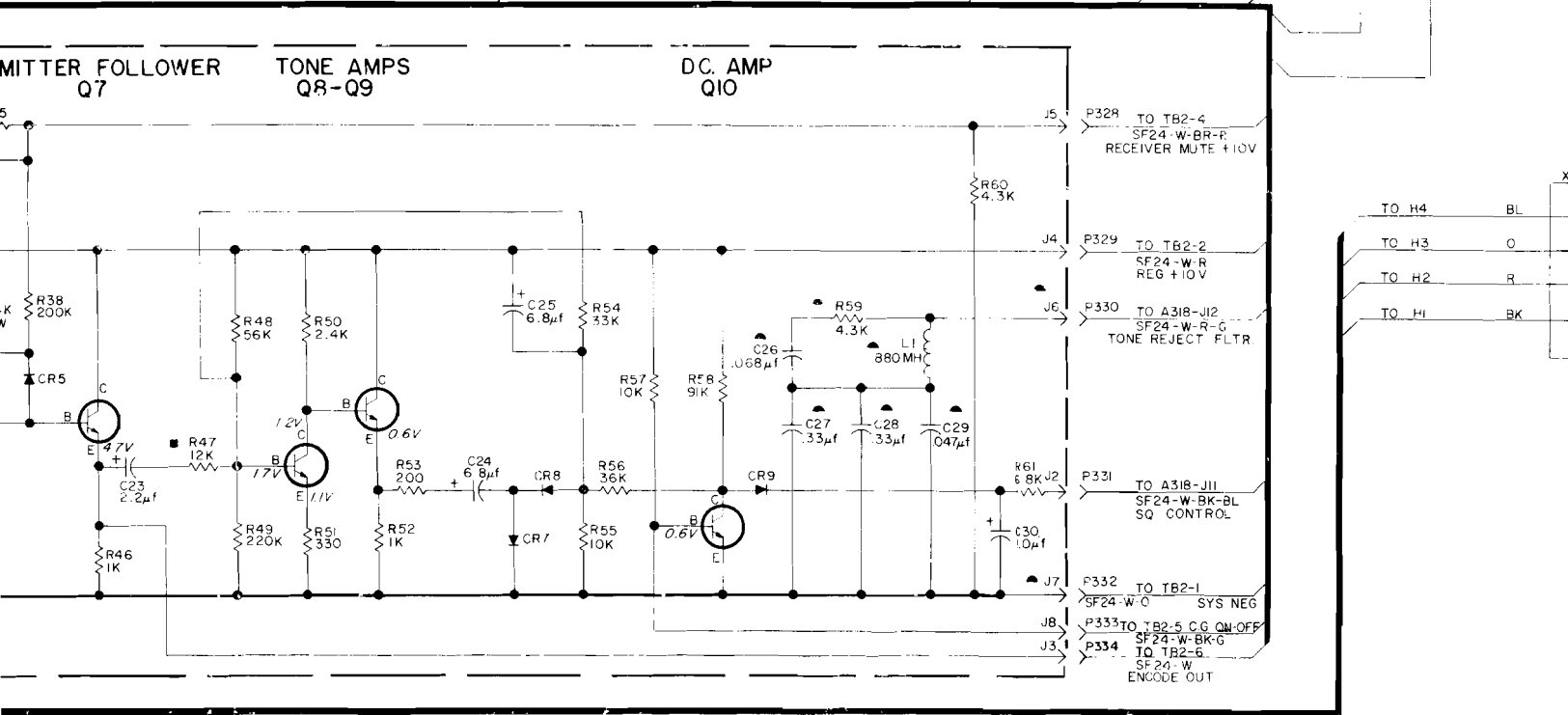
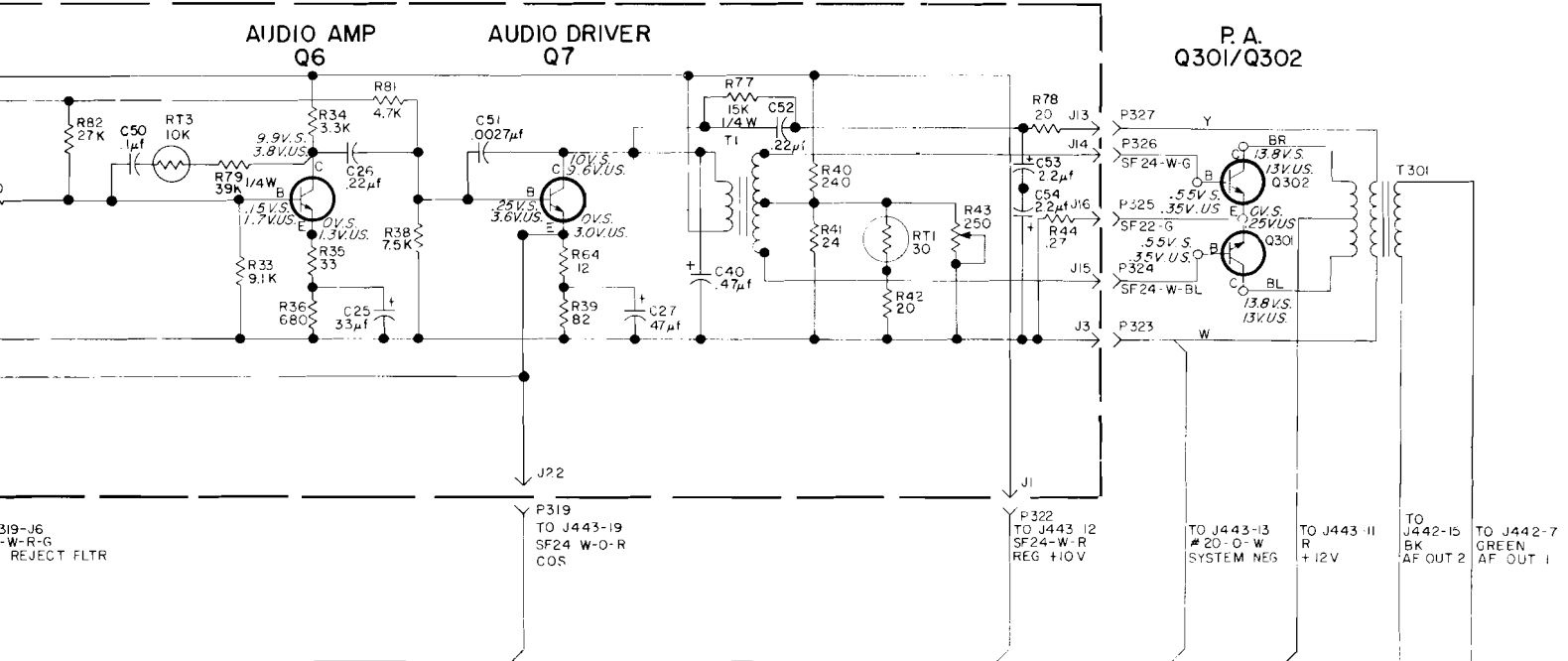


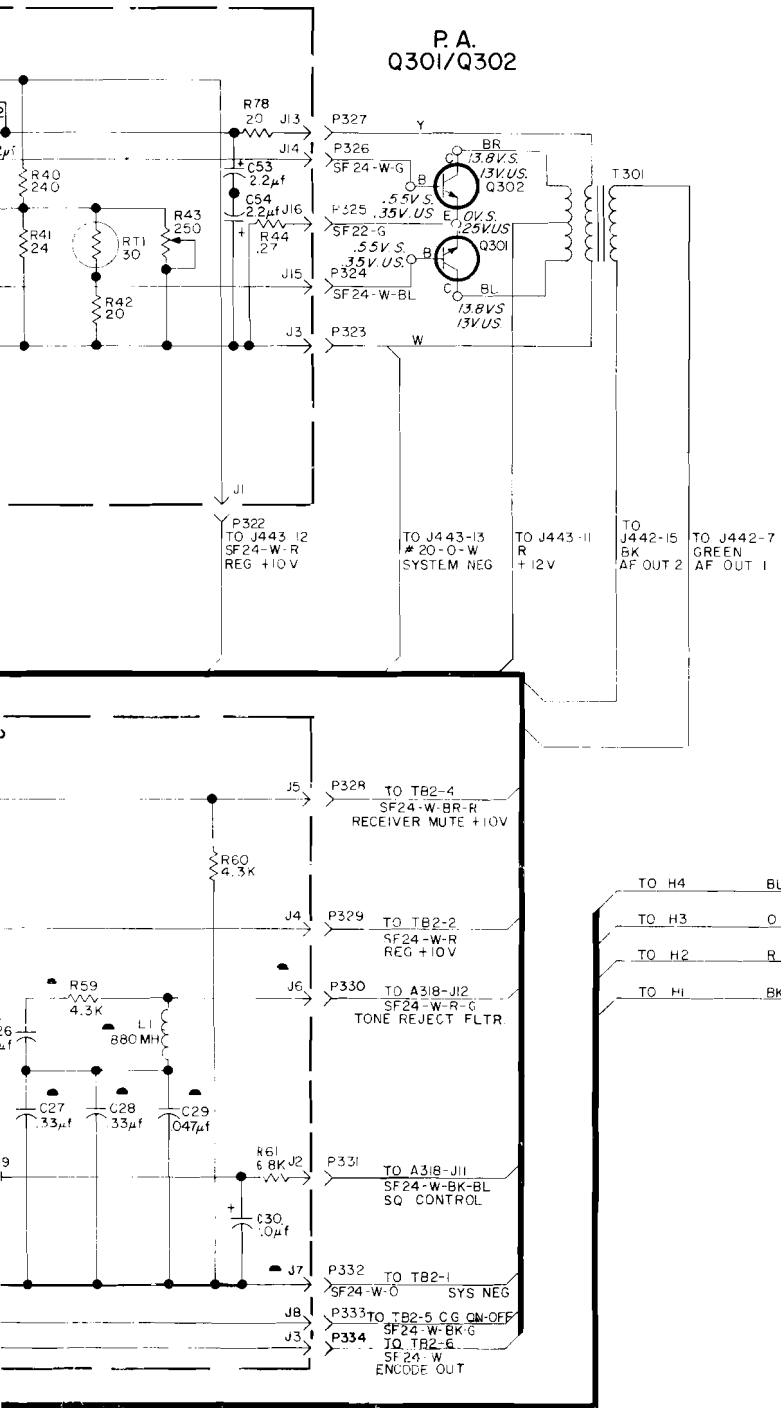
METERING JACK J442











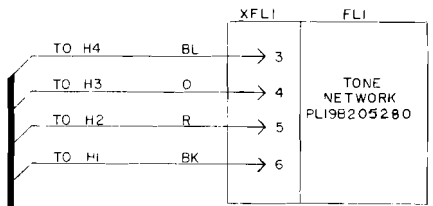
IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

ALL RESISTORS ARE 1/2 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K= 1000 OHMS OR MEG 1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH MILLIHENRYS OR H HENRYS.

VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (J442-8) WITH TEST SET MODEL 4EX3A10 OR A 20,000 OHM-PER-VOLT METER.
 S= NO SIGNAL IN WITH SQUELCH CONTROL FULLY COUNTERCLOCKWISE (MAXIMUM SQUELCH)
 US= SQUELCH CONTROL FULLY CLOCKWISE WITH A ONE MILLIVOLT MODULATED SIGNAL (UNSQUELCHED) AND 5 WATT AUDIO OUTPUT
 NOTE: DC VOLTAGES FOR 1ST MIXER, MULTIPLIER, AND 1ST IF AMPLIFIER TAKEN WITH MODULES REMOVED FROM CASTING AND 10 VOLTS APPLIED TO INPUT LEADS.

- LOW SPLIT 132-150.8 MHZ
- ▲ HIGH SPLIT 150.8-174 MHZ
- VALUE OF R47 IS DETERMINED BY TEST (SEE TEST SPEC 19A127182)
- ▲ THESE ARE ONLY PARTS PRESENT ON A320
- * * USED IN 4ER41C11 FOR IMTS BASE STATION ONLY



SCHEMATIC DIAGRAM

132—174 MHz RECEIVER
 MODELS 4ER41C10-45 & 4ER41E10-45

PARTS LIST

LBI-3877H

132-174 MHz RECEIVER
 MODELS 4ER41C10-21, 34-45
 MODELS 4ER41E10, 11, 14-17, 20, 21
 34, 35, 38-41, 44, 45

SYMBOL	GE PART NO.	DESCRIPTION
A301 and A302		FIRST MIXER A301 19B216077G1 132-150.8 MHz A302 19B216077G2 150.8-174 MHz
----- CAPACITORS -----		
C4	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C5*	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
		Earlier than REV A:
	5491189P1	Polyester: .01 μf ±20%, 50 VDCW.
C6*	5490446P2	Variable, ceramic: approx 5 to 25 pf, 350 VDCW, temp coef 0 PPM; sim to Erie Style 557-36. Deleted by REV D.
C7*	7489162P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
		In Models of REV C and earlier:
	5496218P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.
C8	5496203P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef -3300 PPM.
C9	5491601P130	Phen: 3.3 pf ±5%, 500 VDCW.
----- INDUCTORS -----		
L2*	19B216576G1	Coil.
		In Models of REV C and earlier:
	19A127115G1	Coil.
L3	7488079P6	Choke, RF: 1 μh ±10%, 0.3 ohm DC res max; sim to Jeffers 4411-8K.
----- TRANSISTORS -----		
Q1	19A115953P1	N Type, field effect.
----- RESISTORS -----		
R1	3R152P242J	Composition: 2400 ohms ±5%, 1/4 w.
R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R3*	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w. Deleted by REV D.
R4	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R5*	3R77P331K	Composition: 330 ohms ±10%, 1/2 w. Added by REV G.
----- TRANSFORMERS -----		
T1 and T2		COIL ASSEMBLY T1 19B216100G1 T2 19B216100G2
----- CAPACITORS -----		
C1	5496218P235	Ceramic disc: 4.0 pf ±5%, 500 VDCW, temp coef -80 PPM.
C2*	5496218P234	Ceramic disc: 3.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
		In REV G and earlier:
	5491238P12	Ceramic disc: 2 pf ±0.25 pf, 500 VDCW, temp coef -80 ±120 PPM.
C3	5494481P11	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.

SYMBOL	GE PART NO.	DESCRIPTION
----- INDUCTORS -----		
L1	19B216100P6	Coil.
R6*	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w. Added to G1 by REV H. Added to G2 by REV J.
	5493185P5	Tuning slug.
A303 and A304		SECOND MULTIPLIER A303 19B216107G1 132-150.8 MHz A304 19B216107G2 150.8-174 MHz
----- CAPACITORS -----		
C5	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FAS5C.
C6	19B209243P105	Polyester: 0.047 μf ±10%, 50 VDCW.
C7	5494481P11	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C8	19B209243P105	Polyester: 0.047 μf ±10%, 50 VDCW.
C14	5491601P16	Phenolic: 0.62 pf ±10%, 500 VDCW; sim to Quality Components Type MC.
C15	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FAS5C.
C17 and C18	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FAS5C.
----- TRANSISTORS -----		
Q1	19A115330P1	Silicon, NPN.
----- RESISTORS -----		
R1	3R152P392K	Composition: 3900 ohms ±10%, 1/4 w.
R2	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.
R3	3R152P331K	Composition: 330 ohms ±10%, 1/4 w.
R4	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.
R5	3R152P104K	Composition: 0.1 megohm ±10%, 1/4 w.
----- TRANSFORMERS -----		
T1 and T2		COIL ASSEMBLY T1 19B216097G1 T2 19B216097G2
----- CAPACITORS -----		
C1	5491601P107	Phenolic: 0.27 pf ±5%, 500 VDCW; sim to Quality Components Type MC.
C2	5496218P255	Ceramic disc: 47 pf ±5%, 500 VDCW, temp coef -80 PPM.
C3	5496218P252	Ceramic disc: 36 pf ±5%, 500 VDCW, temp coef -80 PPM.
C4	5496203P134	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef -3300 PPM.
----- INDUCTORS -----		
I1	19B216097P6	Coil.
	5491798P5	Tuning slug.
T3 and T4		COIL ASSEMBLY T3 19B216106G1 T4 19B216106G2
----- CAPACITORS -----		
C9	5494481P11	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C10	5496218P241	Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C11	5496218P238	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
----- DIODES AND RECTIFIERS -----		
CR1	19A115250P1	Silicon.
----- INDUCTORS -----		
L2	19B216106P6	Coil.
	5491798P5	Tuning slug.

SYMBOL	GE PART NO.
T5 and T6	
C12	5496218P241
C13	5496218P239
C16	5496218P770
----- CAPACITORS -----	
L3	19B216102P6
	5491798P5
T81	7487424P7
A305 thru A310	
C1 thru C4	5494481P112
C5 thru C8	5496219P751
C9 thru C12	5491271P106
C13 thru C16	5496219P40
C17 thru C20	19C300685P93
C21	5496219P771
C23	5494481P114
C24	5490008P31
C25	5496219P467
C26 thru C28	5494481P112
C31	5494481P112
CR1 thru CR4	19A115603P1
J1 thru J6	4033513P4
L2 and L3	7488079P16
Q1 and Q2	19A115330P1
R1 thru R4	3R152P562J

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	GE PART NO.	DESCRIPTION
		----- INDUCTORS -----
L1	19B216100P6	Coil.
R6*	3R152P103K	Composition: 10,000 ohms $\pm 10\%$, 1/4 w. Added to G1 by REV H, Added to G2 by REV J.
	5493185P5	Tuning slug.
A303 and A304		SECOND MULTIPLIER A303 19B216107G1 132-150.8 MHz A304 19B216107G2 150.8-174 MHz
		----- CAPACITORS -----
C5	5493392P7	Ceramic, feed-thru: .001 pf $\pm 100\%$ -0%, 500 VDCW; sim to Allen Bradley Type FA5C.
C6	19B209243P105	Polyester: 0.047 μ f $\pm 10\%$, 50 VDCW.
C7	5494481P11	Ceramic disc: .001 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
C8	19B209243P105	Polyester: 0.047 μ f $\pm 10\%$, 50 VDCW.
C14	5491601P16	Phenolic: 0.62 pf $\pm 10\%$, 500 VDCW; sim to Quality Components Type MC.
C15	5493392P7	Ceramic, feed-thru: .001 pf $\pm 100\%$ -0%, 500 VDCW; sim to Allen Bradley Type FA5C.
C17 and C18	5493392P7	Ceramic, feed-thru: .001 pf $\pm 100\%$ -0%, 500 VDCW; sim to Allen Bradley Type FA5C.
		----- TRANSISTORS -----
Q1	19A115330P1	Silicon, NPN.
		----- RESISTORS -----
R1	3R152P392K	Composition: 3900 ohms $\pm 10\%$, 1/4 w.
R2	3R152P103K	Composition: 10,000 ohms $\pm 10\%$, 1/4 w.
R3	3R152P331K	Composition: 330 ohms $\pm 10\%$, 1/4 w.
R4	3R152P103K	Composition: 10,000 ohms $\pm 10\%$, 1/4 w.
R5	3R152P104K	Composition: 0.1 megohm $\pm 10\%$, 1/4 w.
		----- TRANSFORMERS -----
T1 and T2		COIL ASSEMBLY T1 19B216097G1 T2 19B216097G2
		----- CAPACITORS -----
C1	5491601P107	Phenolic: 0.27 pf $\pm 5\%$, 500 VDCW; sim to Quality Components Type MC.
C2	5496218P255	Ceramic disc: 47 pf $\pm 5\%$, 500 VDCW, temp coef -80 PPM.
C3	5496218P252	Ceramic disc: 36 pf $\pm 5\%$, 500 VDCW, temp coef -80 PPM.
C4	5496203P134	Ceramic disc: 100 pf $\pm 5\%$, 500 VDCW, temp coef -3300 PPM.
		----- INDUCTORS -----
I1	19B216097P6	Coil.
	5491798P5	Tuning slug.
T3 and T4		COIL ASSEMBLY T3 19B216106G1 T4 19B216106G2
		----- CAPACITORS -----
C9	5494481P11	Ceramic disc: .001 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
C10	5496218P241	Ceramic disc: 10 pf ± 0.25 pf, 500 VDCW, temp coef -80 PPM.
C11	5496218P238	Ceramic disc: 7.0 pf ± 0.25 pf, 500 VDCW, temp coef -80 PPM.
		----- DIODES AND RECTIFIERS -----
CR1	19A115250P1	Silicon.
		----- INDUCTORS -----
L2	19B216106P6	Coil.
	5491798P5	Tuning slug.

SYMBOL	GE PART NO.	DESCRIPTION
T5 and T6		COIL ASSEMBLY T5 19B216102G1 T6 19B216102G2
		----- CAPACITORS -----
C12	5496218P241	Ceramic disc: 10 pf ± 0.25 pf, 500 VDCW, temp coef -80 PPM.
C13	5496218P239	Ceramic disc: 8.0 pf ± 0.25 pf, 500 VDCW, temp coef -80 PPM.
C16	5496218P770	Ceramic disc: 200 pf $\pm 5\%$, 500 VDCW, temp coef -750 PPM.
		----- INDUCTORS -----
L3	19B216102P6	Coil.
	5491798P5	Tuning slug.
		----- TERMINAL BOARDS -----
TB1	7487424P7	Miniature, phen: 4 terminals.
A305 thru A310		FIRST OSCILLATOR A305 19B204419G1 132-150.8 MHz 1 FREQ A306 19B204419G4 132-150.8 MHz 2 FREQ A307 19B204419G2 132-150.8 MHz 4 FREQ A308 19B204419G5 150.8-174 MHz 1 FREQ A309 19B204419G3 150.8-174 MHz 2 FREQ A310 19B204419G6 150.8-174 MHz 4 FREQ
		----- CAPACITORS -----
C1 thru C4	5494481P112	Ceramic disc: .001 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.
C5 thru C8	5496219P751	Ceramic disc: 33 pf $\pm 5\%$, 500 VDCW, temp coef -750 PPM.
C9 thru C12	5491271P106	Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C13 thru C16	5496219P40	Ceramic disc: 9 pf ± 0.25 pf, 500 VDCW, temp coef 0 PPM.
C17 thru C20	19C300685P93	Ceramic disc: 5 pf ± 0.1 pf, 500 VDCW, temp coef 0 PPM.
C21	5496219P771	Ceramic disc: 220 pf $\pm 5\%$, 500 VDCW, temp coef -750 PPM.
C23	5494481P114	Ceramic disc: .002 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.
C24	5490008P31	Silver mica: 150 pf $\pm 5\%$, 500 VDCW; sim to Electro Motive Type DM-15.
C25	5496219P467	Ceramic disc: 150 pf $\pm 5\%$, 500 VDCW, temp coef -220 PPM.
C26 thru C28	5494481P112	Ceramic disc: .001 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.
C31	5494481P112	Ceramic disc: .001 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.
		----- DIODES AND RECTIFIERS -----
CR1 thru CR4	19A115603P1	Silicon.
		----- JACKS AND RECEPTACLES -----
J1 thru J6	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
		----- INDUCTORS -----
L2 and L3	7488079P16	Choke, RF: 10 μ h $\pm 10\%$, 0.6 ohm DC res; sim to Jeffers 4421-7K.
		----- TRANSISTORS -----
Q1 and Q2	19A115330P1	Silicon, NPN.
		----- RESISTORS -----
R1 thru R4	3R152P562J	Composition: 5600 ohms $\pm 5\%$, 1/4 w.

SYMBOL	GE PART NO.	DESCRIPTION
R5 thru R8	3R152P104K	
R9	3R152P153J	
R10	3R152P101K	
R11 and R12	3R152P102J	
R13	3R152P151J	
R14	3R152P103J	
R15	3R152P101K	
R19	3R152P360J	
RT1 thru RT4	19B209284P5	
T1 and T2		
C29	5496218P253	
C30	5496218P250	
C32	5496218P34	
C33	5494481P12	
CR5	19A115250P1	
L1	19A121093P1	
R16	3R152P103K 5491798P5	
XY1 thru XY4		
Y1 thru Y4	19B206576P4	
Y1 thru Y4	19B206576P5	
A311 thru A314		
C1 thru C6	5494481P112	
CR1 thru CR4	19A115250P1	

SYMBOL	GE PART NO.	DESCRIPTION
T5 and T6		COIL ASSEMBLY T5 19B216102G1 T6 19B216102G2
		----- CAPACITORS -----
C12	5496218P241	Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C13	5496218P239	Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C16	5496218P770	Ceramic disc: 200 pf ±5%, 500 VDCW, temp coef -750 PPM.
		----- INDUCTORS -----
L3	19B216102P6 5491798P5	Coil. Tuning slug.
		----- TERMINAL BOARDS -----
TB1	7487424P7	Miniature, phen: 4 terminals.
A305 thru A310		FIRST OSCILLATOR A305 19B204419G1 132-150.8 MHz 1 FREQ A306 19B204419G4 132-150.8 MHz 2 FREQ A307 19B204419G2 132-150.8 MHz 4 FREQ A308 19B204419G5 150.8-174 MHz 1 FREQ A309 19B204419G3 150.8-174 MHz 2 FREQ A310 19B204419G6 150.8-174 MHz 4 FREQ
		----- CAPACITORS -----
C1 thru C4	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C5 thru C8	5496219P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.
C9 thru C12	5491271P106	Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C13 thru C16	5496219P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C17 thru C20	19C300685P93	Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coef 0 PPM.
C21	5496219P771	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -750 PPM.
C23	5494481P114	Ceramic disc: .002 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C24	5490008P31	Silver mica: 150 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C25	5496219P467	Ceramic disc: 150 pf ±5%, 500 VDCW, temp coef -220 PPM.
C26 thru C28	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C31	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
		----- DIODES AND RECTIFIERS -----
CR1 thru CR4	19A115603P1	Silicon.
		----- JACKS AND RECEPTACLES -----
J1 thru J6	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
		----- INDUCTORS -----
L2 and L3	7488079P16	Choke, RF: 10 µh ±10%, 0.6 ohm DC res; sim to Jeffers 4421-7K.
		----- TRANSISTORS -----
Q1 and Q2	19A115330P1	Silicon, NPN.
		----- RESISTORS -----
R1 thru R4	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.

SYMBOL	GE PART NO.	DESCRIPTION
R5 thru R8	3R152P104K	Composition: 0.1 megohm ±10%, 1/4 w.
R9	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.
R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R11 and R12	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.
R13	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.
R14	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.
R15	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R19	3R152P360J	Composition: 36 ohms ±5%, 1/4 w.
		----- THERMISTORS -----
RT1 thru RT4	19B209284P5	Disc: 43 ohms nominal, color code green.
		----- TRANSFORMERS -----
T1 and T2		COIL ASSEMBLY T1 19B204421G1 T2 19B204421G2
		----- CAPACITORS -----
C29	5496218P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.
C30	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
C32	5496218P34	Ceramic disc: 3 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C33	5494481P12	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
		----- DIODES AND RECTIFIERS -----
CR5	19A115250P1	Silicon.
		----- INDUCTORS -----
L1	19A121093P1	Coil. Includes tuning slug 5491798P5.
		----- RESISTORS -----
R16	3R152P103K 5491798P5	Composition: 10,000 ohms ±10%, 1/4 w. Tuning slug.
		----- SOCKETS -----
XY1 thru XY4		Refer to Mechanical Parts (RC-1627).
		----- CRYSTALS -----
		When reordering give GE Part No. and specify exact freq needed. Crystal freq = (OF -5.30 MHz) - 9.
Y1 thru Y4	19B206576P4	Quartz: freq range 14077.777 to 16166.666 KHz, temp range -30°C to +85°C. (132-150.8 MHz)
Y1 thru Y4	19B206576P5	Quartz: freq range 16166.667 to 18744.444 KHz, temp range -30°C to +85°C. (150.8-174 MHz)
A311 thru A314		FIRST OSCILLATOR A311 19B216178G1 132-150.8 MHz 1 FREQ A312 19B216178G2 132-150.8 MHz MULT-FREQ A313 19B216178G3 150.8-174 MHz 1 FREQ A314 19B216178G4 150.8-174 MHz MULT-FREQ
		----- CAPACITORS -----
C1 thru C6	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
		----- DIODES AND RECTIFIERS -----
CR1 thru CR4	19A115250P1	Silicon.

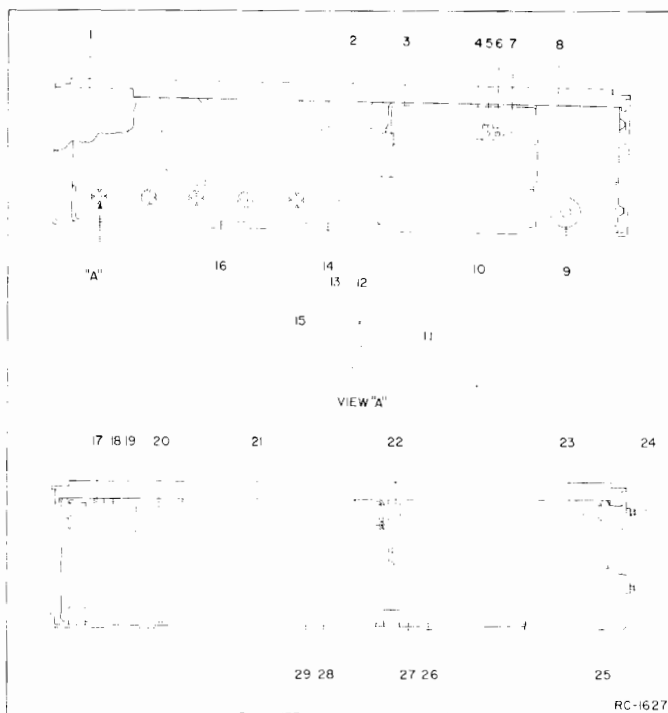
SYMBOL	GE PART
J1 thru J6	4033513P4
L2 and L3	7488079P16
L4	7488079P8
Q1	19A115330P1
R1	3R152P272J
R2	3R152P103J
R3	3R152P102J
R4	3R152P151J
R5	3R152P101K
T1 and T2	
C29	5496218P25
C30	5496218P25
C32	5496218P34
C33	5494481P12
CR5	19A115250P1
L1	19A121093P1
R16	3R152P103K 5491798P5
XY1 thru XY4	19B216043G1 19D413071P1 19A115834P2
Y1 thru Y4	4R26A11 19D413070P1
A315	
C1	5494481P11
C2*	5493392P107
	5494481P111

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
±10%, 1/4 w.		----- JACKS AND RECEPTACLES -----	C3	5493392P108	Ceramic, stand-off: 22 pf ±10%, 500 VDCW; sim to Allen Bradley Type S55D.
±5%, 1/4 w.	J1 thru J6	Contact, electrical; sim to Bead Chain L93-3.	C7 and C8	19A116080P105	Polyester: 0.047 μf ±10%, 50 VDCW.
±10%, 1/4 w.		----- INDUCTORS -----	E1 thru E3	4029309P1	----- TERMINALS ----- Feed-thru: 750 VRMS max, 5.5 amps; sim to Sealectro PT-SM-27.
±5%, 1/4 w.	L2 and L3	Choke, RF: 10 μh ±10%, 0.60 ohms DC res max; sim to Jeffers 4421-7K.	Q1	19A115925P1	----- TRANSISTORS ----- Silicon, NPN.
±10%, 1/4 w.	L4	Choke, RF: 2.20 μh ±10%, 1 ohm DC res max; sim to Jeffers 4411-12K.	R1	3R152P511J	----- RESISTORS ----- Composition: 510 ohms ±5%, 1/4 w.
±5%, 1/4 w.	Q1	----- TRANSISTORS -----	R2	3R152P332K	Composition: 3300 ohms ±10%, 1/4 w.
±10%, 1/4 w.		Silicon, NPN.	R3	3R152P682K	Composition: 6800 ohms ±10%, 1/4 w.
±5%, 1/4 w.	R1	----- RESISTORS -----	R4	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
±10%, 1/4 w.	R2	Composition: 2700 ohms ±5%, 1/4 w.	T1		----- TRANSFORMERS ----- COIL ASSEMBLY 19B216103G1
±5%, 1/4 w.	R3	Composition: 10,000 ohms ±5%, 1/4 w.	C4	5496218P265	----- CAPACITORS ----- Ceramic disc: 120 pf ±5%, 500 VDCW, temp coef -80 PPM.
±10%, 1/4 w.	R4	Composition: 1000 ohms ±5%, 1/4 w.	C5	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
±5%, 1/4 w.	R5	Composition: 150 ohms ±5%, 1/4 w.	C6	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
±10%, 1/4 w.	T1 and T2	----- TRANSFORMERS ----- COIL ASSEMBLY T1 19B204421G1 T2 19B204421G2	C9	5496218P246	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef -80 PPM.
±5%, 1/4 w.	C29	----- CAPACITORS ----- Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.	R5	3R152P101K	----- RESISTORS ----- Composition: 100 ohms ±10%, 1/4 w.
±10%, 1/4 w.	C30	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	5491798P7		Tuning slug.
±5%, 1/4 w.	C32	Ceramic disc: 3 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.	A316		CRYSTAL FILTER 19B204616G3
±10%, 1/4 w.	C33	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	FL5	19B206692G1	----- FILTERS ----- Bandpass.
±5%, 1/4 w.	CR5	----- DIODES AND RECTIFIERS ----- Silicon.	R7	3R152P562K	----- RESISTORS ----- Composition: 5600 ohms ±10%, 1/4 w.
±10%, 1/4 w.	L1	----- INDUCTORS ----- Coil. Includes tuning slug 5491798P5.	R8	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.
±5%, 1/4 w.	R16	----- RESISTORS ----- Composition: 10,000 ohms ±10%, 1/4 w. Tuning slug.	A317		SECOND MIXER 19B216119G1
±10%, 1/4 w.	XY1 thru XY4	----- SOCKETS ----- Socket assembly. Includes: Socket cavity. Electrical contact.	C2	19A116080P7	----- CAPACITORS ----- Polyester: 0.1 μf ±20%, 50 VDCW.
±5%, 1/4 w.	19D413071P1	Socket cavity.	C3	5494481P112	Ceramic disc: .001 pf ±10%, 500 VDCW; sim to RMC Type JF Discap.
±10%, 1/4 w.	19A115834P2	Electrical contact.	C4 and C5	5490008P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
±5%, 1/4 w.	4EG26A11	----- OSCILLATORS ----- When reordering, specify ICOM Frequency. ICOM Frequency = (OF - 5.3 MHz) ÷ 9. Integrated Circuit Oscillator Module (ICOM).	C6	5490008P9	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
±10%, 1/4 w.	19D413070P1	Cap, decorative.	C7 and C8	19A116080P5	Polyester: 0.047 μf ±20%, 50 VDCW.
±5%, 1/4 w.	A315	HIGH IF AMPLIFIER 19B216109G1	C9	5496219P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.
±10%, 1/4 w.	C1	----- CAPACITORS ----- Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C10	19A116080P7	Polyester: 0.1 μf ±20%, 50 VDCW.
±5%, 1/4 w.	C2*	Ceramic, stand-off: .001 pf ±100%-0%, 500 VDCW; sim to Allen-Bradley Type S55D. In Models earlier than REV B: Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C11	5496219P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
±10%, 1/4 w.	5494481P111		C12	5496219P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
C5 and C6	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C38*	5496267P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. Deleted by REV C. Earlier than REV A:
C7	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.		5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
C8	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.	C39	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDCW.
C9 and C10	5490008P37	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-13.	C40*	5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Earlier than REV A:
C11	5496219P656	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -470 PPM.		19B209243P117	Polyester: 0.22 µf ±10%, 50 VDCW.
C12	5494481P108	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C41	5490008P129	Silver mica: 120 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C13	19A115680P107	Electrolytic: 100 µf +150% -10%, 15 VDCW; sim to Mallory Type TT.	C42*	19B209243P4	Polyester: 0.033 µf ±20%, 50 VDCW. Deleted by REV A.
C14 and C15	19A115680P104	Electrolytic: 50 µf +150% -10%, 25 VDCW; sim to Mallory Type TT.	C43*	5496267P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague Type 150D. Deleted by REV A.
C16	5494481P112	Ceramic disc: .001 pf ±10%, 500 VDCW; sim to RMC Type JF Discap.	C49*	5496267P9	Tantalum: 3.3 µf ±15%, VDCW; sim to Sprague Type 150D. Added by REV A. Deleted by REV C.
C17	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	C50*	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW. Added by REV A.
C18	5494481P108	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C51*	5494481P127	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV A.
C19 and C20	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.	C52*	19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW. Added by REV A.
C21*	19A116080P3	Polyester: 0.022 µf ±20%, 50 VDCW. Earlier than REV A:	C53* and C54*	5496267P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague Type 150D. Added by REV A.
C22	19B209243P1	Polyester: 0.01 µf ±20%, 50 VDCW.	C55*	5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. Added by REV C.
C23	19A116080P108	Polyester: 0.15 µf ±10%, 50 VDCW.			----- DIODES AND RECTIFIERS -----
C24*	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.	CR1 and CR2	19A115250P1	Silicon.
C25	19B209243P106	Polyester: .068 µf ±10%, 50 VDCW. Deleted by REV A.	CR3* and CR4*	19A115250P1	Silicon. In REV F and earlier: Germanium.
C26*	5496267P6	Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 150D.		4038056P1	Silicon.
C26*	19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW. In REV D and earlier:	CR5 and CR6	19A115250P1	Silicon.
	5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Earlier than REV A:	CR7*	19A115250P1	Silicon. Deleted by REV C.
	19B209243P14	Polyester: 0.33 µf ±20%, 250 VDCW.	CR8*	19A115250P1	Silicon. Added by REV A. Deleted by REV C.
C27*	5496267P2	Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 150D. In REV B and earlier:			----- JACKS AND RECEPTACLES -----
	5496267P6	Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 150D.	J1 thru J22	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
C28*	5496267P229	Tantalum: 0.68 µf ±10%, 35 VDCW; sim to Sprague Type 150D. Deleted by REV A.			----- INDUCTORS -----
C29*	5496267P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Deleted by REV A.	L1	19A115711P6	Transformer, freq: 455 KHz; sim to TOKO PEFCN-14733-CX12.
C30	19A116080P8	Polyester: 0.15 µf ±20%, 50 VDCW.	L2	19A115711P7	Transformer, freq: 455 KHz; sim to TOKO PEFCN-14734-BNL2.
C31	19A116080P102	Polyester: 0.015 µf ±10%, 50 VDCW.	L3	19A127134G1	Choke. Includes tuning slug 7486872P7.
C32	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.			----- TRANSISTORS -----
C33	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.	Q1 thru Q6	19A115123P1	Silicon, NPN; sim to Type 2N2712.
C34	4029003P207	Silver mica: 1830 pf ±2%, 500 VDCW; sim to Electro Motive Type DM-20.	Q7	19A115300P4	Silicon, NPN; sim to Type 2N3053.
C35	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.	Q8	19A115123P1	Silicon, NPN; sim to Type 2N2712.
C36*	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW. In REV B and earlier:	Q9	19A115362P1	Silicon, NPN; sim to Type 2N2925.
	19B209243P7	Polyester: 0.1 µf ±20%, 50 VDCW.	Q10*	19A116774P1	Silicon, NPN; sim to Type 2N5210. In REV G and earlier:
C37*	5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Earlier than REV A:		19A115123P1	Silicon, NPN; sim to Type 2N2712.
	5496267P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D.			----- RESISTORS -----
			R1	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
			R2	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
			R3	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
			R4	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.

ITEM NO.	DESCRIPTION
.2G1	Coil.
*16	Choke, RF: 10 μ h \pm 10%, 0.6 ohm DC res max; sim to Jeffers 4421-7K.
----- PLUGS -----	
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 41854.
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 41854.
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 41854.
----- TRANSISTORS -----	
*3P2	Silicon, NPN.
	In REV D and earlier:
*8P1	Silicon, NPN.
----- RESISTORS -----	
*1K	Composition: 330 ohms \pm 10%, 1/4 w.
*8P444	Metal film: 0.28 megohm \pm 2%, 1/2 w.
*K	Composition: 39 ohms \pm 10%, 1 w.
----- TRANSFORMERS -----	
*1P2	Audio freq: 300 to 4000 Hz, Pri: 1.00 ohms \pm 15% DC res, Sec 1: .23 ohm \pm 10% DC res, Sec 2: 10.5 ohms \pm 15% DC res.
----- TERMINAL BOARDS -----	
*7	Miniature, phen: 4 terminals.
*26	Miniature, phen: 6 terminals.
----- CABLES -----	
*4G1	Coaxial: approx 5 inches long. Includes J441.
<p style="text-align: center;">HARNES ASSEMBLY 19E500873G7</p> <p>(Includes C307, C317, C318, J441-J443, P301-P304, P307-P313, P315-P317, P319, P320, P322-P327, R302, R303, T301, TB2)</p>	
<p style="text-align: center;">CHANNEL GUARD MODIFICATION KIT 19A127178G1 (Used with A319)</p>	
----- MISCELLANEOUS -----	
*76G1	Harness (Encoder/Decoder). Includes:
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 42827-2.
*2	Contact, electrical; sim to Amp 42827-2.
<p style="text-align: center;">CHANNEL GUARD MODIFICATION KIT 19A127178G2 (Used with A320)</p>	
----- MISCELLANEOUS -----	
*77G1	Harness (Tone Reject Filter). Includes:

SYMBOL	GE PART NO.	DESCRIPTION
P321	4029840P2	Contact, electrical; sim to Amp 42827-2.
P330	4029840P2	Contact, electrical; sim to Amp 42827-2.
P332	4029840P2	Contact, electrical; sim to Amp 42827-2.
MECHANICAL PARTS (SEE RC-1627)		
1	19C303396G4	Bottom cover. (Station)
	19C303385G1	Bottom cover. (Mobile)
2	19C317344P3	Heat sink.
3	19A121222P1	Support. (Mounts C312 and C313).
4	4033089P1	Clip. (Part of XY1-XY4).
5	19B200525P9	Rivet. (Part of XY1-XY4).
6	19A115793P1	Contact. (Part of XY1-XY4).
7	4039307P1	Crystal socket. (Part of XY1-XY4).
8	19B216073P1	Cover. (Used with A317).
9	4034252P5	Can. (Used with T1 on A317).
10	19C303389G1	Chassis.
11	4036765G2	(Not Used).
12	4036765G4	Screw. (Part of C301 thru C306).
13	7137968P8	Nut, stamped: No. 6-32 thread; sim to Palnut T0632005. (Part of C301 thru C306).
14	19A121221P1	Support. (Mounts C310 and C311).
15	4036899P4	(Not Used).
16	7145451P1	Cleat.
17	19B204583G2	Hinge.
18	19B216727P1	Support. (Used with Q301 and Q302).
19	19A116023P2	Plate, insulated. (Used with Q301 and Q302).
20	19A115222P3	Insulator, bushing. (Used with Q301 and Q302).
21	4029851P6	Clip, loop.
22	19B204583G1	Hinge.
23	19B204583G3	Hinge.
24	19A121676P1	Guide pin.
25	19C303485G3	Top cover. (Station, except Repeaters and VM).
	19C303676G2	Top cover. (Station, Repeater and VM only).
	19C303385P2	Top cover. (Mobile).
26	19A121297P1	Angle.
27	7160861P4	Nut. (Used to secure cover).
28	4035267P2	Button, plug. (Used with A318 thru A320).
29	4036555P1	Insulator disc. (Used with Q7 on A318).



SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART
R56	3R77P363J	Composition: 36,000 ohms ±5%, 1/2 w.	C2*	5496218P640	Ceramic disc: 9.0 pf ±0.25 pf, 500 VDCW, temp coef -470 PPM.	L312	19B216112
R57	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.			Earlier than REV A:	L313 and L314	7488079PM
R58	3R77P913J	Composition: 91,000 ohms ±5%, 1/2 w.		5496218P638	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, temp coef -470 PPM.		
R59*	3R77P182J	Composition: 1800 ohms ±5%, 1/2 w. In REV C and earlier:		5491798P5	Tuning slug.	P301 thru P313	4029840P2
	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.			----- TRANSFORMERS -----		
R60	3R77P432J	Composition: 4300 ohms ±5%, 1/2 w.	T3 and T4		COIL ASSEMBLY T3 19B216478G1 T4 19B216478G2	P315 thru P317	4029840P2
R61	3R77P682K	Composition: 6800 ohms ±10%, 1/2 w.			----- CAPACITORS -----	P319 and P320	4029840P2
		----- THERMISTORS -----					
RT1	5490828P22	Thermistor: 50,000 ohms ±10%, color code yellow; sim to Globar Type 763H.	C3	5496218P638	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, temp coef -470 PPM.	P322	4029840P2
		----- SOCKETS -----	C4	5496218P635	Ceramic disc: 4.0 pf ±0.25 pf, 500 VDCW, temp coef -470 PPM.	P323	4029840P1
XFL1	19A121920G3	Reed, mica-filled phen: 7 pins rated at 1 amp at 500 VRMS with 4-1/2 inches of cable.		5491798P5	Tuning slug.	P324	4029840P2
A320		----- TONE REJECT FILTER 19C311797G2			----- CABLES -----	P325	4029840P1
		----- CAPACITORS -----	W1	5491689P74	RF. Includes J444 connector.	P326	4029840P2
C26	19A116080P206	Polyester: 0.068 µf ±5%, 50 VDCW.	W2	19B205634G2	RF. Includes J2 connector 19B209122P3.	P327	4029840P1
C27 and C28	19A116080P210	Polyester: 0.33 µf ±5%, 50 VDCW.	W3	19A127476G1	RF. Includes P3 connector.	Q301* and Q302*	19A116203
C29*	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW. Earlier than REV A:			CHASSIS AND RF CIRCUIT 19E500872G1 and G2		19A115948
	19B209243P107	Polyester: 0.1 µf ±10%, 50 VDCW.			----- CAPACITORS -----		
		----- JACKS AND RECEPTACLES -----	C301 thru C306		(See Mechanical Parts RC-1627)	R301	3R152P331
J6 and J7	4033513P4	Contact, electrical; sim to Bead Chain L93-3.	C307	7774750P4	Ceramic disc: .001 µf +100% -0%, 500 VDCW.	R302	19A116278
		----- INDUCTORS -----	C310 thru C313		Ceramic, feed-thru: 1000 pf +150%-0%, 500 VDCW.	R303	3R78P390K
L1	19A115690P1	Coil, RF: 880 mh ±5%, sim to Arttd AC5672.	C314	5496267P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	T301	19A116041
		----- RESISTORS -----	C315	19A115680P3	Electrolytic: 20 µf +150% -10%, 25 VDCW; sim to Mallory Type TT.		
R59*	3R77P182J	Composition: 1800 ohms ±5%, 1/2 w. In REV A and earlier:	C317 and C318	5494481P12	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	TB1	7487424F7
	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.			----- DIODES AND RECTIFIERS -----	TB2	7487424F2
A321 and A322		RF PRE AMP A321 19A127479G1 132-150.8 MHz A322 19A127479G2 150-8-174 MHz	CRI*	19A116062P2	Selenium. Added by REV C. Deleted in G1 by REV J, deleted in G2 by REV K.	W441	19B205634
		----- CAPACITORS -----	J441		Connector. (Part of W441).		
C5 thru C7	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	J442	19B205689G2	Connector: 18 contacts.		
C8 and C9	19A116080P101	Polyester: 0.01 µf ±10%, 50 VDCW.	J443	19C303426G1	Connector: 20 pin contacts.		
		----- TRANSISTORS -----	J444		Connector: (Part of A321/A322-W1).		
Q1	19A116154P1	N Channel, field effect.			----- INDUCTORS -----		
		----- RESISTORS -----	L301	19B216112G4	Coil.		
R1	3R152P221J	Composition: 220 ohms ±5%, 1/4 w.	L302	19B216112G3	Coil.		
R2 and R3	3R152P220J	Composition: 22 ohms ±5%, 1/4 w.	L303	19B216112G8	Coil.	P314	4029840P2
		----- TRANSFORMERS -----	L304	19B216112G7	Coil.	P318	4029840P2
T1 and T2		COIL ASSEMBLY T1 19B216479G1 T2 19B216479G2	L305	19B216112G8	Coil.	P321	4029840P2
		----- CAPACITORS -----	L306	19B216112G7	Coil.	P328 thru P335	4029840P2
C1	5496218P641	Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -470 PPM.	L307	19B216112G8	Coil.		
			L308	19B216112G7	Coil.		
			L309	19B216112G6	Coil.		
			L310	19B216112G5	Coil.		
			L311	19B216112G2	Coil.		19B21617

DESCRIPTION	
Silicon.	
Silicon.	
Silicon, Zener.	
Silicon.	
----- FILTERS -----	
TONE FREQUENCY NETWORK 19B205280	
71.9 Hz	
77.0 Hz	
82.5 Hz	
88.5 Hz	
94.8 Hz	
100.0 Hz	
103.5 Hz	
107.2 Hz	
110.9 Hz	
114.8 Hz	
118.8 Hz	
123.0 Hz	
127.3 Hz	
131.8 Hz	
136.5 Hz	
141.3 Hz	
146.2 Hz	
151.4 Hz	
156.7 Hz	
162.2 Hz	
167.9 Hz	
173.8 Hz	
179.9 Hz	
186.2 Hz	
192.8 Hz	
203.5 Hz	
----- JACKS AND RECEPTACLES -----	
Contact, electrical sim to Bead Chain L93-3.	
----- INDUCTORS -----	
Coil, RF: 880 MH ±5%, sim to Arttd AC5872.	
----- TRANSISTORS -----	
Silicon, NPN; sim to Type 2N2712.	
Silicon, NPN; sim to Type 2N2925.	
Silicon, NPN; sim to Type 2N2712.	
Silicon, NPN; sim to Type 2N2925.	
Silicon, NPN; sim to Type 2N2712.	
----- RESISTORS -----	
Composition: 6800 ohms ±10%, 1/2 w.	
Composition: 68,000 ohms ±5%, 1/2 w.	
Composition: 8200 ohms ±5%, 1/2 w.	
Composition: 1500 ohms ±5%, 1/2 w.	
Composition: 6800 ohms ±10%, 1/2 w.	
Composition: 200 ohms ±5%, 1/2 w.	
Composition: 11,000 ohms ±5%, 1/2 w.	
Metal film: 10,500 ohms ±2%, 1/2 w.	
In REV A:	
Composition: 6200 ohms ±5%, 1/4 w.	
Earlier than REV A:	
Composition: 5100 ohms ±5%, 1/4 w.	
Metal film: 11,000 ohms ±2%, 1/2 w.	
Composition: 5100 ohms ±5%, 1/2 w.	
Composition: 10,000 ohms ±5%, 1/2 w.	

SYMBOL	GE PART NO.	DESCRIPTION
R12	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
R13	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
R14	3R77P133J	Composition: 13,000 ohms ±5%, 1/2 w.
R15	3R77P510J	Composition: 51 ohms ±5%, 1/2 w.
R16	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
R17	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R18	3R77P622J	Composition: 6200 ohms ±5%, 1/2 w.
R19	3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.
R20	3R77P223J	Composition: 22,000 ohms ±5%, 1/2 w.
R21	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R22	3R77P301J	Composition: 300 ohms ±5%, 1/2 w.
R23	3R77P223J	Composition: 22,000 ohms ±5%, 1/2 w.
R24	3R77P433J	Composition: 43,000 ohms ±5%, 1/2 w.
R25	3R77P133J	Composition: 13,000 ohms ±5%, 1/2 w.
R26	3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.
R27	3R77P151J	Composition: 150 ohms ±5%, 1/2 w.
R28	3R77P562J	Composition: 5600 ohms ±5%, 1/2 w.
R29	3R77P513J	Composition: 51,000 ohms ±5%, 1/2 w.
R30	3R77P334J	Composition: 0.33 megohms ±5%, 1/2 w.
R31	3R77P104J	Composition: 0.1 megohm ±5%, 1/2 w.
R32	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
R33	19A116278P342	Metal film: 26,700 ohms ±2%, 1/2 w.
R34	19A116278P233	Metal film: 2150 ohms ±2%, 1/2 w.
R35	19A116278P365	Metal film: 46,400 ohms ±2%, 1/2 w.
R36	19A116278P301	Metal film: 10,000 ohms ±2%, 1/2 w.
R37	19A116278P65	Metal film: 46.4 ohms ±2%, 1/2 w.
R38	3R77P204J	Composition: 0.2 megohm ±5%, 1/2 w.
R39	19A116278P385	Metal film: 75,000 ohms ±2%, 1/2 w.
R40	19A116278P329	Metal film: 19,000 ohms ±2%, 1/2 w.
R41	19A116278P285	Metal film: 7500 ohms ±2%, 1/2 w.
R42	19A116278P412	Metal film: 130,000 ohms ±2%, 1/2 w.
R43	19A116278P269	Metal film: 5110 ohms ±2%, 1/2 w.
R44	19A116278P117	Metal film: 147 ohms ±2%, 1/2 w.
R45 and R46	3R77P102J	Composition: 1000 ohms ±5%, 1/2 w.
NOTE The value of Resistor R47 must be obtained from the component, then find corresponding value in parts list for the correct part number.		
R47A	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
R47B	3R77P912J	Composition: 9100 ohms ±5%, 1/2 w.
R47C	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R47D	3R77P113J	Composition: 11,000 ohms ±5%, 1/2 w.
R47E	3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.
R47F	3R77P133J	Composition: 13,000 ohms ±5%, 1/2 w.
R47G	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
R47H	3R77P752J	Composition: 7500 ohms ±5%, 1/2 w.
R48	3R77P563J	Composition: 56,000 ohms ±5%, 1/2 w.
R49	3R77P224J	Composition: 0.22 megohm ±5%, 1/2 w.
R50	3R77P242J	Composition: 2400 ohms ±5%, 1/2 w.
R51	3R77P331J	Composition: 330 ohms ±5%, 1/2 w.
R52	3R77P102J	Composition: 1000 ohms ±5%, 1/2 w.
R53	3R77P201J	Composition: 200 ohms ±5%, 1/2 w.
R54	3R77P333J	Composition: 33,000 ohms ±5%, 1/2 w.
R55	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.

SYMBOL	GE PART NO.	DESCRIPTION
R56	3R77P363J	Composition: 3630 ohms ±5%, 1/2 w.
R57	3R77P103K	Composition: 10,300 ohms ±5%, 1/2 w.
R58	3R77P913J	Composition: 9130 ohms ±5%, 1/2 w.
R59*	3R77P182J	Composition: 1820 ohms ±5%, 1/2 w.
	3R152P432J	Composition: 4320 ohms ±5%, 1/2 w.
R60	3R77P432J	Composition: 4320 ohms ±5%, 1/2 w.
R61	3R77P682K	Composition: 6820 ohms ±5%, 1/2 w.
RT1	5490828P22	Thermistor
XFL1	19A121920G3	Resistor
A320		
C26	19A116080P206	Polymer capacitor
C27 and C28	19A116080P210	Polymer capacitor
C29*	19A116080P205	Polymer capacitor
	19B209243P107	Polymer capacitor
J6 and J7	4033513P4	Contact
L1	19A115690P1	Coil
R59*	3R77P182J	Composition: 1820 ohms ±5%, 1/2 w.
	3R152P432J	Composition: 4320 ohms ±5%, 1/2 w.
A321 and A322		
C5 thru C7	5494481P107	Ceramic capacitor
C8 and C9	19A116080P101	Polymer capacitor
Q1	19A116154P1	Thyristor
R1	3R152P221J	Composition: 2210 ohms ±5%, 1/2 w.
R2 and R3	3R152P220J	Composition: 2200 ohms ±5%, 1/2 w.
T1 and T2		
C1	5496218P641	Ceramic capacitor

SYMBOL	GE PART NO.	DESCRIPTION
R45	3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.
R46	3R77P913J	Composition: 91,000 ohms ±5%, 1/2 w.
R48*	19A116278P249	Metal film: 3160 ohms ±2%, 1/2 w.
	3R77P302J	In REV A: Composition: 3000 ohms ±5%, 1/2 w.
	3R77P332J	Earlier than REV A: Composition: 3300 ohms ±5%, 1/2 w.
R49	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R50	3R77P222J	Composition: 2200 ohms ±5%, 1/2 w.
R51	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R52	3R77P682J	Composition: 6800 ohms ±5%, 1/2 w.
R53*	3R77P223J	Composition: 22,000 ohms ±5%, 1/2 w.
	3R77P303J	In REV E and earlier: Composition: 30,000 ohms ±5%, 1/2 w.
	3R77P473J	In REV A and B: Composition: 47,000 ohms ±5%, 1/2 w.
	3R77P303J	Earlier than REV A: Composition: 30,000 ohms ±5%, 1/2 w.
R54	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
R55	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R56	3R77P224J	Composition: 0.22 megohms ±5%, 1/2 w.
R57	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R58	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.
R59	3R77P393K	Composition: 39,000 ohms ±10%, 1/2 w.
R60 and R61	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R62*	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w. Deleted by REV C.
	3R77P223K	Earlier than REV A: Composition: 22,000 ohms ±10%, 1/2 w.
R63*	3R77P432J	Composition: 4300 ohms ±5%, 1/2 w. Deleted by REV A.
R64*	3R77P120J	Composition: 12 ohms ±5%, 1/2 w.
	3R77P180J	In REV B and earlier: Composition: 18 ohms ±5%, 1/2 w.
R65*	3R77P154K	Composition: 0.15 megohm ±10%, 1/2 w. Deleted by REV A.
R66	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
R75*	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w. Added by REV A. Deleted by REV C.
R76*	3R152P912J	Composition: 9100 ohms ±5%, 1/4 w. Added by REV A. Deleted by REV C.
R77*	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.
	3R152P652J	In REV B: Composition: 5600 ohms ±5%, 1/4 w. Added by REV A.
R78*	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.
	3R77P100J	In REV C and earlier: Composition: 10 ohms ±5%, 1/2 w. Added by REV A.
R79*	3R152P393J	Composition: 39,000 ohms ±5%, 1/4 w. Added by REV A.
R80*	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w. Added by REV C.
R81*	3R152P472J	Composition: 4700 ohms ±5%, 1/4 w. Added by REV C.
R82*	3R77P273J	Composition: 27,000 ohms ±5%, 1/2 w. Added by REV C.

SYMBOL	GE PART NO.	DESCRIPTION
RT1	5490828P41	----- THERMISTORS ----- Thermistor: 30 ohms ±10%, color code black, white; sim to Globar Type BL211H-4.
RT2	5490828P9	Thermistor: 10,000 ohms ±10%, color code yellow; sim to Globar Type 551H8.
RT3*	5490828P9	Thermistor: 10,000 ohms ±10%, color code yellow; sim to Globar Type 551H8. Added by REV. A.
		----- TRANSFORMERS -----
T1	19A116040P1	Audio: 300- 4000 Hz, Pri: 19.3 ohms ±10% DC res, Sec: 23.5 ohms ±10% DC res.
A319		ENCODER/DECODER 4EK16A10 19C311797G1
		----- CAPACITORS -----
C1	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.
C2 and C3	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.
C4	19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW.
C5	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.
C6	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.
C7	19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW.
C8	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.
C9	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.
C10	19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW.
C11	19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW.
C12	19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW.
C13	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.
C14	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.
C15	5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.
C16	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.
C17	5496267P417	Tantalum: 1.0 µf ±5%, 35 VDCW; sim to Sprague Type 150D.
C18	5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.
C19	19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW.
C20	5494481P111	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C21	5496267P9	Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
C22	5496267P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D.
C23	5496267P13	Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
C24	5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.
C25	5496267P18	Tantalum: 6.8 µf ±20%, 35 VDCW; sim to Sprague Type 150D.
C26	19A116080P206	Polyester: 0.068 µf ±5%, 50 VDCW.
C27 and C28	19A116080P210	Polyester: 0.33 µf ±5%, 50 VDCW.
C29*	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.
		In REV B and earlier: Polyester: 0.1 µf ±10%, 50 VDCW.
C30	19B209243P107	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D.
		----- DIODES AND RECTIFIERS -----
CR1 and CR2	19A115250P1	Silicon.

SYMBOL	GE PART NO.
CR3 and CR4	5494922P1
CR5	19A115250P1
CR6	4036887P3
CR7 thru CR9	19A115250P1
FL1	19B205280G1 19B205280G2 19B205280G3 19B205280G4 19B205280G5 19B205280G6 19B205280G7 19B205280G8 19B205280G9 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1 19B205280G1
J1 thru J8	4033513P4
L1	19A115690P1
Q1	19A115123P7
Q2	19A115362P1
Q3 and Q4	19A115123P1
Q5 thru Q8	19A115362P1
Q9 and Q10	19A115123P1
R1	3R77P682K
R2	3R77P683J
R3	3R77P822J
R4	3R77P152J
R5	3R77P682K
R6	3R77P201J
R7	3R77P113J
R8*	19A116278F
	3R152P622J
	3R152P512J
R9	19A116278I
R10	3R77P512J
R11	3R77P103J

SYMBOL	GE PART NO.	DESCRIPTION
R5	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
R6	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
R7	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
R8	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
R9	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
R10	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
R11	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
R12	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
R13	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.
R14	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R15	3R77P333J	Composition: 33,000 ohms ±5%, 1/2 w.
R16	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.
R17	3R152P471J	Composition: 470 ohms ±5%, 1/4 w.
R18 and R19	3R152P513J	Composition: 51,000 ohms ±5%, 1/4 w.
R20	3R152P472K	Composition: 4700 ohms ±10%, 1/4 w.
R21 and R22	3R77P362J	Composition: 3600 ohms ±5%, 1/2 w.
R23	3R77P104K	Composition: 0.1 megohm ±10%, 1/2 w.
R24	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.
R25 and R26	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R27 and R28	3R77P753J	Composition: 75,000 ohms ±5%, 1/2 w.
R29	3R77P182J	Composition: 1800 ohms ±5%, 1/2 w.
R30*	3R77P821J	Composition: 820 ohms ±5%, 1/2 w. In REV C and earlier:
	3R77P102J	Composition: 1000 ohms ±5%, 1/2 w.
R31	3R77P821J	Composition: 820 ohms ±5%, 1/2 w.
R32*	3R77P752J	Composition: 7500 ohms ±5%, 1/2 w. Deleted by REV A.
R33*	3R77P912J	Composition: 9100 ohms ±5%, 1/2 w. Earlier than REV A:
	3R77P203J	Composition: 20,000 ohms ±5%, 1/2 w.
R34	3R77P332K	Composition: 3300 ohms ±10%, 1/2 w.
R35	3R77P330K	Composition: 33 ohms ±10%, 1/2 w.
R36	3R77P681J	Composition: 680 ohms ±5%, 1/2 w.
R37*	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w. Deleted by REV A.
R38*	3R77P752J	Composition: 7500 ohms ±5%, 1/2 w. Earlier than REV A:
	3R77P622J	Composition: 6200 ohms ±5%, 1/2 w.
R39*	3R77P820J	Composition: 8200 ohms ±5%, 1/2 w. Earlier than REV A:
	3R77P131J	Composition: 130 ohms ±5%, 1/2 w.
R40	3R77P241J	Composition: 240 ohms ±5%, 1/2 w.
R41*	3R152P240J	Composition: 24 ohms ±5%, 1/2 w. Earlier than REV A:
	3R77P300J	Composition: 30 ohms ±5%, 1/2 w.
R42*	3R77P200J	Composition: 20 ohms ±5%, 1/2 w. Earlier than REV A:
	3R77P160J	Composition: 16 ohms ±5%, 1/2 w.
R43	19B209358P101	Variable, carbon film: approx 25 to 250 ohms ±10%, 0.2 w; sim to CTS Type X-201.
R44	19B209022P101	Wirewound: .27 ohms ±10%, 2 w; sim to LRC Type BWH.

SYMBOL	GE PART NO.	DESCRIPTION
R45	3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.
R46	3R77P913J	Composition: 91,000 ohms ±5%, 1/2 w.
R48*	19A116278P249	Metal film: 3160 ohms ±2%, 1/2 w. In REV A: Composition: 3000 ohms ±5%, 1/2 w. Earlier than REV A: Composition: 3300 ohms ±5%, 1/2 w.
	3R77P302J	Composition: 3000 ohms ±5%, 1/2 w.
	3R77P332J	Composition: 3300 ohms ±5%, 1/2 w.
R49	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R50	3R77P222J	Composition: 2200 ohms ±5%, 1/2 w.
R51	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
R52	3R77P682J	Composition: 6800 ohms ±5%, 1/2 w.
R53*	3R77P223J	Composition: 22,000 ohms ±5%, 1/2 w. In REV E and earlier: Composition: 30,000 ohms ±5%, 1/2 w. In REV A and B: Composition: 47,000 ohms ±5%, 1/2 w. Earlier than REV A: Composition: 30,000 ohms ±5%, 1/2 w.
	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.
	3R77P303J	Composition: 30,000 ohms ±5%, 1/2 w.
R54	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
R55	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R56	3R77P224J	Composition: 0.22 megohms ±5%, 1/2 w.
R57	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R58	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.
R59	3R77P393K	Composition: 39,000 ohms ±10%, 1/2 w.
R60 and R61	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R62*	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w. Deleted by REV C. Earlier than REV A: Composition: 22,000 ohms ±10%, 1/2 w.
	3R77P223K	Composition: 22,000 ohms ±10%, 1/2 w.
R63*	3R77P432J	Composition: 4300 ohms ±5%, 1/2 w. Deleted by REV A.
R64*	3R77P120J	Composition: 12 ohms ±5%, 1/2 w. In REV B and earlier: Composition: 18 ohms ±5%, 1/2 w.
	3R77P180J	Composition: 18 ohms ±5%, 1/2 w.
R65*	3R77P154K	Composition: 0.15 megohm ±10%, 1/2 w. Deleted by REV A.
R66	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
R75*	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w. Added by REV A. Deleted by REV C.
R76*	3R152P912J	Composition: 9100 ohms ±5%, 1/4 w. Added by REV A. Deleted by REV C.
R77*	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w. In REV B: Composition: 5600 ohms ±5%, 1/4 w. Added by REV A.
	3R152P652J	Composition: 5600 ohms ±5%, 1/4 w. Added by REV A.
R78*	3R77P200J	Composition: 20 ohms ±5%, 1/2 w. In REV C and earlier: Composition: 10 ohms ±5%, 1/2 w. Added by REV A.
	3R77P100J	Composition: 10 ohms ±5%, 1/2 w. Added by REV A.
R79*	3R152P393J	Composition: 39,000 ohms ±5%, 1/4 w. Added by REV A.
R80*	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w. Added by REV C.
R81*	3R152P472J	Composition: 4700 ohms ±5%, 1/4 w. Added by REV C.
R82*	3R77P273J	Composition: 27,000 ohms ±5%, 1/2 w. Added by REV C.

SYMBOL	GE PART NO.	DESCRIPTION
RT1		545
RT2		545
RT3*		545
T1		19A
A319		
C1		19A
C2 and C3		19A
C4		19A
C5		19A
C6		19A
C7		19A
C8		19A
C9		19A
C10		19A
C11		19A
C12		19A
C13		19A
C14		19A
C15		545
C16		19A
C17		545
C18		545
C19		19A
C20		545
C21		545
C22		545
C23		545
C24		545
C25		545
C26		19A
C27 and C28		19A
C29*		19A
C30		545
CR1 and CR2		19A

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the number of the assembly. The revision stamped on the assembly includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - Chassis and RF Assembly 19E500872-G1 & -G2

To incorporate a better high-frequency capacitor. Changed C5 on First Mixer A301/A302.

REV. A - 2nd Mixer A317 (19B216119-G1)

To make receiver compatible with new system. Added C17.

REV. B - Chassis and RF Assembly 19E500872-G1 & -G2

To improve stability. Changed C2 on Hi IF Amp A315.

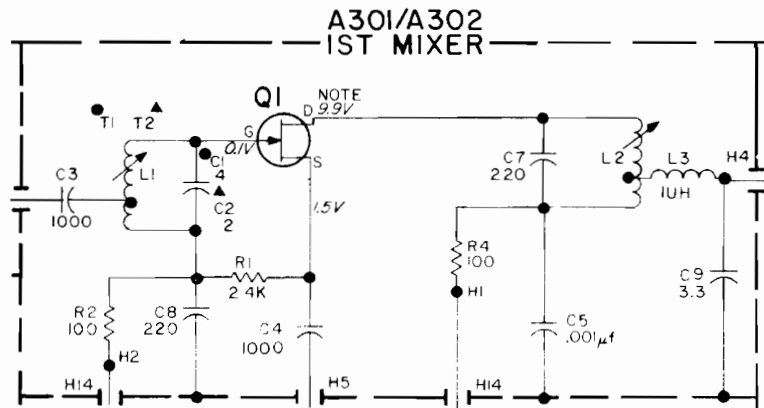
REV. C - Chassis and RF Assembly 19E500872-G1 & -G2

To protect the receiver against positive voltage transients. Added thyrector CR1 between J443-11 and -13.

REV. D - Chassis and RF Assembly 19E500872-G1 & -G2

To improve sensitivity and improve Intermodulation (EIA) performance. Deleted C6 & R3 and changed C7 & L2 on First Mixer A301/A302.

Schematic Diagram Was:



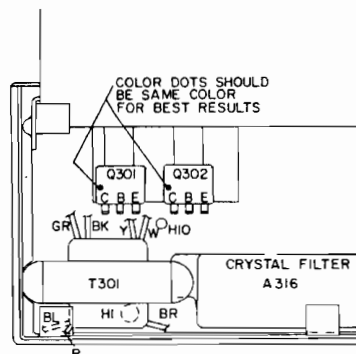
Step 7 of receiver alignment was:

7.	B (2nd IF AMP)	Pin 2	C6 and L1 (on 1st MIXER A301/A302)	Maximum	Apply an on-frequency signal into Hole 304, and tune C6 and L1 for maximum meter reading, keeping signal below saturation.
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REV. E - Chassis and RF Assembly 19E500872-G1 & -G2

To incorporate new PA transistors. Changed Q301/Q302 and added R303.

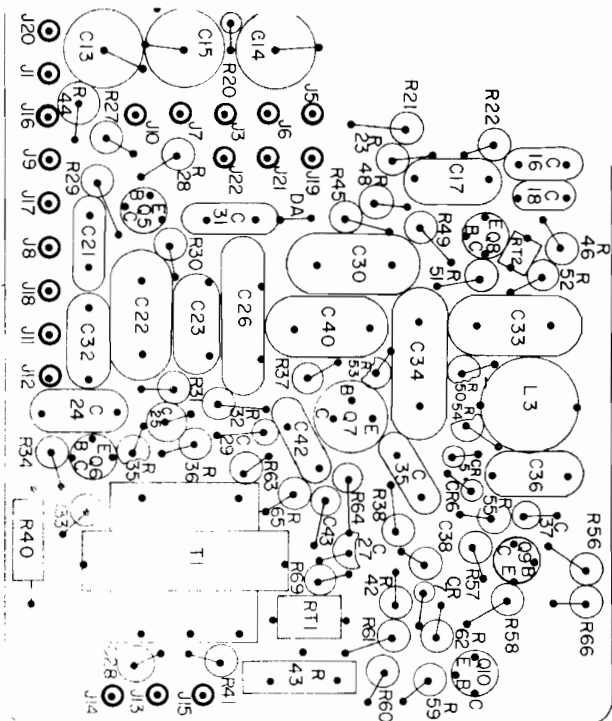
Outline Diagram Was:



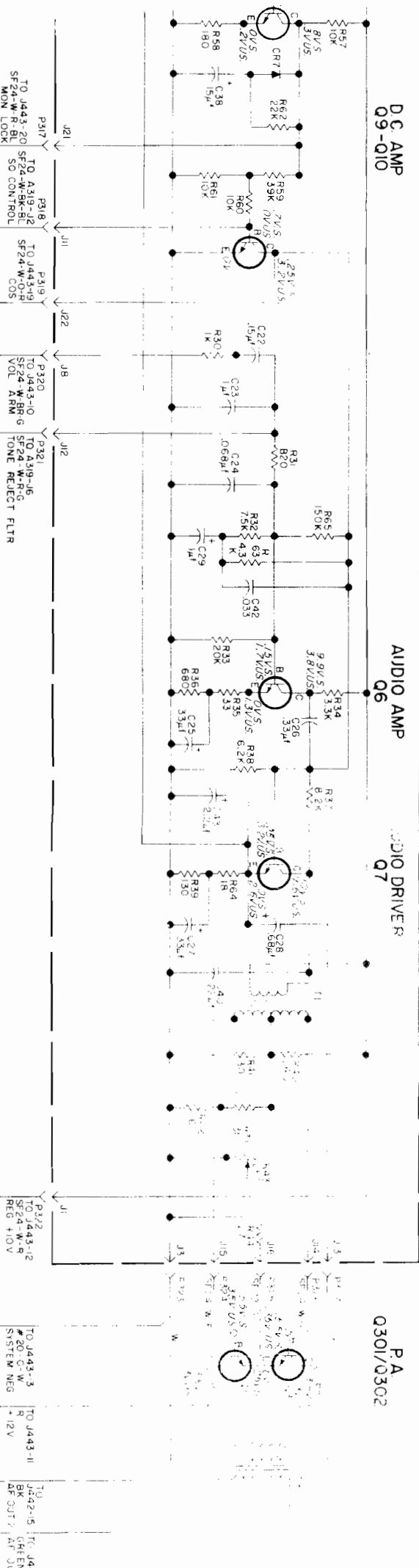
To make IF Audio & Squelch Board compatible with new PA transistors and to improve squelch operation, Added C49-C54, CR8, R75-R79, and RT3. Deleted C24, C28, C29, C42, C43, R32, R37, R63 and R65. Changed C21, C26, C37, C38, C40, R33, R38, R39, R41, R42, R48, R53 and R62.

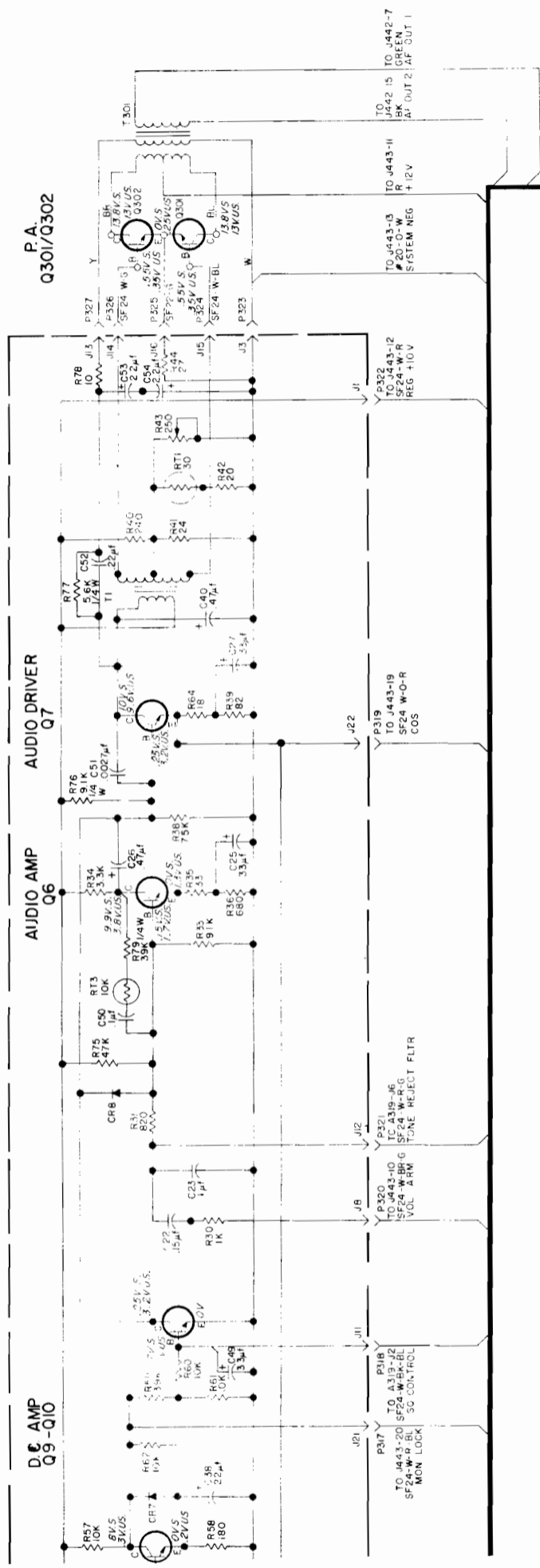
Outline Diagram Was:

IF-AUDIO & SQUELCH BOARD A318



Schematic Diagram Was:

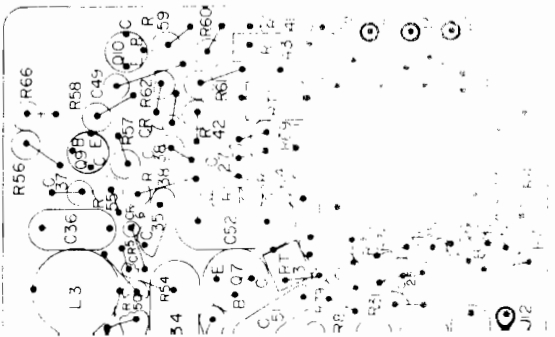




Panel Guard. Removed
te-Orange wire between

changed R48.

and to reduce receiver
R76. Added C55, R80,



REV. D - IF Audio & Squelch Board A318 (19D413129-G1)

To improve receiver frequency response.
Changed R30 and R78.

REV. D - Channel Guard Encoder/Decoder A319 (Model 4EK16A10)
REV. D - Tone Reject Filter A320 (19C311797-G2)

To prevent excessive roll-off at 300 Hertz.
Changed R59.

REV. E - IF Audio & Squelch Board A318 (19D413129-G1)

To compensate for vendor change.
Changed C26.

REV. F - IF Audio & Squelch Board A318 (19D413129-G1)

To improve squelch action.
Changed R53.

REV. G - Chassis and RF Assembly (19E500872-G1 & G2)

To stabilize the 1st mixer. Deleted R301
on the 2nd Multiplier and added R5 to the
1st mixer.

REV. H - Chassis and RF Assembly (19E500872-G2)

To improve tone of the 1st mixer.

REV. H - Chassis and RF Assembly (19E500872-G1)

To eliminate oscillations. Added R6.

REV. J - Chassis and RF Assembly (19E500872-G2)

To eliminate oscillations. Added R6.

REV. J - Chassis and RF Assembly (19E500872-G1)

To remove unnecessary protection.
Removed CR1.

REV. K - Chassis and RF Assembly (19E500872-G2)

To remove unnecessary protection.
Removed CR1.

REV. H - IF Audio and Squelch Board A318 (19D413129-G1)

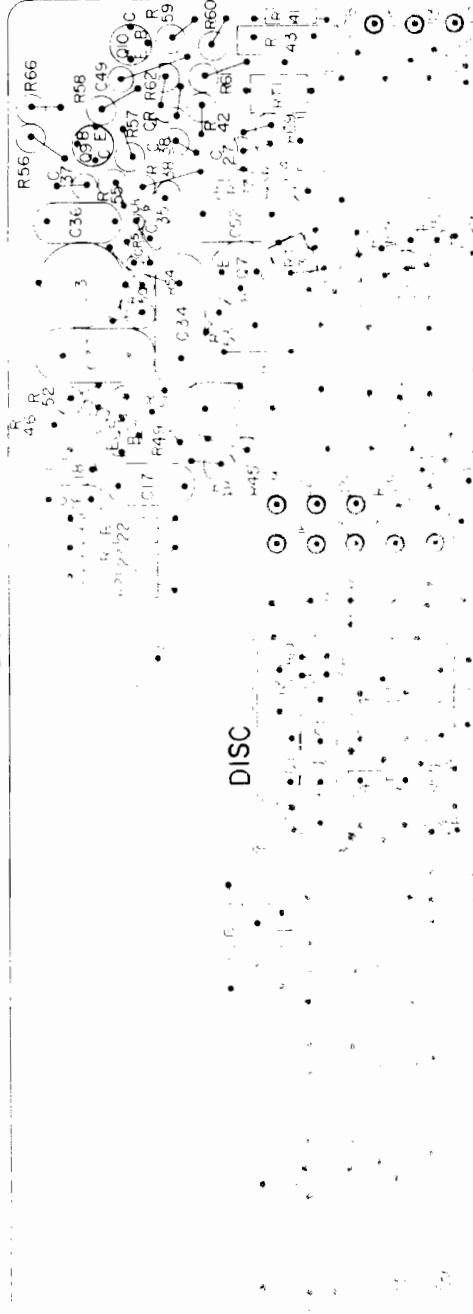
To insure squelch action at -30 C.
Changed Q10.

PRODUCTION CHANGES

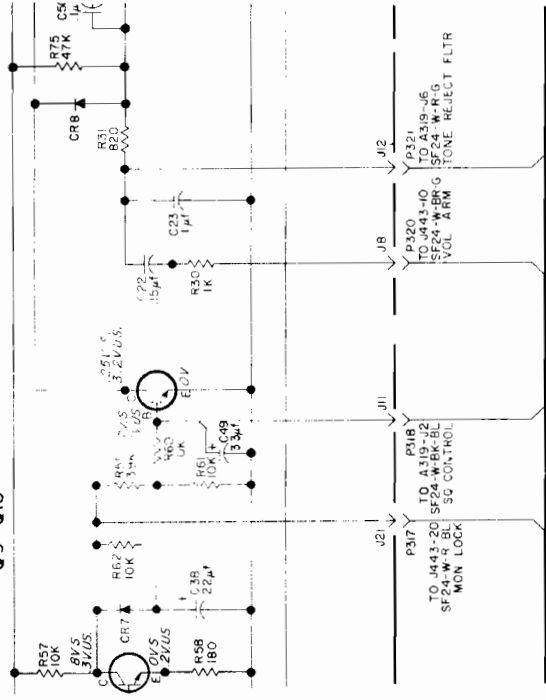
- REV. B - Channel Guard Encoder (Model 4EK16A10) To increase stop-band attenuation. Changed R8.
- REV. C - Channel Guard Encoder (Model 4EK16A10) To optimize frequency response. Changed C29.
- REV. A - Tone Reject Filter (19C31797-G2) Chassis and RF Assembly (19E509872-G1 & G2)
To eliminate squelch opening thump in receivers with Channel Guard. Removed white-Orange wire between TB2-1. Added a White-Orange wire between P312 (or J17 on IF Audio and Squelch board) and TB2-1.
- REV. A - RF Pre Amp A322 (19A127479-G2) To assure band-end tuning at 150.8 MHz. Changed C2.
- IF Audio & Squelch Board A318 (19D413129-G1)
- REV. B - To control more closely the squelch control rotation. Changed R48.
- REV. C - To eliminate barely audible squelch switching transients and to reduce receiver squelch tail. Deleted C38, C49, CR7, CR8, R62, R75, and R76. Added C55, R80, R81, and R82. Changed C27, C36, R53, R64, and R77.

Outline Diagram was:

IF-AUDIO & SQUELCH BOARD A318



D.C. AMP Q9-Q10



- REV. D - IF Audio & Squelch Board A318 (19D) To improve receiver frequency response. Changed R30 and R78.
- REV. D - Channel Guard Encoder/Decoder A319
- REV. B - Tone Reject Filter A320 (19C311797) To prevent excessive roll-off at 3. Changed R59.
- REV. E - IF Audio & Squelch Board A318 (19E) To compensate for vendor change. Changed C26.
- REV. F - IF Audio & Squelch Board A318 (19F) To improve squelch action.